

(abstract)

# PATENT ABSTRACTS OF JAPAN

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## (54) METHOD AND DEVICE FOR MANUFACTURING SEMICONDUCTOR DEVICE

### (57)Abstract:

**PURPOSE:** To form the shallow impurity distribution of boron to a sample by using a specific raw material for ion implantation and ion-implanting the molecules or cluster ions of boron or of boron and hydrogen to the sample.

**CONSTITUTION:** A borane or its derivatives are employed as an ion implantation raw material. The molecules or cluster ions of boron, such as B<sub>4</sub>H, B<sub>5</sub>H, B<sub>5</sub>H, B<sub>10</sub>H, B<sub>10</sub>H, etc., or of boron and hydrogen are formed while being made to differ from a raw material gas such as a conventional boron fluoride (BF<sub>3</sub>) gas or other solid raw materials, and ion-implanted to a sample. Accordingly, a high-concentration P-type layer can be shaped in a shallow region of several hundred Ångström or less in the sample, and an extremely thin base layer is acquired when the title method is applied for forming a base in an N-P-N transistor, thus attaining the increase of working speed.

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# I. PATENT ABSTRACTS OF JAPAN

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(71)Applicant : SUMITOMO CHEM CO LTD

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## (54) DIELECTRIC COMPOSITION, ITS PRODUCTION AND ITS USE

### (57)Abstract:

PURPOSE: To obtain a dielectric composition capable of providing dense structure and excellent in insulating property by selecting a dielectric composition having a specific composition.

CONSTITUTION: This dielectric composition has a composition expressed by the formula,  $s(AuCvRwOx)-(1-s)(AOy-bCO_r-aGO_z)$  [A is Ca, Sr, Ba, Pb, La, Ce, Pr, Nd, Pm, Sm, Eu, Gd, Tb, Dy, Ho, Er, Tm, Yb, Lu or Y; C is Bi, Sb, Cr or Ti; R is Ti, Ta, Hf, W, Mo, Nb or Zr; G is B, As, Sb, Si, Ge, Te or P;  $0.3 < (s) \leq 0.95$ ;  $1/19 \leq (a) \leq 2.0$ ;  $0.5 \leq (b)/(a) \leq 7$ ; (u), (v), (w) and (x) are each a real number determined so that total electron charge becomes 0; when A is divalent, (y) is 1; when A is trivalent, (y) is 1.5; when C is trivalent, (r) is 1.5 and when C is quadrivalent, (r) is 2; when C is pentavalent, (r) is 2.5; when C is hexavalent, (r) is 3; when G is trivalent, (z) is 1.5; when G is quadrivalent, (z) is 2; when G is pentavalent, (z) is 2.5].

## CLAIMS

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[Claim(s)]  
 [Claim 1]A general formula (1)  
 [Formula 1]  
 $s(AuCvRwOx)-(1-s)(AOy-bCO_r-aGO_z)$   
 the inside of a formula, and A -- Ca, Sr, Ba, Pb, La, Ce, Pr, Nd, and Pm. One or two or more

elements which were chosen from Sm, Eu, Gd, Tb, Dy, Ho, Er, Tm, Yb, Lu, and Y, One or two or more elements in which 1 or two or more elements in which C was chosen from Bi, Sc, Sb, Cr, and Tl, and R were chosen from Ti, Ta, Hf, W, Mo, Nb, and Zr, and G are one sort or two sorts or more of elements chosen from B, As, Sb, Si, germanium, Te, and P. s, a, and b express the real number, and are in the range of  $0.3 < s \leq 0.95$ ,  $1/19 \leq a \leq 2$ , and  $0.5 \leq b/a \leq 7$ . s expresses the molar fraction of a crystal phase. u, v, w, and x are the real numbers decided that the whole electric charge is set to 0. y, r, and z express the number of oxygen, and it is  $y = 1.5$ , when A is divalent and  $y = 1$  and A are trivalent, It is  $r = 3$ , when C is trivalent,  $r = 1.5$  and C are tetravalence,  $r = 2$  and C are pentavalence and  $r = 2.5$  and C are 6 values, It is  $z = 2.5$ , when G is trivalent,  $z = 1.5$  and G are tetravalence and  $z = 2$  and G are pentavalence. Dielectric constituent having the presentation shown.

[Claim 2] A compound of said element A as a raw material which may be converted into an oxide or an oxide, A compound of said element C, a compound of said element B, and a compound of said element G, A manufacturing method of the dielectric constituent according to claim 1 mixing in the state of a cluster of as [ whose size of the it is an atom, molecules, or those aggregates and is less than 0.1 micrometer in diameter ], oligomer, or particles, and heat-treating this mixture at temperature which it may convert into an oxide.

[Claim 3] In a method of manufacturing a dielectric constituent by applying a dielectric formation solution, forming a thin film on a substrate, and subsequently heat-treating this thin film, A manufacturing method of the dielectric constituent according to claim 1 using a solution which becomes an organic solvent and this organic solvent from a compound of the meltable element A, a compound of the element R, a compound of the element C, and a compound of the element G as a dielectric formation solution.

[Claim 4] colloidal one containing a compound of the element A, a compound of the element C, a compound of the element B, and a compound of the element G -- sol -- this colloidal one -- sol -- a manufacturing method of a dielectric constituent of claim 1 heat-treating at temperature which each inner compound may convert into an oxide.

[Claim 5] A manufacturing method of the dielectric constituent according to claim 1 producing a film by sputtering using an oxide sintering target containing an oxide of the element A, an oxide of the element C, an oxide of the element B, and an oxide of the element G.

[Claim 6] A thin film capacitor forming the dielectric constituent according to claim 1 filmy on a glass substrate covered with a glass substrate, a ceramic substrate or a metal thin film, and a conductive oxide thin film or a ceramic substrate, a metallic foil, or a semiconductor substrate.

## DETAILED DESCRIPTION

[Detailed	Description	of	the	Invention]
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[0001]

[Industrial Application] This invention relates to a dielectric constituent, and its manufacturing method and use. The dielectric constituent of this invention is applicable to piezoelectric components, such as dielectric products, such as a thin film capacitor, a capacitor for DRAM memories, a ferroelectric memory, a multilayer capacitor, and dielectric paste, an actuator, a resonator, a filter, and an ultrasonic motor, etc. It is applicable by doping of rare earth ions to piezoelectric components, such as an actuator and a pressure-sensitive sensor, as a piezo-electric composite among dielectric constituents to a fluorescent substance raw material again the end of

detailed

single

crystal

powder.

[0002]

[Description of the Prior Art]Conventionally, dielectrics, such as barium titanate and lead titanate, are used as a ceramic capacitor or a filter by the dielectric characteristics and piezoelectric property. The application what is called to a ferroelectric memory which uses polarization as a memory is also studied briskly in recent years.

[0003]In these ceramic capacitors, in order to enlarge capacity generally, a lamination type is used and it is used. In the manufacturing method of a stacked capacitor, dielectric powder with a particle diameter of 0.5-5 micrometers obtained at solid phase reaction or a solution reaction, It mixes with a binder or a solvent, a slurry is manufactured, this slurry is fabricated to sheet metal with a doctor blade method etc., 10 - ten layers of numbers laminate this sheet metal, and the process of subsequently calcinating at 1200-1300 \*\* is taken.

[0004]however -- when based on such a method, at the temperature of not less than 1300 \*\*, calcination temperature is high -- silver, copper, etc. -- the metal of cheapness and low resistance was not able to be comparatively used as an electrode. In order to make calcination temperature low, the method of mixing glass frit with dielectric powder is also tried. Although it became possible to reduce calcination temperature at about 1000 \*\* by this method, it was still high, in view of the silver melting point (965 \*\*), and when glass frit was moreover added in large quantities and the rate of the dielectric fell, dielectric characteristics fell.

[0005]Since it was very difficult to use the particle diameter of 1 micrometer or less dielectric powder and since especially glass frit grinds and is manufactured, it was difficult for the structure of a precise green body to be hard to be attained, and to make thickness thin. That is, since dielectric powder was large when forming a filmy dielectric with a doctor blade method using the powder of the dielectric obtained with the solid phase technique or the liquid phase process, it was difficult for the thickness of a dielectric to be 20micro or less.

[0006]By the way, the electric capacity of a capacitor is  $C = (\epsilon_0 \epsilon_r S / d) \times n$  (among a formula). C -- area and d show inter electrode distance, a vacuum dielectric constant and  $\epsilon_r$  show specific inductive capacity  $\epsilon_0$ , and, as for electric capacity and S, n shows the number of laminations. what is necessary is just to increase the number of laminations, since it has a relation and there is a limit in area and thickness for the miniaturization of a laminate type ceramic capacitor, and high-capacity-izing, although it divides and comes out, In the thick described method of thickness, a limit is naturally produced in high capacity-ization. There is the method of thin-film-izing a dielectric layer as one of the solution of this.

[0007]In the case of a stacked capacitor, one layer is about 20-40 micrometers, but if-izing can be carried out [ thin film ] to about 1-5 micrometers, big capacity is obtained and, moreover, it can miniaturize. Although the method of manufacturing a filmy dielectric by spreading of gaseous phase methods, such as a sputtering technique, a vacuum deposition method, and a CVD method, and a sol-gel method, and an organic metallic compound and a pyrolysis other than a doctor blade method and print processes, etc. are known as the method of thin-film-izing, Since thickness became thin, it was easy to connect too hastily, and there was a fault, like the leakage current is large. In order to acquire a precise Plastic solid, the method of using ferroelectric glass ceramics is also known.

[0008]About these dielectric powder, it is manufactured as 0.5-5-micrometer dielectric powder with the coprecipitation method by a solution reaction, etc. in the solid phase reaction by generally calcinating powder, such as an oxide and carbonate, at an elevated temperature, and solution. Also in which reaction of these, the powder obtained consists of secondary particles currently formed by a primary particle condensing, and there was a problem in the homogeneity of a presentation, and crystallinity. In order to solve this, the hydrothermal crystallization method

is proposed, but the method needs high temperature high pressure, and an installation cost, productivity, etc. to cost becomes high. Then, the method of using glass ceramics as other methods is also proposed.

[0009]In the method of using glass ceramics, after blending a compound with the presentation which can form glass first, quench, after fusing at an about 1400 \*\* elevated temperature, and consider it as glass, it is made to crystallize by subsequently heat-treating this at 600-800 \*\*, and glass ceramics are obtained. According to this method, in order not to receive restriction of the size of the first particles, thin-film-izing is possible, and moreover, low dielectric loss and high withstand voltage can be realized for the substantia compacta. A detailed single crystal is obtained by [ which dissolve a part for this glass ] removing.

[0010]However, the presentation which can be vitrified as known well is restricted extremely. An alkaline metal, alkaline-earth metals, the metal except the metal (oxides, such as Si, B, P, Se, and Te) which builds a glass meshes-of-a-net formation oxide, metallic oxides, and specifically promoting crystallization, for example, if Ti, Zr, Ta, etc. work as a nucleation agent and it blends with glass are known especially. For this reason, it is very difficult to make more than 30% a rate of a high permittivity crystal phase which needs these for a large quantity, for this reason high permittivity was not able to be obtained by this method.

[0011]

[Problem(s) to be Solved by the Invention]By increasing the rate of a ferroelectric crystal phase, this invention demonstrates the characteristic, gives a precise organization at low temperature rather than a crystal phase independent case, and relates to a good dielectric constituent, and its insulating manufacturing method and use. It is related with the dielectric constituent obtained by the manufacturing method more compoundable at low temperature especially, and this manufacturing method, and its use.

[0012]

[Means for Solving the Problem]That is, this invention is shown below.

[1]General formula (1)

[Formula 2]

$s(\text{Au} \quad \text{Cv} \quad \text{Rw} \quad \text{Ox})-(1-s)(\text{AOy} \quad -\text{bCOr} \quad -\text{aGOz})(1)$

the inside of a formula, and A -- Ca, Sr, Ba, Pb, La, Ce, Pr, Nd, and Pm. One or two or more elements which were chosen from Sm, Eu, Gd, Tb, Dy, Ho, Er, Tm, Yb, Lu, and Y, One or two or more elements in which 1 or two or more elements in which C was chosen from Bi, Sc, Sb, Cr, and Tl, and R were chosen from Ti, Ta, Hf, W, Mo, Nb, and Zr, and G are one sort or two sorts or more of elements chosen from B, As, Sb, Si, germanium, Te, and P. s, a, and b express the real number, and are in the range of  $0.3 < s \leq 0.95$ ,  $1/19 \leq a \leq 2$ , and  $0.5 \leq b/a \leq 7$ . s expresses a molar fraction of a crystal phase. u, v, w, and x are the real numbers decided that the whole electric charge is set to 0. y, r, and z express the number of oxygen, and it is  $y = 1.5$ , when A is divalent and  $y = 1$  and A are trivalent, It is  $r = 3$ , when C is trivalent,  $r = 1.5$  and C are tetravalence,  $r = 2$  and C are pentavalence and  $r = 2.5$  and C are 6 values, It is  $z = 2.5$ , when G is trivalent,  $z = 1.5$  and G are tetravalence and  $z = 2$  and G are pentavalence. Dielectric constituent having the presentation shown.

[0013][2]A compound of said element A as a raw material which may be converted into an oxide or an oxide, A compound of said element C, a compound of said element B, and a compound of said element G, Said paragraph mixing in the state of a cluster of as [ whose size of the it is an atom, molecules, or those aggregates and is less than 0.1 micrometer in diameter ], oligomer, or particles, and heat-treating this mixture at temperature which it may convert into an oxide [1]A

manufacturing method of a dielectric constituent of a statement. [0014][3]In a method of manufacturing a dielectric constituent by applying a dielectric formation solution, forming a thin film on a substrate, and subsequently heat-treating this thin film, Said paragraph using a solution which becomes an organic solvent and this organic solvent from a compound of the meltable element A, a compound of the element R, a compound of the element C, and a compound of the element G as a dielectric formation solution [1]A manufacturing method of a dielectric constituent of a statement. [0015][4]colloidal one containing a compound of the element A, a compound of the element C, a compound of the element B, and a compound of the element G -- sol -- this colloidal one -- sol -- said paragraph heat-treating at temperature which each inner compound may convert into an oxide A manufacturing method of a dielectric constituent of [1]. [0016][5]Said paragraph producing a film by sputtering using an oxide sintering target containing an oxide of the element A, an oxide of the element C, an oxide of the element B, and an oxide of the element G [1]A manufacturing method of a dielectric constituent of a statement. [0017][6]Said paragraph [1]A thin film capacitor forming a dielectric constituent of a statement filmy on a glass substrate covered with a glass substrate, a ceramic substrate or a metal thin film, and a conductive oxide thin film or a ceramic substrate, a metallic foil, or a semiconductor substrate.

[0018]Hereafter, this invention is explained still in detail. Ca, Sr, Ba, Pb, La which are defined as the element A in this invention, Ce, Pr, Nd, Pm, Sm, Eu, Gd, Tb, Dy, Ho, Er, A compound of one sort or two sorts or more of elements chosen from Tm, Yb, Lu, and Y. Bi, Sc which are defined as (it is hereafter called a compound of the element A), and the element C, One sort or two sorts or more of compounds chosen from Sb, Cr, and Tl. Ti, Ta which are defined as (it is hereafter called a compound of the element C), and the element R, A compound of one sort or two sorts or more of elements chosen from Hf, W, Mo, Nb, and Zr. When a mixture of those compounds is heat-treated for a compound (henceforth a compound of the element G) of one sort or two sorts or more of elements chosen from B, As, Sb, Si, germanium, Te, and P which are defined as (henceforth a compound of the element R), and the element G, it is a general formula (1).

[Formula 3]  

$$s(\text{Au} \quad \text{Cv} \quad \text{Bw} \quad \text{Ox})-(1-s)(\text{AOy} \quad -\text{bCO}r \quad -\text{aGO}z)(1)$$
A dielectric constituent is obtained by heat-treating at the temperature which is mixed and those compounds may convert subsequently to an oxide so that the dielectric constituent to satisfy may be obtained.

[0019]In a dielectric constituent expressed with a general formula (1), (Au Cv Bw Ox) expresses a dielectric crystal phase, and (AOy -bCO<sub>r</sub> -aGO<sub>z</sub>) expresses a glass phase. A crystal phase expresses s comparatively (molar fraction), and (1-s) expresses a rate (molar fraction) of a glass phase. s is in the range of 0.3 < s ≤ 0.95. When s is 0.3 or less, desirable dielectric characteristics are not acquired and 0.95 is exceeded, generation of a crystal phase is difficult and an elevated temperature is needed. In order to control particle diameter of a crystal phase, generation temperature, etc. desirably, s should just be the above-mentioned range. [0020]y, r, and z express the number of oxygen, and it is y= 1.5, when A is divalent and y= 1 and A are trivalent, When C is trivalent, r= 1.5 and C are tetravalence, r= 2 and C are pentavalence and r= 2.5 and C are 6 values, it is r= 3, and it is z= 2.5, when G is trivalent, z= 1.5 and G are tetravalence and z= 2 and G are pentavalence. a and b express the real number and are in the range of 1/19 ≤ a ≤ 2, and 0.5 ≤ b/a ≤ 7.

[0021]u, v, w, and x are the real numbers decided that the whole electric charge is set to 0. y, r, and z express the number of oxygen, and it is  $y = 1.5$ , when A is divalent and  $y = 1$  and A are trivalent, When C is trivalent,  $r = 1.5$  and C are tetravalence,  $r = 2$  and C are pentavalence and  $r = 2.5$  and C are 6 values, it is  $r = 3$ , and it is  $z = 2.5$ , when G is trivalent,  $z = 1.5$  and G are tetravalence and  $z = 2$  and G are pentavalence.

[0022]x is  $1/2$  of a sum total valence which multiplied a valence of each ion which constitutes A, C, and R by a molar fraction from a request of electroneutrality. b expresses the number of mols of an element standard of a glass phase formation oxide. a case of for example, way acid ( $B_2O_3$ ) - in 1 mol and  $SiO_2$ , in 1 mol and  $P_2O_5$ ,  $PO_{2.5}$  shall be made into mol, and  $SiO_2$  shall be  $BO_{1.5}$  1 mol.

[0023]a expresses a mole ratio to G of the elements A and R which exist in a glass phase, and twice [  $1/19$  to ] as many mole ratios as this are  $1/9$  to 1 time as many mole ratios desirable still more preferably. If a is smaller than  $1/19$ , escaping of A from a compound in a crystal phase and R will arise, the amount of crystal phases will decrease, if more than 2, excessive AO and RO will deposit and a crystal phase will decrease too.

[0024]In a manufacturing method of this invention, as a raw material which may be converted into an oxide or an oxide, A compound of said element A, a compound of said element C, a compound of said element B, and a compound of said element G, It mixes in the state of a cluster of as [ whose size of the it is an atom molecules, or those aggregates and is less than 0.1 micrometer in diameter ], oligomer, or particles, and, simultaneously with formation of this mixture, it heat-treats this mixture after formation at temperature which may be converted into an oxide. When such the precise mixed state is attained, it is already equivalent to a vitreous state in the conventional glass-ceramics method in the state. For this reason, in a conventional method, a high temperature process in required glass Tsukuru becomes unnecessary.

[0025]However, since it is a mere mixture, it is necessary to make it crystallize with heating etc. the way things stand. Timing of heating is based also on a process of creating a mixture. namely, a case where a filmy dielectric is created -- sputtering, CVD, vacuum evaporation, a spreading pyrolysis of an organic compound, and colloidal one, in using spreading of sol, etc., It is possible by heating a substrate during film production or using plasma to make the crystallization cause simultaneously with formation of a mixture. After producing a film at low temperature and obtaining a mixture, it is possible to also make it heat and crystallize. In obtaining powder, it is difficult to heat, at the same time as it generally compounds a mixture, and after obtaining this mixture, it heat-treats, and crystallizes.

[0026]By adjusting a grade of heat-treatment, a grade of crystallization is controllable. That is, in a dielectric constituent expressed with a general formula (1) of this invention, a rate of a crystal phase (Au Cv Bw Ox) to generate changes with grades of heat-treatment, and the maximum is equal to s. When conversion is set to f, a molar fraction of a crystal phase in a final product is expressed with (fxs). Crystallization is promoted, so that cooking time is so long that cooking temperature is generally high.

[0027]A compound of said element A as a raw material which may be converted into an oxide or an oxide, A compound of said element C, a compound of said element B, and a compound of said element G, As a method of mixing in the state of a cluster of as [ whose size of the it is an atom, molecules, or those aggregates, and is less than 0.1 micrometer in diameter ], oligomer, or particles, colloidal one of a method of using meltable metallic compounds for vacuum processes, such as sputtering, CVD, and vacuum evaporation, and an organic solvent, silica colloid, etc. -- a method of using sol, a method of using meltable metallic compounds for water, etc. are

mentioned.

[0028]As a raw material, in applying sputtering process, An oxide corresponding to a presentation of said general formula (1), i.e., PbO, BaO, Li<sub>2</sub>O, Na<sub>2</sub>O, K<sub>2</sub>O, MgO, CaO, SrO, TiO<sub>2</sub>, ZrO<sub>2</sub>, SnO<sub>2</sub>, ZnO, FeO, CoO, NiO, Nb<sub>2</sub>O<sub>5</sub>, Ta<sub>2</sub>O<sub>5</sub>, W<sub>2</sub>O<sub>5</sub>, La<sub>2</sub>O<sub>3</sub>, Y<sub>2</sub>O<sub>3</sub>, B<sub>2</sub>O<sub>3</sub>, As<sub>2</sub>O<sub>3</sub>, A target of each compound, such as Sb<sub>2</sub>O<sub>3</sub>, SiO<sub>2</sub>, GeO<sub>2</sub>, and TeO<sub>2</sub>, is used if needed, Multiple-targets sputtering which controls a presentation and thickness by sputtering time of a target of each compound, Or reactive sputtering using a method and reactive gas (especially oxygen) which are beforehand mixed to a desired presentation and carry out sputtering to it using a target of a sintered dielectric constituent, etc. are mentioned.

[0029]When applying a CVD method, the following compound can be mentioned as a compound of the element A used as a raw material.

[0030]Organic barium compounds, such as lead compound barium ethoxide of halogenides, such as organic lead compounds, such as 4 ethyl lead and screw dipivaloylmethanato lead, or a lead chloride, barium isopropoxide, and screw dipivaloyl barium, or a barium compound of halogenides, such as barium chloride [0031]Organic calcium compounds, such as calcium ethoxide, calcium isopropoxide, and screw dipivaloyl calcium, Or organic strontium compounds, such as lime compound strontium ethoxide of halogenides, such as a calcium chloride, strontium isopropoxide, and screw dipivaloyl strontium, or a strontium compound of halogenides, such as a strontium chloride [0032]Organic lanthanum compounds, such as lantern ethoxide, lantern acetylacetonato, and a tris dipivaloyl lantern, Or organic yttrium compounds, such as lanthanum compound yttrium ethoxide of halogenides, such as a lanthanum chloride, yttrium acetylacetonato, and tris dipivaloyl yttrium, or an yttrium compound of halogenides, such as a yttrium chloride [0033]Organic metallic compounds, such as a cerium compound like cerium ethoxide, a praseodymium compound like praseodymium ethoxide, other neodymium ethoxide, tris dipivaloyl gadolinium, and a tris dipivaloyl terbium [0034]When applying a CVD method, the following compound can be mentioned as a compound of the element R used as a raw material.

[0035]Titanium ethoxide, titanium isopropoxide, titanium butoxide, Titanium compound zirconium ethoxide of halogenides, such as an organic titanium compound like acetic acid titanium, or titanium tetrachloride, A zirconium compound of halogenides, such as an organic zirconium compound like zirconium isopropoxide and zirconium butoxide, or a zirconium tetrachloride [0036]Organic niobium compounds, such as a molybdenum compound of halogenides, such as a tungsten compound of halogenides, such as organic hafnium compounds, such as an organic tantalum compound like pentaethyl tantalum, and hafnium ethoxide, and tungsten chloride, and a molybdenum chloride, and niobium ethoxide [0037]When applying a CVD method, the following compound can be mentioned as a compound of the element G used as a raw material.

[0038]Boron compound arsines, such as borane, triethyl boron, and trimethyl boron, Silicon compounds, such as antimony compound Silang, such as arsenide triethylantimony, such as triethylarsenic and trimethyl arsenic, and trimethyl antimony, a disilane, a tetramethylsilane, a tetraethyl silane, a silicon tetrachloride, a tetraethoxysilane, and a tetramethoxy silane [0039]Germanium hydride, tetramethyl germanium, tetraethyl germanium, Germanium compound hydrogenation telluriums, such as germanium tetrachloride, tetraethoxygermanium, and tetramethoxy germanium, Phosphorus compounds, such as tellurium compound phosphorus oxychloride, such as a tetramethyl tellurium, a tetraethyl tellurium, tellurium tetrachloride, a tetraethoxytellurium, and a tetramethoxy tellurium [0040]When applying a CVD method, the



following compound can be mentioned as a compound of the element C used as a raw material.

[0041]Organic bismuth compounds, such as bismuth ethoxide, bismuth acetylacetonato, and screw dipivaloyl bismuth, Or organic scandium compounds, such as bismuth compound scandium ethoxide of halogenides, such as a bismuth chloride, scandium acetylacetonato, and a screw dipivaloyl scandium, or a scandium compound of halogenides, such as scandium chloride

[0042]Organic antimony compounds, such as antimony ethoxide, antimony acetylacetonato, and screw dipivaloyl antimony, Or organic chromium compounds, such as antimony compound chromium ethoxide of halogenides, such as an antimony chloride, chromium acetylacetonato, and screw dipivaloyl chromium, or a chromium compound of halogenides, such as chromium chloride

[0043]Organic thallium compounds, such as thallium ethoxide, thallium acetylacetonato, and screw dipivaloyl thallium, or a thallium compound of halogenides, such as a thallium chloride

[0044]It is a general formula (1) about these compounds. [Formula 4]the inside of a formula, and A -- Ca, Sr, Ba, Pb, La, Ce, Pr, Nd, and Pm. One or two or more elements which were chosen from Sm, Eu, Gd, Tb, Dy, Ho, Er, Tm, Yb, Lu, and Y, One or two or more elements in which 1 or two or more elements in which C was chosen from Bi, Sc, Sb, Cr, and Tl, and R were chosen from Ti, Ta, Hf, W, Mo, Nb, and Zr, and G are one sort or two sorts or more of elements chosen from B, As, Sb, Si, germanium, Te, and P. s, a, and b express the real number, and are in the range of  $0.3 < s \leq 0.95$ ,  $1/19 \leq a \leq 2$ , and  $0.5 \leq b/a \leq 7$ . s expresses the molar fraction of a crystal phase. u, v, w, and x are the real numbers decided that the whole electric charge is set to 0. y, r, and z express the number of oxygen, and it is  $y = 1.5$ , when A is divalent and  $y = 1$  and A are trivalent, It is  $r = 3$ , when C is trivalent,  $r = 1.5$  and C are tetravalence,  $r = 2$  and C are pentavalence and  $r = 2.5$  and C are 6 values, It is  $z = 2.5$ , when G is trivalent,  $z = 1.5$  and G are tetravalence and  $z = 2$  and G are pentavalence. An oxide film or powder can be obtained by mixing so that it may become, conveying with gas, such as argon, nitrogen, and oxygen, and making it deposit on a substrate or in a reactor.

[0045]A method of mixing each compound made to evaporate with an individual vaporizer in the middle of piping has good controllability so that it may usually be used, but beforehand, a mixing method may be evaporated here, after mixing all the raw materials as a compound with almost equal steam pressure. A flow of gas is between 10-l. part grades for /from 100 ml according to a production rate.

[0046]A sputtering container is corrosion-resistant and can be easy to carry out sputtering on the open air and intercepted conditions. Although a container wall or a substrate may be heated at 300-900 \*\*, when heating, a crystal phase deposits directly. Since it is generally amorphous when not heating, it heats, after picking out this thin film from a sputtering system, and a crystal is deposited. A heating method is mentioned later.

[0047]In the case of vacuum deposition, Ca, Sr, Ba, Pb, La, Ce, Pr, Nd, Pm, Sm, Eu, Gd, Tb, Ho, Er, Tm, Yb, Lu, Y, Bi, Sc, Sb, Cr, Tl, Ti, Ta, Hf, W, Mo, Nb, These alloys mixed to a presentation of a request which gives Zr, B, As, Si, germanium, Te, simple substance metal of P, or a constituent expressed with a general formula (1) are heated with a tungsten boat, an electron beam, etc., and a substrate is deposited. When an obtained thin film is an alloy, it processes heating under an oxidizing atmosphere etc. and converts into an oxide. A heating method is mentioned later.

[0048]A compound of the element A meltable to an organic solvent and this organic solvent as a dielectric formation solution, A method of manufacturing a dielectric constituent is performed as follows, for example by applying this dielectric formation solution on a substrate, forming a thin film using a solution which consists of a compound of the element R, a compound of the element

C, and a compound of the element G, and subsequently heat-treating this thin film.

[0049]In a method of using meltable metallic compounds for an organic solvent, the following compound can be used as a compound of the element A, for example. As a lead compound, diethoxy lead, diisopropoxy lead, dimethoxyethoxy lead, lead acetyl ASENATO, lead formate, lead acetate, etc. are mentioned, for example. As a barium compound, dimethoxybarium, diethoxybarium, diisopropoxy barium, dibutoxybarium, barium acetate, barium acetylacetonato, etc. are mentioned, for example.

[0050]As a magnesium compound, dimethoxymagnesium, diethoxymagnesium, diisopropoxy magnesium, dibutoxymagnesium, etc. are mentioned, for example. As a lime compound, dimethoxycalcium, diethoxycalcium, diisopropoxy calcium, dibutoxycalcium, etc. are mentioned, for example.

[0051]As a strontium compound, dimethoxystrontium, diethoxystrontium, diisopropoxy strontium, dibutoxystrontium, etc. are mentioned, for example.

[0052]as a lanthanum compound -- for example, a trimethoxy lantern and TORIE -- an ibis -- a silane tongue, a triisopropoxy lantern, and TORIBU -- an ibis -- a silane tongue, a lanthanum chloride, etc. are mentioned. As an yttrium compound, trimethoxy yttrium, TORIETOKISHI yttrium, triisopropoxy yttrium, TORIBUTOKISHI yttrium, a yttrium chloride, etc. are mentioned, for example.

[0053]It is \*\*\*\*\* to use the following compound as a compound of the element R in a method of using meltable metallic compounds for an organic solvent, for example. As a titanium compound, tetramethoxy titanium, tetraethoxy titanium, tetra isopropoxy titanium, tetrabutoxy titanium, titanium tetrachloride, etc. are mentioned, for example.

[0054]As a zirconium compound, a tetramethoxy zirconium, a tetraethoxyzirconium, a tetra isopropoxy zirconium, tetra butoxyzirconium, a zirconium tetrachloride, etc. are mentioned, for example. As a tantalum compound, pentamethoxy tantalum, tongue TARUZU acetylacetonato, tantalum pentachloride, etc. are mentioned, for example.

[0055]As a niobium compound, a pentamethoxy niobium, a pentaethoxy niobium, a penta isopropoxy niobium, a pentabutoxy niobium, a chloridation niobium, etc. are mentioned, for example. As a tantalum compound, pentamethoxy tantalum, pentaethoxy tantalum, penta isopropoxy tantalum, pentabutoxytantalum, a tantalum chloride, etc. are mentioned, for example.

[0056]As a tungsten compound, for example, pentamethoxy tungsten, pentaethoxy tungsten, penta isopropoxy tungsten, pentabutoxytungsten, tungsten chloride, etc. are mentioned.

[0057]In a method of using meltable metallic compounds for an organic solvent, the following compounds can be used as a compound of the element G, for example.

[0058]As a boron compound, way acid triethyl, way acid trimethyl \*\* trimethoxy ethoxy boron, way acid triphenyl, way acid, etc. are mentioned, for example. As arsenide, arsenic acid triethyl, arsenic acid trimethyl \*\* trimethoxy ethoxyarsenic, and triphenyl arsenate are mentioned, for example.

[0059]As an antimony compound, antimonic acid triethyl, antimonic acid trimethyl \*\* trimethoxy ethoxyantimony, and triphenyl antimonate are mentioned, for example. As a silicon compound, a tetramethoxy silane, a tetraethoxysilane, tetra isopropoxysilane, tetra butoxysilane, a silicon tetrachloride, etc. are mentioned, for example.

[0060]As a germanium compound, tetramethoxy germanium, tetraethoxygermanium, tetra isopropoxy germanium, tetrabutoxygermanium, germanium tetrachloride, etc. are mentioned, for example. As a tellurium compound, a tetramethoxy tellurium, a tetraethoxytellurium, a tetra isopropoxy tellurium, a tetrabutoxytellurium, tellurium tetrachloride, etc. are mentioned, for

example. As phosphorus compounds, trimethoxy phosphonyl, phosphorus oxychloride, etc. are mentioned, for example.

[0061]In a method of using meltable metallic compounds for an organic solvent, the following are mentioned as a compound of the element C, for example.

[0062]Organic bismuth compounds, such as bismuth ethoxide, bismuth acetylacetonato, and screw dipivaloyl bismuth, or a bismuth compound of halogenides, such as a bismuth chloride.

Organic scandium compounds, such as scandium ethoxide, scandium acetylacetonato, and a screw dipivaloyl scandium, or a scandium compound of halogenides, such as scandium chloride.

[0063]An antimony compound of halogenides, such as organic antimony compounds, such as antimony ethoxide, antimony acetylacetonato, and screw dipivaloyl antimony, or an antimony chloride. Organic chromium compounds, such as chromium ethoxide, chromium acetylacetonato, and screw dipivaloyl chromium, or a chromium compound of halogenides, such as chromium chloride.

[0064]Organic thallium compounds, such as thallium ethoxide, thallium acetylacetonato, and screw dipivaloyl thallium, or a thallium compound of halogenides, such as a thallium chloride.

[0065]A lead compound, a barium compound which were described above as an organic solvent used, A magnesium compound, a lime compound, a strontium compound, a lanthanum compound, An yttrium compound, a bismuth compound, a titanium compound, a zirconium compound, Although what kind of organic solvent may be used as long as it dissolves a niobium compound, a tantalum compound, a tungsten compound, a boron compound, arsenide, an antimony compound, a silicon compound, a germanium compound, a tellurium compound, phosphorus compounds, etc., [0066]Preferably Methanol, ethanol, propanol, butanol, a pentanol, Alcohols, such as methoxy ethanol and ethoxyethanol, benzene, Aromatic hydrocarbon, such as toluene and xylene, pentane, hexane, heptane, Ether, such as aliphatic hydrocarbon, such as octane, dioxane, and a tetrahydrofuran, Ketone, such as acetone, methyl ethyl ketone, and a diethyl ketone, methyl acetate, Carboxylate, such as ethyl acetate and ethyl formate, an acetylacetone, Amide, such as beta-diketones, such as a benzoylacetone and dibenzoylacetone, dimethylformamide, and dimethylacetamide, is mentioned, and independence or two sorts or more can also be used together for these organic solvents.

[0067]A method to which dissolve a compound of said element A, a compound of the element B, a compound of the element C, and a compound of the element G into an organic solvent, and mix at a room temperature as a preparing method of a dielectric formation solution, or said each compound is made to react under heating in an organic solvent is mentioned. Coating liquid can be polymerized in order to raise membranous quality of a coating film. In that case, a solution which diluted water or water of a quantity suitable during mixing or a reaction with a suitable ratio in the above-mentioned organic solvent may be added.

[0068]Although temperature changes with kinds of compound when heating in an organic solvent, and not necessarily limited, it is 60-150 °C in general.

[0069]Although concentration of metallic compounds in a dielectric formation solution changes also with kinds of these metallic compounds, it is converted into an oxide and is more preferably applied at 10 to 50 % of the weight five to 80% of the weight.

[0070]In a dielectric formation solution, carboxylic acid (carbon numbers 6-20) for stabilization, glycol, amine, etc. can be added. A surface-active agent of polymeric materials, such as polyol and ethyl cellulose, methyl cellosolve, ethylcellosolve, an acetylacetone, a high boiling point compound like glycerin, the Nonion system, or an anionic system, etc. can be added, for example for improvement in the workability of a dielectric formation solution.

[0071]colloidal one containing a compound of the element A, a compound of the element C, a compound of the element B, and a compound of the element G -- sol, this colloidal one -- sol -- in a manufacturing method of a dielectric constituent of this invention heat-treated at temperature which each inner compound may convert into an oxide -- colloidal one -- colloidal one produced by carrying out partial hydrolysis of the aforementioned dielectric formation solution as sol -- sol can be used. colloidal one of a compound of the element A, a compound of the element C, a compound of the element B, and a compound of the element G -- colloidal one produced by mixing sol -- sol can also be used.

[0072]thus, a dielectric formation solution obtained or colloidal one -- as the method of using sol -- these dielectric formation solutions or colloidal ones -- a method of heat-treating, after fabricating to a method of heat-treating and producing a film after applying sol on a substrate and forming a thin film, and bulk is mentioned. this dielectric formation solution or colloidal one -- a method of heat-treating, after drying or hydrolyzing sol and obtaining powder is also employable.

[0073]As the film production method to a substrate, publicly known coating methods, such as dip coating, a spray method, the spinner method, and brush painting, can be used. Thus, an obtained thin film can also be dried further if needed.

[0074]a time of fabricating on an object of bulk -- said dielectric formation solution carried out or colloidal one -- it can carry out by publicly known methods, such as a slip casting, a colloidal press, and the tape cast, using sol. If needed, gel powder produced by hydrolyzing and drying a dielectric formation solution prepared as mentioned above with further an excessive amount of water can also be fabricated by methods, such as a dry type press, a slip casting, and tape casting, after carrying out temporary quenching, grinding and.

[0075]Hydrolysis may be performed by making it react to a solution containing an excessive amount of more than twice [ at least ] as many water as the number of metal mols contained in a solution in this compound solution, or water, or only neglecting it in the air and making it react to moisture in the air. Thus, oxide precursor powder can be obtained.

[0076]As the method of gelling, desiccation is mentioned first. Generally, when carrier fluid is lost, repulsive force of sol is lost and it is gelled. This method is applicable to all the sol. By addition of pH adjustment or a salt, even if it suppresses Coulomb repulsion, it gels. Gelling acid sol by addition of ammonia, caustic alkali of sodium, etc. in a neutral-alkaline region, for example, alkaline sol gels acid, such as chloride and nitric acid, by addition in neutral-acidic regions. By adding salts, such as a chloride of potash, a calcium chloride, and an aluminium nitrate, if electrolytic concentration of colloid solution is made high, Coulomb repulsion will be covered and it will become small, and it gels. Gelling can be caused even if it adds organic solvents, such as isopropanol and acetone, etc.

[0077]Thus, as soon as it carries out temporary quenching, a compound of the element A, the element C, and the element G obtains desiccation and/or powder of moderate size of as [ whose a field of each compound is 0.1 micrometer or less ] for obtained gel or settlings and it makes this into a paste raw material, it can fabricate by a publicly known method. A method of fabricating like the above as a method of fabricating to a method and bulk which produce a film on a substrate as coating liquid is mentioned.

[0078]It mixes using meltable metallic compounds in water, and the following compound is mentioned as a compound of the element A in a method of making it coprecipitating if needed and obtaining a mixture.

[0079]As a lead compound, a lead nitrate, lead acetate, a lead chloride, etc. are mentioned, for

example. As a barium compound, a barium nitrate, barium acetate, barium chloride, etc. are mentioned, for example. As a lime compound, a calcium nitrate, calcium acetate, a calcium chloride, etc. are mentioned, for example.

[0080]As a strontium compound, strontium nitrate, strontium acetate, a strontium chloride, etc. are mentioned, for example. As a lanthanum compound, a lanthanum nitrate, an acetic acid lanthanum, a lanthanum chloride, etc. are mentioned, for example. As an yttrium compound, nitric acid yttrium, yttrium acetate, a yttrium chloride, etc. are mentioned, for example.

[0081]As a meltable R compound, the following compound is mentioned to water, for example. As a titanium compound, nitric acid titanyl, acetic acid titanyl, tetrachloride titanium, titanyl sulfate, etc. are mentioned, for example. As a JIRUKOUMU compound, zirconium nitrate, acetic acid zirconyl, a zirconium tetrachloride, zirconium sulfate, etc. are mentioned, for example.

[0082]As a niobium compound, nitric acid niobium, acetic acid niobium, niobium chloride, sulfuric acid niobium, etc. are mentioned, for example. As a tantalum compound, nitric acid tantalum, acetic acid tantalum, a tantalum chloride, sulfuric acid tantalum, etc. are mentioned, for example. As a tungsten compound, nitric acid tungsten, acetic acid tungsten, tungsten chloride, sulfuric acid tungsten, etc. are mentioned, for example.

[0083]As a meltable G compound, the following compound is mentioned to water, for example. As a boron compound, way acid is mentioned, for example. As arsenide, arsenic acid is mentioned, for example. As an antimony compound, antimonite acid, nitric acid antimony, antimony acetate, chloridation CHIMON, antimony sulfate, etc. are mentioned, for example.

[0084]As a silicon compound, a silicon tetrachloride, silicic acid, etc. are mentioned, for example. As a germanium compound, germanium tetrachloride, nitric acid germanium, acetic acid germanium, etc. are mentioned, for example. As a tellurium compound, tellurium tetrachloride, a nitric acid tellurium, etc. are mentioned, for example. As phosphorus compounds, phosphoric acid etc. are mentioned, for example.

[0085]It is a general formula (1) about the above-mentioned compound meltable to water. [Formula 5]

$$s(\text{Au} \quad \text{Cv} \quad \text{Rw} \quad \text{Ox})-(1-s)(\text{AOy} \quad -\text{bCOr} \quad -\text{aGOz})(1)$$
  
the inside of a formula, and A -- Ca, Sr, Ba, Pb, La, Ce, Pr, Nd, and Pm. One or two or more elements which were chosen from Sm, Eu, Gd, Tb, Dy, Ho, Er, Tm, Yb, Lu, and Y, One or two or more elements in which 1 or two or more elements in which C was chosen from Bi, Sc, Sb, Cr, and Tl, and R were chosen from Ti, Ta, Hf, W, Mo, Nb, and Zr, and G are one sort or two sorts or more of elements chosen from B, As, Sb, Si, germanium, Te, and P. s, a, and b express the real number, and are in the range of  $0.3 < s \leq 0.95$ ,  $1/19 \leq a \leq 2$ , and  $0.5 \leq b/a \leq 7$ . s expresses the molar fraction of a crystal phase. u, v, w, and x are the real numbers decided that the whole electric charge is set to 0. y, r, and z express the number of oxygen, and it is  $y = 1.5$ , when A is divalent and  $y = 1$  and A are trivalent, It is  $r = 3$ , when C is trivalent,  $r = 1.5$  and C are tetravalence,  $r = 2$  and C are pentavalence and  $r = 2.5$  and C are 6 values, It is  $z = 2.5$ , when G is trivalent,  $z = 1.5$  and G are tetravalence and  $z = 2$  and G are pentavalence. Mix so that it may become, and convey with gas, such as argon, nitrogen, and oxygen, it is made to deposit on a substrate or in a reactor, and a thin film or a substrate is obtained.  
[0086]Thus, a method of fabricating as a method of fabricating using a dielectric formation solution obtained to a method and bulk which produce a film on a substrate as coating liquid is mentioned. moreover -- obtaining settlings by generation of pH adjustment and a poorly soluble salt, etc. -- these settlings -- desiccation -- and/or -- carrying out temporary quenching -- the element A. As soon as a compound of R, C, and G obtains powder of moderate size of as [

whose a field of each compound is 0.1 micrometer or less ] and makes this a paste raw material, it can fabricate in desired shape with a slip casting, a dry type press, etc. [0087]Although pH for making precipitation generate changes with metal, generally it is preferred. [ of pH 3 or more and neutral vicinity ] However, about pH 11 or more are needed for alkaline earth metal ion, such as Sr, and alkali metal ion does not precipitate in pH adjustment. Therefore, at the time of alkaline earth metal ion, formation of a poorly soluble salt is preferred, and precipitation produces it by addition of oxalic acid, sulfuric acid, citrate, etc. It is made to precipitate due to the fall of solubility by removing water from a system at the time of alkali metal ion.

[0088]As the film production method to a substrate, publicly known coating methods, such as dip coating, a spray method, the spinner method, and brush painting, can be used. Thus, an obtained thin film is dried further if needed. When fabricating on an object of bulk, a compound solution obtained by the above-mentioned may be fabricated by publicly known methods, such as a slip casting, a colloidal press, and the tape cast.

[0089]sputtering described until now, vacuum evaporation, CVD, an organic metallic compound, and colloidal ones -- as a drying method of powder obtained from sol, water soluble metallic compounds, etc., publicly known drying means, such as a rotating evaporator, a flaking machine, and an air bus, can be used. In the case of a publicly known constant temperature dryer etc., temperature of desiccation can be performed at temperature of about 100-300 \*\*, and if temporary quenching is required, it will be performed by an electric furnace, gas furnace, etc. at temperature of about 300-900 \*\*.

[0090]As a powdered burning method, known means, such as electrical resistance heating, plasma, high frequency, and laser, can be used. Although calcination temperature changes with presentations, it is necessary to make it into temperature beyond crystallization of a crystal phase, and it is usually 500-1000 \*\* more preferably 400-1200 \*\*. If an organic matter does not decompose at less than 400 \*\*, crystallization does not advance and it exceeds 1200 \*\*, change of a presentation by evaporation of an element, etc. is caused and it is not desirable.

[0091]A firing environments can be calcinated also in oxygen environment, when a crystal phase is easy to be returned among air, inactive gas, and reducing atmosphere. Thus, obtained powder is suitably ground by publicly known methods, such as a ball mill, a vibration mill, a stone milling machine, and attritor, is used as a paste raw material, or is fabricated by publicly known methods, such as a dry type press, a hydrostatic pressure press, and a slip casting.

[0092]Thus, obtained powder is a mixture of many deposit detailed single crystals and a glass component. In order to separate only a detailed single crystal from now on, after dissolving a glass component in water, dilute acid, dilute-alkali solution, etc., filtration, centrifugal separation, or other means can perform. As acid, nitric acid, fluoric acid, chloride, sulfuric acid, acetic acid, etc. are mentioned, for example. As alkali, an ammonia solution, caustic alkali of sodium, caustic potash, etc. are mentioned. These are diluted and used for 5 to 50% of concentration.

[0093]A substrate used for this invention has smooth nature, and if there is necessary heat resistance at the time of heat treatment in a process, anythings can use it. For example, glass or a ceramic substrate, a metallic foil, a semiconductance board, etc. which were covered with a glass substrate, a ceramic substrate, a metal thin film, or a conductive oxide are mentioned.

[0094]Specifically Substrates, such as silica glass, alumina, zirconia, mica, and silicon, Gold, platinum, palladium, silver, copper, chromium, titanium, aluminum, Tantalum, golden-chromium, palladium silver, platinum-tantalum, platinum-titanium, Metal substrates, such as

substrates, such as silica glass covered with thin films, such as indium oxide which doped tin or antimony, alumina, zirconia, mica, and silicon, gold, platinum, palladium, silver, copper, nickel, nickel chromium, and aluminum, are mentioned.

[0095]As mentioned above, as a heating method of a film produced by applying to a substrate, or mold goods, known means, such as electrical resistance heating, plasma, high frequency, and laser, can be used. Although cooking temperature changes with manufacturing methods, in the case of sputtering process, a CVD method, etc., a film is produced, heating a substrate at about 200-700 \*\*, and next heat treatment may be unnecessary, and also may carry out heat treatment of about 500-900 \*\*. In the case of vacuum deposition, generally, heat treatment of about 500-900 \*\* is performed by the inside of the air, or an oxidizing atmosphere.

[0096]metallic compounds meltable to an organic solvent, metallic compounds meltable to water, and colloidal one -- in the case of a method of using sol, although it changes with concentration of metallic compounds in a solvent, a kind of solvent, kinds of substrate, etc., It is necessary to make it temperature beyond crystallization of a dielectric, and about 400-1200 \*\* is usually about 500-1000 \*\* preferably. When an organic matter does not decompose at less than 400 \*\*, crystallization does not advance and it exceeds 1200 \*\*, change of a presentation by evaporation of an element, etc. is caused and it is not desirable.

[0097]In order to make it sinter precisely in bulk powder and a Plastic solid, it is based on a presentation, but 500-1000 \*\* sintering is performed as heat-treatment. Although any in air, inactive gas, and reducing atmosphere may be sufficient as atmosphere of heat-treatment, when a dielectric is easy to be returned, it can be heat-treated in oxygen environment (calcination).

[0098]

[Example]Hereafter, this invention is not limited by the following example although an example explains this invention still in detail.

[0099]After forming an Au electrode in measurement of dielectric characteristics by 100 spatters at a dielectric film, it measured with the impedance analyzer (YHP4275A: made by YOKOGAWA Hewlett Packard). The insulating rate was made into the number of the electrodes which have not inner-short-circuited 100 electrodes. Direct current voltage was impressed and dielectric breakdown voltage was measured with the superinsulation ohm-meter (YHP4329A: made by Yokogawa Hewlett Packard). The check of the crystal phase was based on the powder X diffraction, and crystal form was based on the scanning electron microscope.

[0100]Example 1 strontium diethoxide, bismuth ethoxide, tantalum penta isopropoxide, and a tetraethoxysilane, It prepared in proportion like 0.9( $\text{SrBi}_2\text{Ta}_2\text{O}_9$ )-0.1 ( $\text{SrO-Bi}_2\text{O}_3\text{-SiO}_2$ ), and dissolved into the 1:1 (weight ratio) mixed solvents of isopropanol toluene, and 10% of the weight of the dielectric formation solution was compounded by oxide conversion.

[0101]With a spinner this dielectric formation solution on condition of 2500 rotations on the Si substrate covered with the Pt/Ti (0.5/0.05 micrometer) film After spreading, Heat-treatment in oxygen was performed at 450 \*\* for 30 minutes, the above-mentioned spreading and heat-treatment (calcination) were repeated twice, it calcinated in the atmosphere at 600 \*\* eventually for 1 hour, and thickness obtained the precise and transparent filmy dielectric which is 0.2 micrometer. Generation of  $\text{SrBi}_2\text{Ta}_2\text{O}_9$  was checked by the X diffraction. A dielectric constant is 140, spontaneous polarization is  $5\text{microC/cm}^2$ , and the insulating rate did not produce the dielectric breakdown to 30V 100%.

[0102]Example 2 lead diethoxide, niobium penta isopropoxide, bismuth ethoxide, and trimethyl boron, It prepares in proportion like 0.7( $\text{PbBi}_2\text{Nb}_2\text{O}_9$ )-0.3 ( $\text{PbO-0.5Bi}_2\text{O}_3\text{-0.25B}_2\text{O}_3$ ), It dissolved into the 1:1 (weight ratio) mixed solvents of isopropanol toluene, and the formation solution was

prepared by oxide conversion in the detailed single-crystal-powder end of 15 % of the weight. Subsequently it dried at 130 °C except for the solvent for 30 minutes by the rotary evaporator from this liquid, and gel powder was obtained. This powder was held at 800 °C for 1 hour, and the end of detailed single crystal powder was deposited. This was filtered after washing in 1 N of 40 more °C nitric acid, and only the detailed single crystal was obtained. Generation of the crystal phase was checked according to the X diffraction. [0103]A thin film capacitor can be obtained by forming the dielectric constituent of this patented invention film on glass [ which was covered with glass or the ceramic substrate, the metal thin film, or the conductive oxide thin film ], ceramic substrate, metallic foil, or semiconductance board \*\*.

[0104]

[Effect of the Invention]According to the method of this invention, a dielectric constituent as compared with the method which slurs the conventional dielectric powder and is obtained by a doctor blade method etc., a manufacturing cost is cheap, and high insulation and reliable is obtained. Since it is obtained without what has specific inductive capacity high the rate of a crystal phase compared with the crystallized glass which goes via the conventional melting and high passing through high temperature processing like melting, high-capacity-izing is possible. As for the dielectric constituent of this invention, improvement in an insulating property and reduction of the rate of inferior goods are raised. Since reliability and an insulating rate have a difficulty conventionally especially by this, the way of utilization is paved for the ferroelectric random-access memory which application did not follow, and the industrial value is large.

## TECHNICAL PROBLEM

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[Problem(s) to be Solved by the Invention]By increasing the rate of a ferroelectric crystal phase, this invention demonstrates the characteristic, gives a precise organization at low temperature rather than a crystal phase independent case, and relates to a good dielectric constituent, and its insulating manufacturing method and use. It is related with the dielectric constituent obtained by the manufacturing method more compoundable at low temperature especially, and this manufacturing method, and its use



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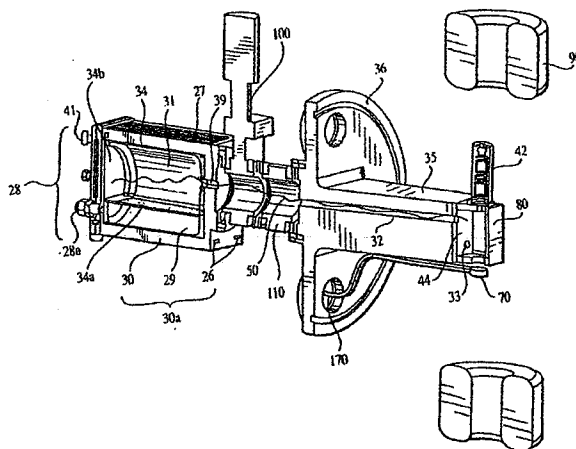
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(54) Title: ION IMPLANTATION SYSTEM AND CONTROL METHOD



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(57) Abstract: Ion implantation with high brightness, ion beam by ionizing gas or vapor, e.g. of dimers, or decaborane, by direct electron impact ionization adjacent the outlet aperture (46, 176) of the ionization chamber (80; 175)). Preferably: conditions are maintained that produce a substantial ion density and limit the transverse kinetic energy of the ions to less than 0.7 eV; width of the ionization volume adjacent the aperture is limited to width less than about three times the width of the aperture; the aperture is extremely elongated; magnetic fields are avoided or limited; low ion beam noise is maintained; conditions within the ionization chamber are maintained that prevent formation of an arc discharge. With ion beam optics, such as the batch implanter of Figure (20), or in serial implanters, ions from the ion source are transported to a target surface and implanted; advantageously, in some cases, in conjunction with acceleration-deceleration beam lines employing cluster ion beams. Also disclosed are electron gun constructions, ribbon sources for electrons and ionization chamber configurations. Forming features of semiconductor devices, e.g. drain extensions of CMOS devices, and doping of flat panels are shown.



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## ION IMPLANTATION SYSTEM AND CONTROL METHOD

### TECHNICAL FIELD

This invention relates to ion sources, implantation, and more particularly to ion implantation with high brightness, low emittance ion sources, acceleration-deceleration transport systems and improved ion source constructions.

### BACKGROUND

5 The following patent applications, herein incorporated by reference, describe the background of this invention: Provisional Patent Application Serial Number 60/267,260, inventor Thomas N. Horsky, filed February 7, 2001, entitled Ion Source for Ion Implantation; Provisional Patent Application Serial Number 60/257,322, inventor Thomas N. Horsky, filed  
10 December 19, 2000, entitled Ion Implantation; PCT Application Serial Number US00/33786, inventor Thomas N. Horsky, filed December 13, 2000, entitled Ion Implantation Ion Source, System and Method and filed November 30, 2000, having the same reference. The referenced patent, for U. S. Purposes, is a continuation in part of my U. S. Provisional Applications 60/170,473 filed December 13, 1999 60/170,473, now expired.

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#### Background: Ion Implantation

Ion implantation has been a key technology in semiconductor device manufacturing for more than twenty years, and is currently used to fabricate the p-n junctions in transistors, particularly for CMOS devices such as memory and logic chips. By creating positively-charged  
20 ions containing the dopant elements (for example,  $^{75}\text{As}$ ,  $^{11}\text{B}$ ,  $^{115}\text{In}$ ,  $^{31}\text{P}$ , or  $^{121}\text{Sb}$ ) required for fabricating the transistors in, for example, silicon substrates, the ion implanters can selectively control both the energy (hence implantation depth) and ion current (hence dose) introduced into the transistor structures. Ion implanters have traditionally used ion sources which generate ribbon beams of up to about 50mm in length; these beams are transported to the substrate and the  
25 required dose and dose uniformity is accomplished by electromagnetic scanning of the ribbon across the substrate, mechanical scanning of the substrate across the beam, or both.

With the recent advent of 300mm-diameter silicon substrates in chip manufacturing, there has been a keen interest in producing ribbons of larger extent than has heretofore been possible with conventional ion implanter designs, in order to increase wafer throughput when using these larger substrates. Taller ribbon beams enable higher dose rates, since more ion current can be transported through the implanter beam line due to reduced space charge blowup of the extended ribbon beam. Many of these new implanter designs also incorporate a serial (one wafer at a time) process chamber, which offers high tilt capability (*e.g.*, up to 60 degrees from substrate normal). The ion beam is typically electromagnetically scanned across the wafer, which is mechanically scanned in the orthogonal direction, to ensure dose uniformity. In order to meet implant dose uniformity and repeatability specifications, the ion beam must have excellent angular and spatial uniformity (angular uniformity of beam on wafer of <1 deg, for example). The production of beams possessing these characteristics imposes severe constraints on the beam transport optics of the implanter, and the use of large-emittance plasma-based ion sources often results in increased beam diameter and beam angular divergence, causing beam loss during transport due to vignetting of the beam by apertures within the beam line. Currently, the generation of high current ion beams at low (<2keV) energy is problematic in serial implanters, such that wafer throughput is unacceptably low for certain low-energy implants (for example, in the creation of source and drain structures in leading-edge CMOS processes). Similar transport problems exist for batch implanters (processing many wafers mounted on a spinning disk), particularly at low beam energies.

While it is possible to design beam transport optics which are nearly aberration-free, the beam characteristics (spatial extent and angular divergence) are nonetheless determined to a large extent by the emittance properties of the ion source (*i.e.*, the beam properties at ion extraction which determine the extent to which the implanter optics can focus and control the beam as emitted from the ion source). Arc-discharge plasma sources which are currently in use have poor emittance, and therefore limit the ability of ion implanters to produce well-focused, collimated, and controllable ion beams.

#### Background: Ion Implantation Sources

The standard ion source technology of the implanter industry is the Enhanced Bernas source. As illustrated in Fig. 1, this is an arc discharge source which incorporates a reflex

geometry: a hot filament cathode immersed in the ionization chamber (where the dopant feed gas resides) emits thermionic electrons confined by a magnetic field, and are reflected from an anticathode located at the opposite end of the chamber. Thus, the electrons execute helical trajectories between the cathode and anticathode, and generate a high-density plasma (on the order of  $10^{12}$  ions/cm<sup>2</sup>). This so-called "plasma column" is parallel to an ion extraction aperture slot from which the ions are extracted by beam-forming optics. By generating a high-density plasma and sustaining discharge currents as high as 10A, the Enhanced Bernas source efficiently dissociates tightly-bound molecular species such as BF<sub>3</sub>. However, the emittance of this source is large due to the following plasma-related effects:

- 1) The plasma potential (typically about 5 V) introduces a random component of velocity to the ions, which directly translates into increased angular dispersion of the extracted ions.
- 2) The temperature of the ions and electrons within the plasma can reach 10,000 K, introducing a thermal velocity which adds to (1), and also introduces an energy spread of several eV to the ions (according to a Maxwell-Boltzmann distribution), making the beam exhibit chromatic aberrations.
- 3) Coulomb scattering between the ions in the plasma introduces an additional non-thermal spread in the ion energy.
- 4) A high extracted current density is needed due to a predominance of unwanted ions (*i.e.*, fragments such as BF<sup>+</sup>, BF<sub>2</sub><sup>+</sup>, and F<sup>-</sup> in a BF<sub>3</sub> plasma), increasing space-charge forces at extraction and causing emittance growth.
- 5) The presence of a strong magnetic field, required for operation of all arc discharge sources, causes beam deflection and hence further emittance growth of the extracted ion beam, especially at low beam energy.
- 6) High-frequency noise present in the plasma is propagated into the beam as high-frequency fluctuations in beam current and in beam potential. This time-varying beam

potential makes charge compensation in the beam plasma difficult to maintain, since it can cause a significant steady or even abrupt loss of the low-energy electrons which normally orbit the beam (being trapped by the positive beam potential), leading to space-charge blowup of the ion beam.

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- 7) The ion extraction aperture cannot be significantly elongated beyond, say, 75mm (typical length is between 20mm and 50mm), since this requires a significant elongation of the plasma column. Bernas sources become unstable if the separation between cathode and anticathode is large, and larger cathode-anticathode separations requires a much higher arc discharge current in order to maintain a stable plasma, increasing power consumption.

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#### Background: Ion Deceleration

Ion implanters of conventional design exhibit poor transmission of low-energy boron at energies below a few keV, with the result that these boron beam currents are too small to be cost-effective in manufacturing semiconductor chips using sub-0.18 micron design rules. Next-generation implanters which have been long-in-planning, and which were introduced into the capital equipment market within the last few years incorporate a different principle of ion optics, attempting to solve this low-energy transmission problem. To counter the effects of space charge repulsion between ions, which dominates beam transport at low energies, a so-called "decel" (i.e. deceleration) approach has been developed to allow the ion beam to be extracted and transported through the implanter at a higher energy than the desired implantation energy so that space charge effects are not so detrimental, and by introducing a deceleration stage late in the beam-line, but upstream from the wafer target, reducing the ions to the desired implant energy as the ions approach the wafer target. For example, the ion beam can be extracted and transported at 2 keV, but decelerated to 500 eV before the ions reach the wafer, achieving a much higher beam current than is obtainable with space-charge-limited beams in beam lines of a conventional, non-deceleration design. Unfortunately, this method of employing deceleration still has posed significant problems which have detracted from its production-worthiness. As the ion beam passes through the deceleration lens to the wafer, the ion beam becomes spatially non-uniform to a great degree, and the ions impact the substrate with a wide distribution of angles of incidence relative to the wafer surface, with potential so-called channeling effects. The spatial

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and angular dose uniformity of a decelerated beam is typically much worse than in conventional, non-deceleration ion implantation. This makes it difficult to achieve a uniform dose, and introduces the need to take other steps which affect cost and throughput. Compounding the problem is the fact that the grossly non-uniform profile of the ion beam also interferes  
5 significantly with accurate dosimetry of the implant, since ion implanters typically sample only a portion of an ion beam at or behind the plane of the wafer. Dosimetry is used to control the degree of implant within a desired range. The accuracy problems with dosimetry produced by partial sampling of a severely extended and non-uniform distribution of ion current in the beam of an acceleration/deceleration implantation system thus also affects the accuracy of the implant,  
10 the capital cost of the implant system, the quality of the wafers, and throughput of the system.

Another, quite different approach for shallow, low energy implants has been proposed (but not implemented in current production) it is that of using molecular ion beams (having clusters of the dopant atom of interest) in conventional implanters that do not have a deceleration stage. Decaborane is one example of such a molecular material.

15 Chip manufacturers are currently moving to 300mm-diameter silicon substrates for fabricating Complimentary Metal-Oxide-Semiconductor (CMOS) memory and logic chips to reduce manufacturing costs over that attainable with 200mm substrates. Though such a shift in wafer size requires building new factories populated with new semiconductor manufacturing tools for processing the larger-diameter wafers, the potential cost reduction per die is about a  
20 factor of two. Thus, the expenditure of billions of US dollars for these facilities has been hoped to enable lower-cost manufacturing, and ultimately a huge competitive advantage for volume manufacturing of both commodity and leading-edge semiconductor chips. Such a cost reduction can only be fully realized if the throughput of wafer units of the fab tools (the tools of the fabrication facility) is the same for 300mm as 200mm substrates, which had been to some extent  
25 been assumed would be the case. Unfortunately, in the case of ion implantation to fabricate ultra-shallow (and ultra high density) semiconductor junctions, even the latest acceleration/deceleration implanters continue to be dose-rate-limited in their wafer throughput, so that there has been essentially little or no net increase in productivity of semiconductor dies by use of the larger wafers. This is a potentially difficult situation for the chip manufacturer: if  
30 many more implanters must be put into production to make up for their reduced output, the potential cost reduction per die sought by use of the larger wafer geometry cannot be realized

due to the increased cost of performing these critical implants (more investment in capital equipment, fab floor space, maintenance cost, etc.).

Background: Ion Doping

5 Over the last decade, implantation systems have been developed for the ion implantation of very large substrates from which flat-panel displays are manufactured. These "Ion Doping" systems deliver long ribbon ion beams to the glass or quartz substrates, which are typically mechanically scanned across a stationary ion beam. The substrate dimension can be as large as a meter, and so the ion ribbon beam must likewise be long enough to ensure uniform doping  
10 (typically wider than the substrate). In order to generate such long ribbon beams, large-volume "bucket" sources are used. Bucket sources in a rectangular or cylindrical geometry are chambers surrounded by an array of permanent magnets which provide magnetic confinement for the enclosed plasma through the creation of cusp magnetic fields. The plasma is generated by one or more RF antennas which couple RF power to the plasma. An extraction lens forms the ribbon  
15 beam from the large-diameter source.

Because of the size of the ion doping system, mass analysis is not used, therefore all ion species created in the bucket source are transported to and implanted into the substrate. This creates many process-related problems including variations in ion implantation depth, and also the implantation of unwanted species. Bucket sources are also particularly susceptible to the  
20 accumulation of deposits within their large ionization volume, hence the potential of severe cross-contamination between n- and p-type dopants requires the use of dedicated-use ion doping systems: the user must purchase one tool for p-type (e.g., boron from diborane gas) and a second complete tool for n-type (e.g., phosphorus from phosphene gas) dopants. This requirement not only doubles the customer's capital equipment costs, but substantially increases the risk of  
25 reduced product yield, since moving the substrates between systems requires further wafer handling steps and increased exposure of the substrates to atmosphere.

Thus, the prior art bucket source technology suffers from the following limitations:

(1) Large footprint (width, height and length).

(2) High degree of expense and complexity.



(3) Low ion production efficiency due to the loss of B (from  $B_2H_6$  feed gas) and P (from  $PH_3$  feed gas) to the walls of the ion source due to the very large wall surface area and large volume of the source.

(4) Contamination and particulate problems associated with the rapid accumulation of deposits within the ion source associated with (3), reducing product yield.

(5) Production of many unwanted ions which are implanted into the substrate, resulting in a lack of implantation process control and a concomitant degradation of device characteristics. For example, significant fractions of  $H^+$  and  $BH_x^+$ , as well as  $B_2H_x^+$ , are produced in the  $B_2H_6$  plasma commonly used to implant boron, a p-type dopant.

(6) Implantation of large currents of  $H^+$  (a result of (5)) during the implantation process limits attainable dose rate and hence throughput, since the total ion current delivered to the substrate must be held below a certain limit to prevent overheating of the substrate.

## SUMMARY

In one aspect, the invention provides a method of ion implantation by producing a high brightness ion beam that extends along an axis by ionizing molecules of a gas or vapor, the molecules containing an implantable species. The method includes providing an ionization chamber having a restricted outlet aperture; providing in the ionization chamber the gas or vapor at a pressure substantially higher than the pressure within an extraction region into which the ions are to be extracted external to the ionization chamber, by direct electron impact ionization by primary electrons, ionizing the gas or vapor in a region adjacent the outlet aperture of the ionization chamber in a manner to produce ions from the molecules of the gas or vapor to a density of at least about  $10^{10} \text{ cm}^{-3}$  at the aperture while maintaining conditions that limit the transverse kinetic energy of the ions to less than about 0.7 eV, the width of the ionization volume adjacent the aperture, in which said density of ions is formed, being limited to a width less than

about three times the corresponding width of the outlet aperture; and conditions within the ionization chamber being maintained to prevent formation of an arc discharge, by an extraction system, extracting ions formed within the ionization chamber via the outlet aperture into the extraction region downstream of the aperture, thereafter, with ion beam optics, transporting the beam to a target surface, and implanting the ions of the transported ion beam into the target.

Variations of this aspect of the invention may include one or more of the following features. Conditions are maintained within the ionization chamber to prevent formation of a plasma. The brightness of the ion beam upon extraction is more than about  $1 \text{ mA-cm}^{-2}\text{-deg}^{-2} \times (E_0/E)$ , where  $E$  is the beam energy, and  $E_0=10\text{keV}$ . The x-emittance of the beam upon extraction is less than about  $70 \text{ mm-mrad} \times (E_0/E)^{1/2}$  (where  $E$  is the beam energy and  $E_0=10\text{keV}$ ), for an ion current density of at least  $1 \text{ mA/cm}^2$ , even for an ion mass of 120 amu. The beam noise of the stream of ions extracted through the outlet aperture is maintained below 1%. The field strength of any magnetic field present in the ionization chamber is less than 70 gauss. The field strength of any magnetic field present in the ionization chamber is less than 20 gauss. There is substantially no magnetic field present in the ionization chamber. Any magnetic field present in the extraction region has a field strength of less than about 20 gauss. The consumption of the gas or vapor is maintained less than 10 sccm. The primary electrons are introduced into the ionization chamber by electron optics in a directed beam generated external to the ionization chamber. The molecules to be ionized respectively comprise or consist of at least two atoms of the implantable species.

In another aspect, the invention provides a method of ion implantation including producing a high brightness ion beam that extends along an axis by providing an ionization chamber having an outlet aperture, providing in the ion chamber molecules of a gas or vapor, in which each molecule to be ionized comprises or consists of at least two atoms of an implantable species, ionizing the molecules and extracting ions formed from said molecules under conditions to produce a beam having, upon extraction, a brightness of upon extraction is more than about  $1 \text{ mA-cm}^{-2}\text{-deg}^{-2} \times (E_0/E)$ , where  $E$  is the beam energy, and  $E_0=10\text{keV}$  and an x-emittance of less than about  $70 \text{ mm-mrad} \times (E_0/E)^{1/2}$  (where  $E$  is the beam energy and  $E_0=10\text{keV}$ ), for an ion current density of at least  $1 \text{ mA/cm}^2$ , even for an ion mass of 120 amu, thereafter, with ion beam optics, transporting the beam to a target surface, and implanting the ions of the transported ion beam into the target.

Variations of this or any other aspect of the invention may include one or more of the following features. The molecules are dimers. The molecules comprise decaborane. The method is conducted in a manner to cause the high brightness ion beam to have a low angular divergence at contact with the target of less than about one degree relative to the axis. The step of implanting the ions of the transported ion beam into the target is employed to cause the high brightness, low divergence beam to form a drain extension region of a transistor structure on the target, in which the transistor structure comprises a source, a gate and a drain. The target further comprises a well dopant and the gate of the transistor structure has a gatelength of 0.20  $\mu\text{m}$  or less, the drain extension intersecting the gate at a lateral junction edge, the drain extension having a lateral abruptness of 3 nm/decade or less, wherein lateral abruptness is defined as the lateral extent required to accomplish a one decade change in the volume concentration of the implanted species at the lateral junction edge, the junction edge being defined as the region where the volume concentrations of the implanted ions and the well dopant are equal. The drain extension has a lateral abruptness of 2 nm/decade or less. The ions of the high brightness, low angular divergence beam are implanted at opposite ends of the gate, sharply defining a channel beneath the gate. Sharply defining the channel beneath the gate includes sharply defining the length of the channel.

In another aspect, the invention provides an ion implantation system for implanting at a desired low implant energy into a target substrate comprising an ion source for producing molecular ions (based on a molecule having a cluster of atoms of the desired species to be implanted), an acceleration stage enabling the ions to be accelerated to a transport energy substantially greater than the desired implant energy, and prior to the target substrate, a deceleration stage for lowering the energy of the ions to the desired implant energy.

Variations of this aspect of the invention may include one or more of the following features. The ion source includes an electron gun for producing a beam of electrons at controlled energy adapted to ionize the molecules by direct electron impact ionization. The energy of the electrons is between about 20eV and 500eV. The gun is arranged relative to an ion chamber to cause the beam of electrons to transit the chamber to a beam dump. A lengthy elongated ionization chamber has a correspondingly elongated slot-form extraction aperture, and electron optics following the aperture are constructed to reduce the length of the profile of the resultant beam, relative to the corresponding length of the extraction aperture, prior to the beam entering

the analyzer. The electron optics comprises a telescope. The extraction aperture of the ionization chamber is of the order of about 6 inches in length. The ion implantation system is constructed for batch operation, a set of wafers being mounted on a carrier that moves relative to the beam to effect scanning. The ion implantation system is constructed as a serial ion implanter.

5 The ion source has a vaporizer mounted integrally with an ionization chamber of the ion source, and temperature control system for the temperature of the vaporizer. The ionization chamber electron gun and a beam dump to which the beam of electrons is directed are each thermally isolated from the ionization chamber. The ion source is a decaborane source and the electron gun is constructed to produce a beam of electron energy between about 50 and 1000 eV. The ion source is a source of  $\text{As}_2^+$  ions. The ion source is a source of  $\text{P}_2^+$  ions. The ion source is a source of  $\text{B}_2^+$  ions. The ion source is a source of  $\text{In}_2^+$  ions. The ion source is a source of  $\text{Sb}_2^+$  ions.

In another aspect, the invention provides a method of conducting ion implantation by use of the ion implantation systems of any of the other aspects of the invention.

15 In another aspect, the invention provides a method of ion implantation of ions at a desired implant energy on a target substrate. The method including forming molecular ions (based on a molecule having a cluster of atoms of the desired species to be implanted, accelerating the ions to and transporting the ions at an energy substantially above the implant energy, and prior to implant upon the substrate, decelerating the ions to the implant energy.

20 Variations of this aspect of the invention may include one or more of the following features. The ions are decaborane. The ions are  $\text{P}_2^+$  ions. The ions are  $\text{B}_2^+$  ions. The ions are  $\text{In}_2^+$  ions. The ions are  $\text{Sb}_2^+$ .

In another aspect, the invention provides an ion implantation system including an ion implanter having an ion extraction system; an ion source capable of providing ions in commercial ion current levels to the ion extraction system, the ion source including an ionization chamber defined by walls enclosing an ionization volume, one of said walls defining an extraction aperture of a length and width sized and arranged to enable the ion current to be extracted from said ionization volume by said extraction system; an electron gun constructed, sized and arranged with respect to the ionization chamber to project a directional beam of primary electrons along an axis through the ionization chamber; and a beam dump aligned with the electron gun to receive the directional beam, the beam dump being maintained at a

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substantial positive voltage relative to the emitter voltage of the electron beam gun, the axis of the beam path of said primary electrons extending in a direction generally adjacent to the aperture, the electron beam having a dimension in the direction corresponding to the direction of the width of the extraction aperture that is about the same as or larger than the width of the aperture.

Variations of this aspect of the invention may include one or more of the following features. The ion implantation system further includes a vaporizer arranged to introduce vapor to the ionization volume. The ion implantation system further includes a gas passage for introducing gas from a gas source to the ionization volume. The ion implantation system further includes a control system enabling control of an energy associated with the primary electrons to ionize individual vapor or gas molecules principally by collisions with primary electrons from the electron gun. The vapor comprises decaborane. The directional beam is a ribbon ion beam. The ribbon beam is of shorter extent than the length of the ion extraction aperture. The ribbon beam is longer than the ion extraction aperture. The ribbon beam is about the same length as the length of the ion extraction aperture. The length of the aperture is at least as long as the length or width of a target substrate.

In another aspect, the invention provides a method of irradiating an extended panel of predetermined dimensions, the method comprising generating a ribbon ion beam with the ion implantation system of any of the other aspects of the invention, and directing the ribbon ion beam onto a surface of the extended panel.

Variations of this aspect of the invention may include one or more of the following features. The extended panel is a flat panel, the method including irradiating the flat panel across substantially an entire panel surface. The ribbon ion beam produced is stationary, the flat panel being mechanically scanned across the beam to accomplish ion doping of the panel. The length of the ribbon beam is longer than the flat panel substrate dimension orthogonal to the scan direction.

#### Electron-Beam Ion Source for Ion Implantation Advantages

In one aspect, the present invention reduces or eliminates the above-described problems associated with conventional ion implantation sources. The disclosed solution has the following features which result in an exceptionally low-emittance ion source, ideally suited to the requirements of next-generation ion implanters:

- 1) There is no plasma, hence no plasma potential.
- 2) The ion density is low (on the order of  $10^{11}$  cm<sup>-2</sup> or less), reducing coulomb scattering  
5 between ions, and the resultant ion energy spread, to a negligible degree.
- 3) Gas molecules are ionized by direct electron impact ionization, resulting in "cold" ions  
which possess thermal energies approximately equal to that of the neutral gas molecules,  
that is,  $\ll 1$  eV. This results in a highly monochromatic source of ions, and enables low  
10 angular divergence in the extracted ion beam.
- 4) By tuning the electron impact energy, a high percentage of the dopant ions of interest can  
be produced, minimizing space-charge effects.
- 15 5) Molecular ions, which are typically dissociated in an arc discharge, are preserved to a  
high degree. For example, when using phosphene (PH<sub>3</sub>) feed gas, a large percentage of  
the PH<sub>3</sub><sup>+</sup> ion can be produced (e.g., 50% of total extracted current). As another example,  
decaborane (B<sub>10</sub>H<sub>14</sub>) can be used to produce a large fraction (>70%) of the decaborane  
ion, B<sub>10</sub>H<sub>x</sub><sup>+</sup>. This ion is very important for implanting boron at very low (<1 keV)  
20 energies, and its use can greatly increase the implanted boron dose rate. Plasma-based  
ion sources such as the Enhanced Bernas source cannot produce decaborane ions since  
plasma effects and elevated wall temperature cause dissociation and subsequent loss of  
the decaborane molecule.
- 25 6) A magnetic field is not required.
- 7) The high-frequency noise observed in arc discharge sources is absent, preserving to a  
much higher degree space charge compensation by low-energy electrons in the beam  
plasma.

- 8) The dimension of the ion extraction aperture is scalable over a broad range, from 12mm to 300mm or greater, for example. This leads to greater extracted currents, and improved compatibility with next-generation ion implanter designs. In fact, this feature enables ion implanter designs not possible with previous ion source designs.

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#### Acceleration/Deceleration Ion Implantation Advantages

According to one aspect of the invention, I provide a technique for obtaining a great increase in low-energy beam current and higher quality and higher production rates for low energy ion implantation, by novel combination of acceleration/deceleration ion implantation with molecular ions as the species being implanted. By this combination, I realize conditions that alleviate the aforementioned non-uniformity and dosimetry problems that have been seen as being inherent in acceleration/deceleration ion implantation systems.

In molecular ion implantation in such systems, an ion beam is formed from a compound which contains multiple atoms of the dopant of interest (for example, B, As, P, Sb, or In) to produce both a shallower implantation profile and a higher effective dose rate than possible with conventional monomer (i.e., single atom) ion implantation. As an important example applied to low-energy boron implantation, rather than implanting an ion current  $I$  of monomer  $B^+$  ions at an energy  $E$ , a decaborane molecular ion,  $B_{10}H_x^+$ , is implanted at an energy  $10 \times E$  and an ion current of  $0.10 \times I$ . Extending this example, a 5 keV, 1 mA  $B_{10}H_x^+$  ion beam is process-equivalent to a 500 eV, 10 mA  $B^+$  ion beam. The resulting implantation depth and dopant concentration (dose) of these two methods have been shown to be equivalent, but the decaborane implantation technique has significant advantages. Since the transport energy (mass  $\times$  velocity<sup>2</sup>) of the decaborane ion is ten times that of the dose-equivalent boron ion, and the ion current is one-tenth that of the boron current, the space charge forces responsible for beam blowup and the resulting beam loss are much reduced relative to monatomic boron implantation. As mentioned above, this approach has been proposed to increase useful boron dose rates of conventional (i.e. non-deceleration ) ion implanters. In one aspect, my contribution is the specialized use of molecular (cluster) ions in acceleration/deceleration ion implantation to realize unexpected advantages.

According to a preferred embodiment of the present invention, decaborane ions are employed in an acceleration/deceleration ion implanter, gaining a large increase in useful boron

dose rate, and, heretofore unappreciated by those of ordinary skill, avoiding the substantial degradation of beam profile characteristics at the wafer that are inherent in decelerating monomer boron ions prior to implantation. Also according to the invention, other important molecular dopants can achieve similar effects. An explanation of the improvement is based on the following considerations.

It is well-known that space-charge effects impose limits on attainable beam currents in the initial ion extraction stage of a conventional (i.e., non deceleration) ion beam implanter as well as in the beam transport stage. Considering the ion extraction stage, the relative improvements enabled by molecular implantation can be quantified by investigating the Child-Langmuir limit, that is, the maximum space charge-limited ion current density which can be utilized by the extraction optics of the ion implanter. Although this limit depends somewhat on the design of the implanter optics, it has been recognized to be usefully approximated as follows:

$$(1) \quad J_{max} = 1.72 (Q/A)^{1/2} U^{3/2} d^{-2},$$

where  $J_{max}$  is in mA/cm<sup>2</sup>,  $Q$  is the ion charge state,  $A$  is the ion mass in amu,  $U$  is the extraction voltage in kV, and  $d$  is the gap width in cm. In practice, the electrostatic extraction optics used by many ion implanters can be made to approach this limit. By extension of equation (1), the following figure of merit,  $\Delta$ , which quantifies the easing of space-charge limitations in the case of molecular implantation relative to monatomic implantation, can be expressed as:

$$(2) \quad \Delta = n (U_n / U_1)^{3/2} (m_n / m_1)^{-1/2},$$

where  $\Delta$  is the relative improvement in dose rate (atoms/s) achieved by implanting a molecular compound of mass  $m_n$  and containing  $n$  atoms of the dopant of interest at an accelerating potential  $U_n$ , relative to a monatomic implant of an atom of mass  $m_1$  at an accelerating potential  $U_1$ . In the case where  $U_1$  is adjusted to give the same implantation depth into the substrate as the monomer implant, equation (2) reduces to:

$$(3) \quad \Delta = n^2.$$



Thus, up to a factor of 100 increase in dose rate can be accomplished by substituting decaborane for boron at ion extraction in a conventional (non deceleration) system.

I realize that the deceleration stage of an acceleration/deceleration implantation system  
5 has a similarity to the operation of extraction optics of an extraction stage that is crucially  
relevant to the issue; both employ a strong focusing field over a short distance. I realize that  
equation (1) has a sufficient degree of validity for the deceleration stage to enable comparison of  
its performance with molecular ions and with monomer ions. Hence, I realize equation (3) can  
also be used to evaluate the deceleration stage. Using this mode of analysis, for example, a  
10 conventional acceleration/deceleration implanter can deliver up to about 2 mA of boron  
monomer to the wafer at an implantation energy of 500 eV, albeit with the significant non-  
uniformity and dosimetry problems mentioned; but by the novel substitution of decaborane  
( $B_{10}H_x^+$ ) for boron monomer in the acceleration/deceleration ion implanter, made possible in a  
production worthy system by using the techniques described in my above referenced patent  
15 applications the same dose rate can be accomplished by implanting 0.2 mA of decaborane at 5  
keV. This reduces sensitivity to space-charge to such an extent in the deceleration stage that the  
usual degradation of beam profile that occurs with deceleration, and implant uniformity, angular  
integrity, and dosimetry of an acceleration/deceleration system are greatly improved.

This novel accel/molecular ion combination (acceleration/deceleration ion implantation,  
20 using a beam of molecular (cluster) ions), can be employed to increase the low-energy boron  
dose rate to new proportions, never before possible in ion implantation. For example, one can  
envision extracting more than 3 mA of decaborane at 20 keV, and decelerating the decaborane  
ions down to 5 keV (a 4:1 deceleration) to achieve a dose rate of up to 30 mA at an effective  
implantation energy of 500 eV! Such a large effective boron dose rate easily enables high dose  
25 implants such as PMOS source/drain extensions at a mechanical throughput limit in excess of  
200 wafers per hour (200 WPH), even for 300mm-diameter substrates (for reference, 2mA of  
conventional boron will produce a wafer throughput of about 25 WPH at a dose of  $8E14$ ). As I  
will discuss later, such high beam currents will also enable novel, important processes for ultra-  
shallow junction formation.

30 Such an acceleration/deceleration system can also be used for dimer implantation. Ion  
beams consisting of dimers (typically not heretofore recognized as suitable ion implantation

materials), can be utilized to reap above-described benefits with other dopant species, using the production-worthy vaporization and ionization techniques provided in my above-referenced patent application. Ion beams of, for example,  $\text{As}_2^+$ ,  $\text{P}_2^+$ ,  $\text{B}_2^+$ ,  $\text{In}_2^+$ , or  $\text{Sb}_2^+$  can be formed, and according to my realization of the beneficial applicability of equation (3) to the deceleration stage, can yield a factor of 4 improvement in the decelerated beams, increasing maximum dose rate and reducing non-uniformity and dosimetry problems in the manner previously described for decaborane implantation. Table Ia below lists materials suitable for dimer implantation as applied to the present invention.

Table Ia

Compound	Melting Pt (deg C)	Dopant	Phase
$\text{As}_2\text{O}_3$	315	$\text{As}_2$	Solid
$\text{P}_2\text{O}_5$	340	$\text{P}_2$	Solid
$\text{B}_2\text{H}_6$	----	$\text{B}_2$	Gas
$\text{In}_2(\text{SO}_4)_3$ $\text{XH}_2\text{O}$	250	$\text{In}_2$	Solid
$\text{Sb}_2\text{O}_5$	380	$\text{Sb}_2$	Solid

As part of the system and method, such dimer compounds are vaporized at temperatures below their melting points, and the vapor is ionized principally by impact action of a broad electron beam transiting a volume containing the vapor.

The use of the disclosed systems for acceleration/deceleration implantation of decaborane, etc. enables new processes in semiconductor manufacturing. Another aspect of the invention is the realization that one or more costly steps can be eliminated from many implant sequences, or their cost reduced, or the quality of the implant sequence improved, by using in the sequence, the combination decel/molecular ion method and system described above.

For example, such a system can be used for the amelioration of transient enhanced diffusion (TED). In the creation of ultra-shallow p-n junctions in CMOS manufacturing, special

attention is given to forming PMOS source/drain (S/D) structures. Boron is the only p-type dopant having a high enough solid solubility to form S/D structures with the required electrical conductivity; however boron will diffuse rapidly in the silicon substrate during the anneal ("activation") cycle that is required to process the wafers. This anomalous boron diffusion, called  
5 transient enhanced diffusion (TED), limits the attainable parameters, in particular the abruptness of the p-n junction. TED is believed to be mediated (detrimentally increased) by defects created in the silicon during the implantation process.

In forming leading-edge, ultra-shallow semiconductor chip devices, manufacturers wish to use very low-energy (sub-keV) boron implants to form very shallow as-implanted boron  
10 profiles, so that the activated profile is largely determined by TED. In order to reduce the extent of TED, a low thermal budget spike anneal (i.e., rapid thermal annealing or RTA) is being used in conjunction with sub-keV implants to achieve more shallow p-n junctions. Recently, it has been proposed that a boron implantation energy of 500eV is probably the lowest energy boron implant employable in order to minimize the depth of the activated p-n junction, since TED is  
15 expected to dominate the profile at this and lower energies after activation. However, I regard this conjecture to be far from proven in manufacturing, since the effects of TED reduce somewhat linearly as the boron implantation depth is decreased. This advantageous "shallowness" effect upon TED is believed to stem from the fact that the exposed silicon surface acts as a "sink", or getter, for defects during TED, so that the shallower the implant, the less the  
20 extent of TED.

Since wafer throughput unfortunately is already far below mechanical limit when performing 500eV boron implants, even in ion implanters using deceleration, and since reducing the implantation energy below 500eV causes the wafer throughput to drop further dramatically, such sub-500eV implants using conventional boron implantation are unlikely to be used in  
25 manufacturing. Such effects of reduced throughput are, of course, much more harmful economically for the 300mm manufacturing that is requiring great capital cost for new fabs and equipment.

However, by employing the new system and method provided here, commercially advantageous throughput of ultra shallow implants can be achieved, with "shallowness"  
30 amelioration of the TED problem, and thus achievable density and performance of implanted devices can be extended to new regimes of quality and smallness of size.

The disclosed acceleration/deceleration systems can also reduce the need to pre-amorphize. To assist in limiting the depth of the as-implanted boron profile, pre-amorphization (destruction of the crystal lattice) implants have often been performed in advance of the boron implant to limit channeling, and thus increase the as-implanted depth profile. Amorphization is accomplished by implants of high doses of germanium or silicon beams. This is an expensive added process which increases the cost and complexity of manufacturing ultra-shallow p-n junctions.

I conceive that *new* process advantages can be obtained in this respect as well by special use of the cluster molecule dopants in an acceleration/deceleration machine in the manner described. That is to say, not only can improved boron dose rate, shallower implants and improved device performance be achieved, but also the damage characteristics of this new molecular implantation system makes possible elimination of the expensive Ge or Si pre-amorphization implant steps. It is known that high density ion clusters such as decaborane cause damage to the local crystal structure upon impact with the silicon surface due to the inelastic nature of the collision. At sufficiently high dose rates (achievable with the present invention, e.g., between 0.5 and 3 mA of decaborane), the resulting damage profile can obviate or reduce the need for a separate pre-amorphization implant, eliminating or reducing the cost of this expensive step in the manufacturing process.

Thus, boron implants at production-worthy wafer throughputs with acceleration/deceleration systems employing decaborane ions can be performed for both 200mm and 300mm substrates at energies as low as 100eV. Since TED effects will be further reduced at these extremely low implantation energies, shallower p-n junctions can be fabricated than heretofore possible.

By ionizing the molecule to produce the molecular ions by primary electron-impact, heat sensitive ion source materials can be employed, especially solid decaborane and the dimers mentioned above.

By employing a broad beam of electrons directed adjacent to a greatly elongated extraction aperture, and employing telescopic optics to reduce the dimension of the beam prior to the beam entering the analyzer of the beam line.

The invention makes possible:

1) Production-worthy wafer throughput for boron implants using decaborane ions at implantation energies between 100eV and 1keV, for 200mm and 300mm wafers;

2) By use of a high dose rate of decaborane (e.g., between about  $2 \times 10^{15}$  and  $2 \times 10^{16}$  decaborane ions per second), producing enough crystal structural damage to obviate or reduce the need for costly pre-amorphization implants;

3) By using extremely low implantation energy (between about 1keV and 5 keV decaborane energy, equivalent to between 100eV and 500eV boron energy) ultra-shallow junctions by a reduction in the broadening of the activated boron profile due to TED.

4) By use of other cluster molecules, including novel dimer materials, achieving similar advantageous results with other implant species.

Thus, fewer steps, significant cost reduction, shallower and more dense p-n junctions, and improved device performance can be achieved than heretofore possible.

#### Electron-Beam Ion Source for Ion Doping Advantages

In another aspect, the present invention can be implemented into an ion doping system as a replacement for the above-described bucket source. The disclosed ion doping system offers the following advantages:

(1) Small footprint—the electron-beam ion source is a small-volume source, and is elongated in only one direction, the desired length of the ribbon beam.

(2) Reduced cost—because of its compact size and scalability, the present invention is simpler and significantly less expensive than the prior art.

(3) High efficiency—because of its smaller volume and reduced surface area, loss of the ions of interest to the walls of the ionization volume is substantially reduced relative to the prior art.

(4) Improved process control—a higher percentage of ions produced are the desired ions. This leads to reduced deposition (fewer ions are produced in the first place to achieve a given ion beam current), higher ion production efficiency of the dopant ion of interest,

and much better control of the implantation process. Since the majority of ions produced from the electron-beam ion source are the ions of interest, the implantation profile and dose accuracy is much improved relative to the prior art.

- 5 (5) Higher throughput—the present invention increases throughput due to its ability to produce higher dopant ion currents than the prior art.
- (6) Soft ionization—the present invention enables the efficient production of molecular ions such as decaborane, which offer significant advantages in throughput and efficiency in  
10 ion doping applications over, for example, diborane.

Reduced capital equipment cost, less fab floor space occupied, and higher product yield—due to its small footprint and reduced complexity, the present invention also enables a single ion doping system to be constructed with two ion sources, one for p-type dopants, and one  
15 for n-type dopants. Using simple dual slit optics, the ion doping system can switch between the two ion sources while processing a lot of substrates. This relieves the high equipment cost of two dedicated systems, halves costly fab floor space, and reduces the risk to product yield which is presently a consequence of prior art ion doping systems.

### DESCRIPTION OF DRAWINGS

20 FIG. 1 is a schematic view of a prior art source for ion implantation.

FIG. 2 is an enlarged schematic view of a portion of the prior art source for ion implantation of Fig. 1.

FIG. 3 is a diagrammatic view of an ion implantation source of the present invention, shown in a cutaway view down the center axis of the source, so the internal components can be  
25 seen.

FIG. 4 is a magnified diagrammatic view of the ionization chamber of the ion implantation source of Fig. 3.

FIG. 4a is a diagrammatic view of Fig. 4a of a preferred embodiment of the electron optics of the ion implantation source of Fig. 3.

FIG. 5 is a schematic diagram of the biasing scheme of power supplies which provide voltage to the ion implantation source of FIG. 3.

FIGs. 6a and 6b are diagrammatic cross-sectional side and top views, respectively, of an alternate ionization chamber for an implantation source of the present invention.

5 FIGs. 7a and 7b are diagrammatic perspective and top views of an apparatus for improving the focus of the electron beam of the ionization chamber of Fig. 6.

FIG. 7c is a Fig. 7C is a schematic illustration of dimensional geometry of the apparatus Figs. 7a and 7b.

FIG. 8 is a diagrammatic view of the apparatus of Figs. 7a and 7b incorporated into an ion implantation source similar to that depicted in Fig. 3.

FIG. 9 is a diagrammatic top view of an alternative ionization chamber of the present invention.

FIG. 10 is a diagrammatic view similar to that of Fig. 3 illustrating the ionization chamber of Fig. 9 incorporated into an ion implantation source.

15 FIG. 11 is a general schematic illustration of ion implantation.

FIG. 12 is a general schematic illustration of an ion source emitting an ion beam.

FIG. 13 is a general schematic illustration of ion implantation forming a drain extension adjacent a gate on a target substrate.

FIG. 14a is a general schematic illustration of a gate edge and drain extension layer formed by boron ion implantation of a previously phosphorus doped silicon substrate while Fig. 14b is a graphical illustration of boron and phosphorus ion concentrations taken along section AA of Fig. 14a and charted on a logarithmic scale.

FIG. 15 is a graphical illustration of the lateral straggle exhibited during ion implantation as a function of the incident angle of ion approach to the target and the ion implantation energy.

25 FIG. 16a and 16b are schematic illustrations of predicted lateral straggle exhibited during ion implantation for normal incidence and 7 degree nonparallel incidence angles, respectively.

FIG. 17 is a view similar to that of Fig. 4, illustrating an alternative ion implantation source of the present invention for producing extended ribbon beams.

FIG. 18a is a diagrammatic view of a dual ion source system of the present invention for enabling both n - and p-type dopants to be implanted in a single ion doping tool.

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FIG. 18b is a diagrammatic view of the ion source of Fig. 18a implanting ions onto a flat panel substrate.

FIG. 19 is a diagrammatic view of a doping tool for flat panel displays into which the arrangement of Fig 18a can be incorporated.

5 FIG. 19a is a graphical illustration of a cracking pattern for decaborane.

FIG. 20 is a side cross-sectional view of an acceleration/deceleration ion implantation system, of the kind having a fixed beam line, wafers being carried on a spinning disk.

FIG. 21 is a side view of an ion source, suitable for decaborane, etc., retrofittable into the ion source housing of a pre-existing acceleration/deceleration ion implantation system, such as  
10 shown in Figure 1.

FIG. 22 is a side view of another ion source suitable for decaborane, etc., used in an acceleration/deceleration ion implantation system, featuring a highly elongated extraction aperture for producing an initial beam of ions having a highly extended cross-section;

FIG. 23 is a view, similar in kind to Figure 2, of an ion source capable of magnetically  
15 confining an electron beam passing through the ionization chamber;

FIG. 24 is a diagrammatic representation of ion optics combined with an ionization chamber from which a beam of ions of highly extended cross-section is extracted.

FIG. 25 is an unscaled perspective view of a lens and lens holder combination of the present invention.

20 FIG. 26 is an unscaled cross-sectional perspective view of the electron gun of Fig. 27.

FIG. 27 is an unscaled perspective view of an electron gun of the present invention.

## DETAILED DESCRIPTION

The following terms and definitions apply throughout the application.

25 Transverse kinetic energy ( $E_T$ ): The component of kinetic energy transverse to the direction of beam propagation, *i.e.*, the direction of the extraction field.  $E_T = \frac{1}{2} m v_T^2$ , where  $v_T$  is the component of velocity orthogonal to the beam direction.

Beam noise ( $N$ ): Fluctuation in beam current intensity as a percentage of average current level, above a frequency of 100Hz.



Emittance ( $\epsilon$ ): The total emittance  $\epsilon$  is the product of the two emittances,  $\epsilon = \epsilon_x \epsilon_y$ , where in the case of vertically-oriented slot lenses,  $\epsilon_x$  is the emittance in the horizontal direction (along the slot width), and  $\epsilon_y$  is the emittance in the vertical direction. For any lens geometry,  $\epsilon_x$  and  $\epsilon_y$  are defined along the two orthogonal directions normal to the direction of beam propagation.

5 The emittance components  $\epsilon_i$  are defined as follows:

$$\epsilon_x = 2 \kappa \Delta x \alpha_x, \epsilon_y = 2 \kappa \Delta y \alpha_y, \text{ where}$$

$$\kappa = (E_0/E)^{1/2}, \text{ where } E \text{ is the beam energy and } E_0 = 10 \text{ keV};$$

10

$\alpha_x$  and  $\alpha_y$  are the beam divergence half-angles into the x- and y-directions, respectively; and  $\Delta x$  and  $\Delta y$  are the beam dimensions in the x- and y-directions, respectively, and the emittance variables are all measured at the same z-position along the direction of propagation, and are chosen to contain at least 70% of the beam current. Emittance components  $\epsilon_i$  are expressed in units of mm-mrad or in cm-deg.

15

Brightness ( $B$ ):  $B$  is the beam current  $I$  divided by total beam emittance:  $B = I / \epsilon_x \epsilon_y$ .

Plasma is defined as a region containing the ionization volume which is substantially electrically neutral, containing electrons and ions contributing approximately equal charge densities opposite in sign.

20

### Ion Implantation Sources

Referring now to the attached figures, a conventional ion source used in ion implantation is shown in Figs. 1 and 2. The Enhanced Bernas source is commonly used in high current, high energy, and medium current ion implanters. The ion source  $a$  is mounted to the vacuum system of the ion implanter through a mounting flange  $b$  which also accommodates vacuum feedthroughs for cooling water, thermocouples, dopant gas feed,  $N_2$  cooling gas, and power. The dopant gas feed  $c$  feeds gas into the arc chamber  $d$  in which the gas is ionized. Also provided are dual vaporizer ovens  $e, f$  in which solid feed materials such as As,  $Sb_2O_3$ , and P may be vaporized. The ovens, gas feed, and cooling lines are contained within a cooled machined aluminum block  $g$ . The water cooling is required to limit the temperature excursion of the aluminum block  $g$  while the vaporizers, which operate between 100C and 800C, are active, and

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also to counteract radiative heating by the arc chamber  $d$  when the source is active. The arc chamber  $d$  is mounted to, but in poor thermal contact with, the aluminum block  $g$ . The ion source  $a$  is an arc discharge source, which means that it operates by sustaining a continuous arc discharge between an immersed hot-filament cathode  $h$  and the internal walls of the arc chamber  $d$ . Since this arc can typically dissipate in excess of 300W, and since the arc chamber  $d$  cools only through radiation, the arc chamber can reach a temperature in excess of 800C during operation.

The gas introduced to arc chamber  $d$  is ionized through electron impact with the electron current, or arc, discharged between the cathode  $h$  and the arc chamber  $d$ . To increase ionization efficiency, a uniform magnetic field  $i$  is established along the axis joining the cathode  $h$  and an anticathode  $j$  by external magnet coils 90, shown in Fig. 2, to provide confinement of the arc electrons. An anticathode or repeller electrode  $j$  (located within the arc chamber  $d$  but at the end opposite the cathode  $h$ ) is typically held at the same electric potential as the cathode  $h$ , and serves to reflect the arc electrons confined by the magnetic field  $i$  back toward the cathode  $h$  and back again repeatedly. The trajectory of the thus-confined electrons is helical, resulting in a cylindrical plasma column between the cathode  $h$  and anticathode  $j$ . Fig. 2 shows a possible electron trajectory between cathode and anticathode, which is helical due to the confining magnetic field  $B$ . The plasma density within the plasma column is typically high, on the order of  $10^{12}$  per cubic centimeter; this enables further ionizations of the neutral and ionized components within the plasma column by charge-exchange interactions, and also allows for the production of a high current density of extracted ions. The cathode  $h$  is typically a hot filament or indirectly-heated cathode, which thermionically emits electrons when heated by an external power supply. It and the anticathode are typically held at a voltage  $V_c$  between 60V and 150V below the potential of the ionization chamber  $d$ . High discharge currents  $D$  can be obtained by this approach, up to 10A. Once an arc discharge plasma is initiated, the plasma develops a sheath adjacent to the surface of the cathode  $h$  (since the cathode  $h$  is immersed within the arc chamber and is thus in contact with the resulting plasma). This sheath provides a high electric field to efficiently extract the thermionic electron current for the arc; high discharge currents can be obtained by this method.

The discharge power  $P$  dissipated in the arc chamber is  $P = D V_c$ , or hundreds of watts. In addition to the heat dissipated by the arc, the hot cathode  $h$  also radiates power to the arc

chamber *d* walls. Thus, the arc chamber *d* provides a high temperature environment for the dopant plasma, which also boosts ionization efficiency relative to a cold environment by increasing the gas pressure within the arc chamber *d*, and by reducing condensation of dopant material on the hot chamber walls.

5 If the solid source vaporizer ovens *e* or *f* are used, the vaporized material feeds into the arc chamber *d* through vaporizer feeds *k* and *l*, and into plenums *m* and *n*. The plenums serve to diffuse the vaporized material into the arc chamber *d*, and are at about the same temperature as the arc chamber *d*. Radiative thermal loading of the vaporizers by the arc chamber also typically prevents the vaporizers from providing a stable temperature environment for the solid feed materials contained therein below about 100C. Thus, only solid dopant feed materials that both  
10 vaporize at temperatures >100C and decompose at temperatures >800C (the nominal wall temperature of a Bernas source) can be vaporized and introduced by this method.

Fig. 3 shows one embodiment of the present invention, certain aspects of which are also  
15 described in the above-referenced patent applications, shown in a cutaway view down the center axis of the source, so the internal components can be seen. The external vaporizer 28 is comprised of vaporizer body 30 and crucible 31 in which solid source feed material 29 such as decaborane resides. Resistive heaters are imbedded into the vaporizer body 30, and water cooling channels 26 and convective gas cooling channels 27 are in intimate contact with  
20 vaporizer body 30, and are used in combination to provide a uniform operating temperature above room temperature to the crucible 31. Thermal conduction between the crucible 31 and the temperature-controlled vaporizer body 30 is provided by pressurized gas introduced by a gas feed 41 into the crucible-vaporizer body interface 34, while the temperature of the vaporizer housing is monitored through a thermocouple. Vaporized decaborane or other vaporized  
25 material 50 is fed through vaporizer exit channel 39 and through heated gate valves 100 and 110 into the ionization chamber 44 through conductance channel 32. The source mounting flange 36 and source block 35 are also temperature controlled to a temperature near or above the vaporizer temperature.

The ion source gas delivery system includes two conduits that feed the ionization  
30 chamber from two separate sources. The first is a small diameter, low-conductance path from a pressurized gas source such as a gas cylinder. The second is from a high-conductance path from

a low-temperature vaporizer, which vaporizes solid material. Regardless of the source, the gas delivery system maintains a gas concentration of a few millitorr in the ionization chamber. The vaporizer maintains tight temperature control of its surfaces that contact the solid material, in order to maintain stable concentrations of gas in the ionization chamber.

5

Referring again to figure 3, the vaporizer assembly, 30a, is comprised of a heated and cooled body, 30 and a removable crucible, 34. Access to the crucible is made possible by removing the end plate, 28 on the back of the vaporizer.

Once the crucible is removed from the vaporizer, it can be recharged by removing its cover, 34b that is elastomerically sealed to the end of the crucible and raising the grate, 34a, which contains the solid, 29.

After recharge the crucible is inserted in the body and a gas seal is made to the bore, 39, at the front end of the body. This bore, 39 is the exit for the vaporized gas. The mechanical fit between the crucible and the body is precisely maintained to achieve temperature uniformity of the crucible. The gap is filled with a gas (cool gas) to facilitate thermal transfer between the two surfaces. The cool gas enters the gap through an end plate fitting, 28a.

Temperature control is performed using PID closed loop control of resistive elements that are imbedded in the body. The body material is highly thermally conductive to maintain temperature uniformity. A small thermal leak is intentionally applied to the body to create stability in the control system using external air channels. The air channels 27 pass around the vaporizer body and are covered by plates that are not shown. Air is ducted to the channels within a manifold system, which is integrated into the vaporizer end plate, 28, to provide slight convective cooling. The air is fed through the inlet after proceeding past a metering valve used for flow control. The air discharges from the assembly into house exhaust.

In addition to the air-cooling, there are also provisions for liquid cooling the vaporizer body. Coolant is ducted through a 1-meter long 6 mm diameter bore that travels back and forth throughout the body. Connections are made through fittings mounted to body ports, 26. The liquid cooling provides rapid cooling of the vaporizer assembly to provide quick service turnaround and also to change solid species.

Referring now to Fig. 4, ionization chamber 44 is in good thermal contact with block 35 through pressurized gas conducted through a conduit into the interface 36 between ionization

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chamber 44 and block 35. Gaseous materials, for example process gases such as  $\text{PH}_3$  which are held in gas cylinders, can be fed into the ionization chamber 44 through gas feed 33. Typically, the gas pressure within the ionization chamber 44 is approximately  $1 \times 10^{-3}$  Torr, while the region external to the ionization chamber 44 is approximately  $1 \times 10^{-5}$  Torr. Referring now to Fig. 4, the electron beam 125 produced by electron gun 42 enters the ionization chamber 44 through electron beam entrance aperture 45, and transits the ionization chamber 44 parallel to and in close proximity to the ion extraction aperture slot 46 contained within ion extraction aperture plate 80, exiting the ionization chamber 44 through electron beam exit aperture 47 and intercepted by beam dump 70. Beam dump 70 is water cooled through water cooled holder 130, which carries electrically resistive ( $>10 \text{ M}\Omega\text{-cm}$ ) de-ionized water. The beam dump is electrically isolated by insulating standoff 56, so that the e-beam current intercepted by beam dump 70 can be monitored externally at HV water feedthrough 170. The ion extraction aperture 80 is electrically isolated from ionization chamber 44 by an electrically insulating, thermally conductive gasket, and biased to a negative potential relative to ionization chamber 44. This bias of ion extraction aperture 80 establishes an electric drift field which attracts the ions towards the aperture 80, and provides a drift velocity to the otherwise thermal ions, enabling higher extracted ion currents than possible in the absence of a drift field. Typical dimensions for some of the ion source structures are: a 7.5mm diameter round electron entrance aperture 45, a 10mm diameter electron beam exit aperture 47, a 25mm diameter by 65mm long electron gun assembly 42, and a 67mm tall ionization chamber 44. Cutout 48 in the gun housing 142 enable the portion of the electron gun assembly 42 which contains the cathode to be exposed to the vacuum environment of the source housing, extending the service lifetime of the cathode 143.

The electron gun optics consist of the cathode 143, beam shaping electrode 145, first anode 147, focus electrode 149, second anode 150, and exit lens 152. This lens system extracts a space charge-limited electron current, and the downstream four-element lens comprised of first anode 147, focus electrode 149, second anode 150, and exit lens 152 both collimates and accelerates the electron beam to the desired final energy. Thermionic electrons are emitted by the hot cathode 143, which may be constructed of refractory metal or  $\text{LaB}_6$ , for example, and may be heated directly or indirectly. The electrons are accelerated across the first anode gap in a Pierce geometry, the equipotentials between cathode 143 and first anode 147 being shaped by the conical beam-shaping electrode 145 and first anode, which maximizes the output current by

allowing for space-charge effects. They can be extracted at up to 5 keV, and decelerated to a final energy which is variable between about 70eV and 2000eV by the downstream optics.

Fig. 4a shows a preferred embodiment of the electron optics, in which the second anode 150' and exit lens 152 are shaped according to a Pierce geometry. This Pierce geometry is inverted from the geometry of the Pierce extractor 144 defined by lenses 145' and 147', so that the lens 153 defined by the concatenation of 150' and 152' can be efficiently used as a deceleration lens, introducing a low-energy (e.g., 100eV or less), generally collimated electron beam into the ionization chamber 44. The incorporation of a "reverse Pierce" geometry for the deceleration lens 153 helps correct for a space charge-limited electron beam, so that a higher and more collimated low energy electron flux may be introduced into the ionization chamber 44 than otherwise possible. For example, the electron beam may be extracted into lens 147' at 1keV, propagate into lens 150' at 500 eV, and decelerate to 100eV within lens 152', enabling a higher electron current than if the beam were extracted at 100eV at the extractor 144.

The space charge forces present within the electron gun optics and especially within the deceleration lens 153 can be further ameliorated by the intentional production of positive ions along the electron beam path. The positive space charge of the ions compensates for the negative space charge of the electrons, reducing the net coulomb repulsion between electrons within the beam, thus reducing beam blow-up and enabling higher electron currents than otherwise possible. This is an effective means for reducing space charge forces: since the ions are heavy and slow-moving, their depletion rate is low, and a reasonable charge balance can be maintained if the rate of ion production is similar to the ion loss rate. The ion production rate at any point in the electron beam path is proportional to the local pressure of ionizable gas at that point. For example, consider local gas pressures  $P_1 > P_2 > P_3 > P_4$  shown in Fig. 4a (I note that it is possible to control the local pressures  $P_i$  by tailoring the conductance between individual lens elements and the ambient vacuum). Further consider the predominant gas species being decaborane ( $B_{10}H_{14}$ ), a large, heavy molecule with a large electron-impact ionization cross section for the production of positive ions. Within the ionization chamber 44,  $P_1$  is highest, approximately  $10^{-3}$  Torr, so that space charge compensation is very effective. This ensures uniform propagation of the electron beam within the primary ionization region, ensuring good uniformity of the ion density adjacent to the ion extraction aperture 46, and hence a uniform ion density in the extracted ion beam.  $P_4$  is the ambient pressure of the source vacuum housing

(nominally  $10^{-5}$  Torr or less), and because the gas within the ionization chamber 44 propagates through electron beam entrance aperture 45', a large pressure gradient is established between these extrema. Since the deceleration lens 153 is close to 45', P2 is relatively high, and space charge repulsion is reduced substantially. The region P3 is adjacent to the cathode 143', hence it  
5 is desired to maintain P3 close to P4, *i.e.*, at a sufficiently low pressure that the arrival rate of decaborane molecules to the cathode surface is less than the desorption rate of decaborane byproducts which can deposit on the cathode surface. This is particularly important for low-temperature cathodes such as LaB<sub>6</sub>, and for field emitter cathodes. In general, refractory metal cathodes operate at sufficiently high temperatures that deposition of cracked process gases is not  
10 a problem.

Fig. 5 shows the biasing scheme of power supplies which provide voltage to the electron gun elements and to the ion source, and dedicated meters. The symbols used in Fig. 5 have the following significance:

- V<sub>S</sub> (source V): 0-40 kV pos @ 100 mA. Sets ion beam energy, biases ionization chamber  
15 relative to ground.
- V<sub>C</sub> (cathode V): 0-2kV neg @ 100 mA. Sets electron beam energy, biases cathode relative to ionization chamber.
- V<sub>F</sub> (filament V): 0-5 V @ 50 A. Provides heater current to directly- or indirectly-heated cathode emitter.
- 20 • V<sub>E</sub> (extraction aperture V): 0-20 V neg @ 100 mA. Biases ion extraction aperture relative to ionization chamber.
- V<sub>1</sub> (Cathode shield V): 0-50 V neg @ 10 mA. Biases beam-shaping electrode relative to cathode.
- V<sub>2</sub> (anode V): 0-5 keV pos @ 50 mA. Biases first anode relative to cathode.
- 25 • V<sub>3</sub> (focus V): 0-5 keV pos @ 10 mA. Biases focus electrode relative to cathode.
- V<sub>4</sub> (exit lens V): 0-2 keV pos @ 50 mA. Biases exit lens relative to cathode and determines the energy at which electron beam leaves tetrode consisting of cathode, anode, focus, and exit elements.
- V<sub>D</sub> (beam dump V): 0-2kV pos @ 100 mA. Biases beam dump relative to cathode.
- 30 • M1: measures electron current leaving electron gun.
- M2: measures cathode emission current.

- M3: measures electron current arriving at beam dump.

Another embodiment of the present invention is suited particularly for ion implantation systems which extract ions from a slot between one and three inches long. The embodiment provides an efficient design for the generation of high currents of ions (e.g., 5 mA of each dopant beam is achievable). In this design, a filament approximately the same length as the ion extraction slot provides a one-dimensional "sheet" of low-energy electrons. The filament is oriented parallel to the ion extraction aperture slot, as also indicated in Fig. 6. An electron beam, as contained within the first embodiment, is not required. This geometry has two very significant advantages: 1) A high electron current is attainable, and 2) low electron injection energies can be achieved while still delivering high electron currents. A corollary to 2) is that, since ionization cross sections at approximately 100 eV are a factor of 5 greater than, e.g., 2 keV, very significant ion currents can be achieved. 3) Finally, no magnetic field is used, and magnetic confinement is not necessary to keep the electron beam from diverging, since the electrons are extracted as a one-dimensional beam, significantly reducing space-charge effects.

Hence, Fig. 6a shows a simple design for an ion source in which the electrons are injected into an ionization chamber along the same direction as the extracted ion beam. A long filament 170 is heated through filament leads 171 and DC power supply 172 to emit electrons 173 along the length of the filament. The filament may be a ribbon, or a thick tungsten wire, for example. The filament 170 is biased below the potential of the ionization chamber 175 by power supply 172 such that the electrons are accelerated through a rectangular entrance slot 74 centered in the rear of the ionization chamber 175. This constitutes a diode arrangement. A top view of this geometry is shown in projection D-D, Fig. 6b. The extended electron beam will ionize the gas within the ionization chamber 175; the ions are extracted through ion extraction aperture 176 within the ion extraction aperture plate 177. Apart from its simplicity, the advantage of the design of Fig. 6a is that high electron currents can be generated by the long filament 170 and focused uniformly along the ion extraction aperture 176. The ion beam thus produced should be uniform, since the electron path length through the gas within the ionization chamber 175 is the same along the length of the ion extraction aperture 176. Also, since the electron beam is elongated in the vertical dimension, it is less susceptible to space charge blow-up, and thus



higher total electron currents of a given energy can be delivered into the ionization chamber 175 than with a small, round electron beam.

To improve performance, a grid electrode 179 with a long rectangular slot can also be inserted between filament 170 and chamber entrance aperture 174 to improve focusing of the electron beam. This constitutes a triode configuration. To prevent the possibility of any transition metal contamination of the ionization chamber due to evaporation of the filament onto the entrance aperture 174 and eventual migration of tungsten or rhenium into the chamber 175, the filament can be further remotized, removing evaporated material from line-of-sight with the ionization chamber.

This embodiment is illustrated in schematic Fig. 7a. The filament 170 is remotized away from the ionization chamber 175, and the electron beam is propagated through a lens comprised of a series of long, rectangular apertures. The schematic representation of Fig. 7a shows a triode arrangement in which filament 170, beam shaping electrode 178, grid electrode 179, and ionization chamber entrance aperture 174 are all held at different potentials, but this arrangement is not limited to a triode; more lenses can be added as needed. A top view, showing in greater detail the electron optics of Fig. 7a and the propagation of the electron beam 173, is shown in Fig. 7b. Typical electrode voltages are: cathode potential  $V_C = -100V$ , beam shaping electrode  $V_1 = -102V$ , grid potential  $V_2 = +100V$ , source potential  $V_S = 0$  (all voltages are shown relative to the ionization chamber, or source, potential), and ion extraction electrode potential  $V_E = -5V$ , for example, although the lens system  $V_C$  through  $V_S$  can be operated over a broad range of voltages and electron energies to optimize performance in producing the ions of interest to a particular implantation process.  $V_E$  is a bias voltage on the ion extraction aperture 177, which establishes a constant drift field  $E$  as also indicated in Fig. 7b.  $E$  imparts a drift velocity to the ions created within the ionization chamber, attracting positively charged ions toward the ion extraction aperture plate 177, where they can be efficiently extracted by an external extraction field to form the ion beam. Since the ions are created along the electron beam 173,  $E$  tends to provide forward momentum to the ions, such that their lateral component of kinetic energy is essentially thermal, *i.e.*, of magnitude  $\ll 1eV$ . Fig. 8 shows the triode filament injection embodiment of Figs. 7a and 7b incorporated into an ion source similar to that depicted in Fig. 3. Fig. 8 shows a detail of the ionization chamber 175 and triode 200, and shows the triode contained within the source block 35. The other elements of Fig. 3 such as low-temperature

vaporizer 28, gate valves 100 and 110, mounting flange 36 and gas feed 33, for example, are part of this embodiment as well, although not shown. However, the electron gun 42, magnet coils 90, and beam dump 70 are not part of the embodiment of Fig. 8, since these electron gun-related components have been replaced by the triode 200. Some further advantages of the approach of Fig. 8 are: 1) the filament is remoted to a lower pressure location (by directly exposing it to ambient vacuum within the source vacuum housing through vacuum conductances 190, for example), enhancing filament life; 2) remoting of the filament prevents contamination of the ionization chamber by the filament material; 3) the lens system facilitates accel-decel transport of the electron beam, enabling higher electron currents to be achieved within the ionization chamber. 4) The radiative heat load produced by filament 170 is conveniently conducted away in large part by the water-cooled source aluminum block 35. 5) The electron beam can be made to focus on the ion extraction aperture, resulting in a high ion extraction efficiency, and small lateral momentum. This last is due to the fact that the nominal electron trajectories are along the drift field  $E$  in Fig. 7b, such that the ions which are created by electron impact reach the ion extraction aperture having essentially a thermal lateral component of kinetic energy, *i.e.*,  $<<1\text{eV}$ . 6) The embodiment of Fig. 7b and Fig. 8 results in a low-emittance, high-brightness source of ions, enabling improved control of ion beam propagation through the implanter, and much improved spatial and angular uniformity of the ion beam on the wafer substrate, relative to the prior art.

Fig. 7c shows a tetrode geometry similar to the triode of Fig. 7b, but also having dimensional information. Dimensions are given in mm. The tetrode enables true zoom capability, so that the focusing properties of the lens system are somewhat independent of the final electron energy. This allows for extraction of the electrons emitted from the refractory filament 170' at a higher energy than the electrons entering the ionization chamber 175', *i.e.*, using deceleration to deliver higher, space charge-limited electron currents into the ionization region. Representative lens voltages are shown in Table A, given for an object distance of 4 lens aperture diameters ("D") and an image distance of 6D from the reference plane of the tetrode. These lens tunings inject 100eV electrons into the ionization region by extracting the electrons at energies ranging from 300eV to 100eV. These tunings assume that the electrons have 100eV upon entering the ionization chamber. Since these lenses are one-dimensional, they do not focus or confine the beam in the long ( $y$ -direction) dimension of the slot. At high current density, the

electron beam expands along  $y$  due to space-charge repulsion, resulting in beam loss through vignetting. Space charge repulsion and beam loss can be much reduced by allowing positive ions to be produced along the beam path by electron-impact ionization. The positive space charge of the ions compensates for the negative space charge of the electrons, reducing the net coulomb repulsion between electrons within the beam, thus reducing beam blow-up and enabling higher electron currents than otherwise possible. In order to prevent ions created in the ionization region 181' from being extracted and lost into the tetrode, lens element 180' is always maintained at a substantially positive potential relative to  $V_0$ , the ionization chamber potential.

The creation of positive ions in the beam path is an effective means for reducing space charge forces: since the ions are heavy and slow-moving, their depletion rate is low, and a reasonable charge balance can be maintained if the rate of ion production is similar to the ion loss rate. The ion production rate at any point in the electron beam path is proportional to the local pressure of ionizable gas at that point. For example, consider local gas pressures  $P_1 > P_2 > P_3 > P_4$  shown in Fig. 7c (I note that it is possible to control the local pressures  $P_i$  by tailoring the conductance between individual lens elements and the ambient vacuum). Further consider the predominant gas species being decaborane ( $B_{10}H_{14}$ ), a large, heavy molecule with a large electron-impact ionization cross section for the production of positive ions. Within the ionization chamber 175',  $P_1$  is highest, approximately  $10^{-3}$  Torr, so that space charge compensation is very effective; ideally, the charge density of ions is the same as the electron density. This ensures uniform propagation of the electron beam within the primary ionization region, ensuring good uniformity of the ion density adjacent to the ion extraction aperture 176', and hence a uniform ion density in the extracted ion beam.  $P_4$  is the ambient pressure of the source vacuum housing (nominally  $10^{-5}$  Torr or less), and because the gas within the ionization chamber 175' propagates through electron beam entrance aperture 174'', a large pressure gradient is established between these extrema. Since the deceleration lens 153 is close to 45',  $P_2$  is relatively high, and space charge repulsion is reduced substantially. The region  $P_3$  is adjacent to the cathode 143', hence it is desired to maintain  $P_3$  close to  $P_4$ , i.e., at a sufficiently low pressure that the arrival rate of decaborane molecules to the cathode surface is less than the desorption rate of decaborane byproducts which can deposit on the cathode surface. This is particularly important for low-temperature cathodes such as  $LaB_6$ , and for field emitter cathodes.

In general, refractory metal cathodes operate at sufficiently high temperatures that deposition of cracked process gases is not a problem.

In another embodiment, Fig. 9 shows the top view of a hybrid source which incorporates the design and operating features of the first two embodiments. It is analogous to Fig. 7b, but shows to intersection of the round electron beam 210 (shown going into the plane of the drawing) with the ribbon electron beam 173 from the long filament emitter-based triode 200. Thus, this third embodiment has both an axially-positioned, long filament emitter and a longitudinal electron beam. Fig. 10 shows a detail of the present embodiment incorporated into the ion source, which is a modification of Fig. 3. In addition to the low-temperature vaporizer 28 shown in Fig. 3, Fig. 10 further incorporates a high-temperature vaporizer 220 enclosed by the source block 35. Vaporizer 210 is positioned within source block 35 such that it does not interfere with the vapor conduit 32 or the gas feed 33 of Fig. 3. Vapor is conducted from vaporizer 220 to the volume within ionization chamber 175 by vapor conduit 225, shown in Fig. 10. The purpose of this second vaporizer 220 is to introduce vapors from solid dopant compounds such as elemental P, As and Sb, and also  $\text{Sb}_2\text{O}_3$  and  $\text{InCl}_3$ , for example. Thus, vapors of these and other commonly-used solid dopants, as well as vapors of special low-temperature materials such as  $\text{B}_{10}\text{H}_{14}$  and trimethyl indium (TMI) can be introduced into the ionization chamber 44 by the embodiment of Fig. 10.

The features and advantages of the embodiment of Figs. 9 and 10 are: 1) high ion beam currents can be obtained; 2) lack of a magnetic field, combined with a high electron density near the extraction aperture, and the creation of ions in a path along the drift field direction, result in a very low-emittance source of ions. 3) A full complement of solid and gaseous feed materials can be used, and the incorporation of two vaporizers can accommodate both n- and p-type dopants without requiring servicing of the ion source between the different implants; 4) the low-energy electron beam produced by the filament, in conjunction with a higher-energy electron beam provided by the e-gun, enables the production of multiply-charged ion species through a stepwise ionization process in which copious amounts of singly-charged species are produced by the low-energy beam, which are again ionized by the higher-energy beam, resulting in multiply-ionized species. 5) The ability to "tune" the electron beam energy of the several electron sources gives

the ion source of Fig. 9 great flexibility in producing different cracking patterns of molecular feed species, allowing the tailoring of the ion beam contents to specific implant requirements.

#### Drain Extensions

5 It is proposed that the technology disclosed herein has significant advantages when applied to the process of implanting the drain extension of a transistor that will result in a higher performance device. The basic concept is that the disclosed sources will provide a beam with low emittance, which in turn will create a junction with reduced lateral abruptness, which gives the transistor higher performance in exactly the ways needed for scaled technologies.

10 The transistor with a more abrupt lateral junction will have improved performance in several ways. First, the junction region contributes a component to the series resistance, and the more abrupt junction will contribute less series resistance, which in turn increases the drive current and transconductance of the transistor. The abrupt junction also reduces subthreshold conduction, which is very important as the supply voltage is reduced. One benefit of this feature  
15 is the reduction of off-state current, which would reduce the static current of the entire circuit, extending battery life, for instance. Improved subthreshold characteristics also allow for more freedom in the overall design of the technology, allowing the reduction of the threshold voltage without increasing static current. This allows a direct tradeoff between circuit performance (improved by lower threshold voltages) and the standby power (which is improved  
20 by reducing static current). These features are increasingly important as the supply voltage is reduced, as it is with each generation of technology beyond 0.25um.

Within the field of ion implantation, a beam of ions is produced and transported to an impact target, with some degree of energy which causes the ions to enter the target material and penetrate to some depth. This is shown diagrammatically in figure 11. The target is typically a  
25 silicon wafer 1 where a transistor or other structure is being fabricated. The ion beam 2 is directed at the silicon wafer 1 to intentionally place the ions into the silicon into some feature that contributes to the creation of a functional device. The ions do not all travel along the same path, but rather create a distribution of atoms within the silicon, as shown by the depth profile 5 in figure 1. The depth profile is generally characterized by two parameters: the projected range  
30 6 which is the average depth of penetration, and the straggle 7 which is a measure of the variation in depth of the atom distribution. These parameters depend strongly on the conditions

of the ion beam being used for the implantation process, with heavier ions or those with lower energy producing shallower profiles. Generally analysis of ion implantation processes only consider an ion beam 2 which is entirely parallel, which allows direct computation of the expected profile, projected range and straggle. However, ion beams are not entirely parallel.

5 There always exists some fraction of the beam that is not parallel, such as the illustrated nonparallel ion 4. Nonparallel ion 4 will impact the silicon substrate at a nonzero angle of incidence 3. In general, all ion beams contain non parallel components, the magnitude of which depend strongly on the beam conditions, the implantation equipment details, and the tuning of the implanter. Some of the implications of the various ion angles contained in the ion beam are  
10 discussed below.

There are several ways to characterize the non parallel components of the ion beam. First, as the beam 10 is created and leaves the ion source 9, the emittance 8 can be measured to characterize the angular distribution of beam 10, as illustrated in Figure 12. This parameter is a measure of the total angular distribution of the beam as it is extracted from the source, and is  
15 usually expressed in terms of the solid angle. Once the ion beam is being transported down the beamline, the terminology generally used to discuss the angular distribution is the divergence 11. Divergence 11 refers to the maximum angle of the beam relative to the beam axis. When the beam reaches the target, each ion has an angle of incidence as described above, because the target might be tilted relative to the beam axis for specific process effects. Thus, beam  
20 divergence 11 generates a range of incident angles when the beam reaches the target. It is important to note that these terms and parameters are limiting: the beam actually contains ions traveling at many angles, and there is a distribution function which would describe the beam density as a function of divergence angle. Still, these terms are useful because much of the following discussion relates to the ions with the largest angles.

25 One exemplary ion implantation process discussed herein is the drain extension implant. This is one step in the formation of a transistor: see figure 13. The drain extension implant is very important because it forms the structures that define the most important aspects of transistor functionality. First, it is the means by which self-alignment is accomplished: the gate electrode 13/ gate oxide 12 stack is patterned to create a well defined gate edge 14. The feature masks the  
30 ion beam 2 which is going to form the drain extension. Where the gate stack has been removed, the implant penetrates into the silicon and forms an implanted layer which is the drain extension

15, but where the gate stack has not been removed the implant penetrates into the gate electrode  
16. This process results in the drain extension junction being aligned with the gate electrode,  
which makes a good transistor structure and is known as a self-aligned gate. As further  
discussed below, nonparallel ions 4 and especially those that are directed under the gate and  
5 impact the silicon at the base of the gate edge, like the ion shown in figure 3 are of particular  
interest.

An important aspect of semiconductor technology is the requirement for constant scaling.  
Scaling is the process by which all dimensions are reduced so that more transistors can be placed  
in a given silicon area, reducing the cost per function. For ion implantation, the result is a  
10 constant need to reduce the ion energy, because reducing dimensions also includes reducing the  
ion depth dimension, and this is accomplished by reducing the implant energy. Notably, many  
aspects of semiconductor technology must continuously develop new methods, equipment and  
materials to keep up with the industry demands for scaling, and ion implantation is included.  
This scaling has progressed sufficiently to create a major issue for ion implantation: challenge to  
15 make the junctions shallow enough to meet scaling requirements. The most severe issue relates  
to the formation of the p-type junctions since the boron atoms used are light and tend to penetrate  
deep into the silicon. In particular, the p-type drain extension is the most challenging implant  
because it uses the lowest energy boron beam. It is noted that there are fundamental problems  
with ion implanters delivering high current beams at low energy, and the methods being used to  
20 improve the low energy boron beam currents have adverse effects on the quality of the beam  
delivered, especially its divergence.

The ion implantation is not the only step required to form the drain extension. In  
addition, a heat treatment or annealing step must be performed to make the implanted atoms  
electrically active. Another problem is that this heat treatment must be performed at a high  
25 temperature (i.e. > 900C) such that there are also diffusion effects to consider. Diffusion is the  
movement of implanted ions out of their as-implanted depth profile, and generally deeper and  
laterally within the substrate. Since the challenge is to make a shallow junction (actually Ultra-  
Shallow Junction, or USJ), diffusion effects must be minimized. There is also an additional issue  
as the diffusion time is minimized: an effect known as transient-enhanced diffusion (TED). This  
30 effect is a result of silicon interstitials present in the implanted layer due to the implantation  
damage to the silicon crystal caused by the ion implantation. The result is a strong enhancement

of the boron diffusion, which only lasts a short time. However, a short anneal cycle is desirable to minimize diffusion, and so the TED effect increases the need to shorten annealing time. It is noted that diffusion, and TED, move the implanted layer both in depth and laterally. There is much development of advanced annealing equipment and processes to perform this critical  
5 process, and whatever is developed to keep the junctions shallow will also provide a benefit in improving the lateral abruptness.

The scaling of the boron implant energy has produced a crisis for boron implantation: low productivity due to low current delivery capability. Since the need is for high ion currents at low ion energy, the result is a situation where the beam has high space charge density, which  
10 creates problems. At beam extraction from the source, the space charge density tends to compensate the extraction field and results in the well known  $E^{3/2}$  relationship between beam current and energy. This effect dramatically reduces the available beam current as the energy is reduced. In addition, the space charge of the beam during transport tends to create a Coulomb force which pushes the ions laterally out of the beam, resulting in "beam blowup" and a loss of  
15 beam current as the beam is transported down the beamline. This effect is also strongly energy dependent, with the result that it is very difficult to deliver Low Energy Boron (LEB) ion beams to the silicon wafer target.

There have been two approaches to addressing the issue of LEB beam current by the implant industry, both of which result in a more divergent beam at the wafer. The first approach  
20 is to design a beamline with the shortest possible distance between the source and the silicon wafer, which allows more of the beam to reach the wafer. These short beamline are also made with a more open transport bath, so that a larger beam is able to transit the length. In terms of the beam divergence, this approach results in higher divergence of the beam at the wafer. The second approach to increasing LEB ion current is the use of deceleration. In this approach, the  
25 beam is extracted and transported most of the way to the wafer at higher energy, and then the beam is decelerated right before the wafer to implant at the correct energy. This approach also results in higher divergence at the wafer, and also introduces energy contamination to the beam on wafer.

The most important part of the depth profile is at the junction edge, as shown in Figs. 14a  
30 and 14b. As illustrated, the implanted boron layer interacts with the existing doping concentration to form a P/N junction. The gate edge and drain extension layer is shown in Fig



14a, where a lateral cut is shown (A-A' 17) which is below and parallel to the silicon surface. In Fig 14b, the doping concentrations are shown along the A-A cut. In the region of the drain extension, the boron concentration 18 is high, of order  $1E20\text{ cm}^{-3}$ , which is shown as a high value on the log scale 19. Prior to the LEB implant for the drain extension, there was an N-type  
5 doping concentration 20 already established, which is shown as Phosphorus, but could be any kind of N-type dopant. The critical feature is the spot where the two doping concentrations are equal, which is the junction edge, 21. The value of the concentrations is much lower here, since the N-type concentration is more likely to be of the order  $E17\text{-}E18\text{ cm}^{-3}$ . Thus, the boron concentration 18 is also of this magnitude at this spot. It is now noted that the boron  
10 concentration at the junction edge is much less than the concentration within the drain extension, by at least 100X. This is important because it shows that a small component of the beam, of order 1%, can be very influential in determination of the junction edge, as will be further described below. In addition, the slope of the boron profile in the lateral direction at the junction edge is defined as the lateral abruptness of the drain junction. This parameter is usually  
15 expressed in units of nm/decade, or the lateral extent of the profile, in nm, required to move up one order of magnitude in boron concentration. A typical value of the drain lateral abruptness, for  $0.18\mu\text{m}$  technology, would be 10nm/dec, while requirements for future scaling reduce with each generation with a goal of  $<5\text{nm/decade}$ .

A low divergence beam, such as that of the present invention, when used to form the  
20 drain extension, will improve the lateral abruptness of the drain extension and result in a higher performance transistor. Two mechanisms contribute to this advantage: reduced lateral penetration and reduced lateral straggle.

The first component, lateral penetration, is strictly geometric. Referring to figure 13, a beam with low divergence essentially places all of the incoming ions within the drain extension  
25 region, out from under the gate edge, which is desired. A divergent beam will have nonparallel ions incoming, and we are particularly interested in those nonparallel ions positioned exactly as depicted in Fig 13, where the spot where the ion penetrates the silicon substrate is right at the base of the gate edge 14. This ion, on average, will come to rest at the position marked with the X, which is laterally displaced from the primary distribution of drain extension boron atoms.  
30 Since there is a distribution of incident angles within a divergent beam, the result is a lateral extension of the profile under the gate edge. This produces a graded junction in the lateral

direction which is not as abrupt as that which would be produced by a low divergence beam. As discussed above, the concentration at the junction edge is much lower than the peak concentration in the drain extension, so it only takes a small fraction (1%) of the beam to have high divergence to significantly extend the junction laterally. In addition, there generally is a distribution of angles within the beam where the higher angles have less intensity, also contributing to a laterally graded junction. For an estimate of the degree of improvement with a low divergence beam, we can estimate the lateral displacement by the sine of the incident angle times the depth to the vertical junction edge. If we use 7 degrees for our divergent beam, the lateral displacement is 12% of the junction depth, while the normal estimate is the lateral junction edge is at 70% of the junction depth. Since this would now place the lateral junction at 82% of the vertical junction depth, the divergent beam produced a junction 17% more extended than a low divergence beam would (for this effect).

The second mechanism involved with beam divergence and lateral junction formation is the lateral straggle. Straggle occurs because the silicon target is not a uniform homogenous medium and is rather a crystalline lattice with individual atoms arranged in a regular pattern with space in between. The incoming ions may either hit a silicon atom directly, hit a silicon atom with a glancing incidence, or miss the silicon atoms completely. This statistical process results in a distribution of conditions for the various incoming boron ions. The straggle is normally considered as a vertical variation in the depth profile, but a masked edge like our present case also involves lateral straggle. The important factor is that the lateral straggle is dependent on the incident angle, with divergent ions producing more lateral straggle. For a more detailed discussion of this phenomenon, the reader is referred to reference: Nakagawa, Hada and Thome, IIT '98, p 767. One of the figures from this reference is reproduced as Figure 15 illustrating the results of calculations of the lateral straggle as a function of the incident angle,  $\theta$ , and the ion energy. The normal expectation of 70% lateral to vertical straggle is shown as the dashed, relatively horizontal line, which is explicitly noted as assuming a zero angle of incidence. The data points are for various incident angles and energies, but it is seen that it is quite likely that ions incident with an angle of 7 degrees has at least double the lateral straggle of the conventional model. It is also noted that the effect is larger for higher angles, so the distribution spreads out laterally, which is exactly the opposite of the desire to keep the junction abrupt.

Referring now to Figs. 16a and 16b, in order to make numerical estimates of the relative magnitudes of these effects, a model is constructed which resolves these effects into the same terms. The first step in the model is to reduce the variables by making an approximation: the vertical junction depth is equal to the projected range ( $R_p$ ) plus two times the vertical straggle ( $\Delta R_p$ ) or

$$X_j = R_p + 2\Delta R_p$$

This allows the expression of the lateral junction position in terms of the vertical straggle, since the relationships have already been expressed.

The low divergence lateral junction edge occurs at a position which is two times the lateral straggle by this model. Since we already know that the lateral straggle is 0.7 times the vertical straggle, the lateral junction edge occurs at  $1.4\Delta R_p$  inside the gate edge. Now, the divergent beam case includes two terms, which add to produce the lateral junction edge. The first term is that the lateral straggle is twice the normal incidence case, so this contribution is  $2.8\Delta R_p$ . The second term is the geometric effect which was 12% of the junction depth, which is now  $0.48\Delta R_p$ . Adding this to the other term produces a lateral junction edge which occurs at a position  $3.28\Delta R_p$  inside the gate edge, or 2.3 times more extended in the lateral direction. The lateral abruptness will also be improved by a similar ratio. This is a dramatic advantage which directly results from having a source with low emittance.

Another critical parameter associated with an MOS transistor is the channel length. The channel length is the distance between the source and drain, that is, between the lateral junction edge of the source and the drain. While the discussion so far has centered on the drain side of the transistor, there is another region on the other side of the gate which forms the source at the same time that the drain is formed. It is important to note that it is the lateral extension of the source and drain that determine the channel length. The implantation profile is determined by the implantation parameters, most importantly species and energy, but also tilt, twist, mask edge, and beam divergence. Once again, the beam emittance determines the beam divergence, and thus has an impact on the transistor formation. It is clear that the channel length will be longer for the low divergence beam, since there is less ion beam penetrating under the gate stack. It is

not a benefit to have longer channel lengths in general, but the low divergence case produces a transistor closer to the ideal situation where the channel length is the same as the gate length.

For this case, the problem with the high divergence beam is that the divergence is not always the same. This is a natural result for beam conditions with significant divergence, because of the natural variation with beam tuning and setup. The variation comes because any time that the beam intersects an aperture, some of the beam is lost, and part of the divergence envelope is also lost, because there is a direct relationship between the position in space and the angle that that part of the beam will have with the substrate when it gets there. For example, take two conditions: one with the beam setup centered on an aperture and one where the aperture clips part of the beam. For the centered case, the divergence will also be centered, and so the beam intersects the wafer with the nominal angle plus or minus the same amount, say  $\pm 5$  degrees. For the second case, the edge of the beam, which is clipped by the aperture, is also the extreme of the angular spread, which is only taken off of one side. So, in this case, the angle at the substrate might be the nominal angle with asymmetric divergence, say  $+2/-5$  degrees. Now, if the side where the divergence has been clipped is the side which is defining the edges of the transistor channel, we have changed the junction profile by eliminating the high angle ions, such that the channel would now likely be longer because the ions did not penetrate as far under the gate edge. This variation in channel length is highly undesirable, and a beam with low emittance would not be subject to this variability. It is noted that the variations discussed are normal, and are a result of the automation of modern equipment. In today's production tools, an automatic routine establishes the beam conditions, running a sequence of prescribed steps to establish and optimize the beam conditions. It is normal that this system does not reach the same beam conditions each time; its task is to create a beam consistent with the requirements, and there are always many solutions to the tuning problem. These tuning solutions produce different divergences in the beam itself, it is not necessary to have an off center beam, or any abnormal condition, to create beams with variable divergence.

Another benefit of the low emittance ion beam would be the ability to design the process so that the channel lengths are uniformly small, rather than having to design so that the shortest channel only occurs for worst case conditions. Since the performance of the circuit is directly connected to the channel length, the ability to produce uniformly short channels directly allows higher performance to be realized, for all other process steps being unchanged.

Note that channels too short are likely to fail, either because the drain to source voltage cannot be sustained because the channel is too short, or that the threshold voltage falls out of the operational range due to short channel effects. So, in the process of designing the process and the circuit, the distribution of channel lengths produced by the normal range of process variation must be conservatively considered, so that none of the transistors fail (failure rates of even one ppm are too large). Stated another way, the distribution of channel lengths shows less variation, and this allows the average channel length to be designed to be smaller, resulting in higher performance at no additional cost.

#### 10 Extended Ribbon-Beams

There is currently great interest in extending the design of conventional ion implanters to produce ribbon beams of larger extent than heretofore. This interest in extended ribbon beam implantation is generated by several factors: 1) the recent industry-wide move to larger substrates, *i.e.*, 300mm-diameter silicon wafers; 2) the expectation that even larger substrates, *i.e.*, 450mm-diameter silicon wafers, will be put into production for conventional CMOS and other device manufacturing, and 3) the recent industry-wide move towards serial implanter designs which can benefit greatly from the incorporation of electromagnetically-scanned extended ribbon beams in order to increase wafer throughput, and to improve dose uniformity across the substrate. Since in conventional ion implant the wafer throughput tends to decrease with increasing substrate size and is inversely proportional to substrate area, and further, since the expected economic benefits inherent in the use of large-area substrates cannot be realized unless wafer throughput is kept roughly constant, the ability to deliver significantly higher ion beam currents is critical to the continued success of ion implant in silicon device manufacturing. While the beam current (hence dose rate) delivered to the wafer can scale with the length of the ribbon beam, this requirement is hindered by prior art ion sources for the following reasons: 1) prior art ion implantation sources can only produce ribbons of a limited extent (up to between two and three inches long), and 2) if the extended ribbon beam is produced by beam expanding optics, the current density in the beam drops in proportion to the magnification, such that the total current delivered to the large substrate is unchanged.

30 By utilizing the technology I described previously in embodiment 1, 2, and 3, I can produce ribbon beams of almost arbitrary extent as extracted directly from the ion source. This

is accomplished by simply scaling the length of the ion source as indicated in Fig. 17. Fig. 17 shows an embodiment similar to that of Fig. 4, namely an electron gun 230 delivering a variable-energy electron beam 235 into a ionization chamber 240 filled with dopant-containing gas, and intercepted by a water-cooled beam dump 250. The electron beam propagates parallel to, and adjacent to, ion extraction aperture 260 from which an ion beam is extracted by extraction optics. An optional external magnetic field **B** is provided by magnet coils (not shown). The use of a longitudinal magnetic field oriented parallel to the path of the electron beam will confine the electron beam 235 over even a very long path length. The path length is given by  $(x + y)$  as indicated in Fig. 17, where  $x$  is the extent of the electron gun, and  $y$  is the extent of the ionization chamber ( $y$  is also roughly the length of the ion extraction aperture, and the desired length of the extracted ribbon ion beam 270). I envision the profile of the ionization chamber 240 to be cylindrical, with the extraction aperture occupying a flat face of the cylinder.

The arrangement of Fig. 17 can be advantageously used as an ion source for the ion doping of flat panel displays. For example, the ion extraction aperture 260 can be 850mm long for producing ribbon beams to implant rectangular panels having a short dimension of 750mm. In this case, the ionization chamber length  $y$  in Fig. 17 would be longer than 850mm, for example 900mm. Electron gun 230 is designed to deliver a high current, low energy electron beam 235 into ionization chamber 240. Typical specifications are: cylindrical lens diameter = 1 inch, electron beam energy = 100 eV (adjustable between 20eV and 250 eV), maximum electron current = 200 mA, electron current dynamic range = 400 (i.e., electron current is adjustable between 500  $\mu$ A and 200 mA). The electron beam is confined both in the electron gun and in the ionization chamber by an external magnetic field **B** produced by a pair of magnet coils. It is important that the electron beam be well-confined and collimated by **B** because of the long electron beam path length through the ion source. A magnetic flux density of between 50 G and 200 G is applied in order to maintain good uniformity of ion production (ion density) across the length of the ion extraction aperture 260 by limiting spreading of the electron beam diameter as it propagates through the ionization chamber 240 due to space-charge forces within the low-energy electron beam. The uniformity of ion generation along the aperture is further improved by reducing the feed gas pressure (relative to typical prior art ion source pressure which ranges between about  $4 \times 10^{-4}$  Torr and  $4 \times 10^{-3}$  Torr) within the ionization chamber 240 so that a smaller fraction of electrons are scattered out of the beam, for example an ionization chamber pressure of

$1 \times 10^{-3}$  Torr or less. We note that prior art, plasma-based ion sources cannot operate at significantly reduced pressure since the plasma cannot be sustained at low pressure. This low-pressure operating mode can reduce process gas consumption in ion doping systems by more than an order of magnitude, significantly reducing tool cost of ownership (COO).

5 A further, dramatic reduction of COO is illustrated in Fig. 18b, which shows a dual ion source system 600 with dual-slit extraction optics 610. A single pair of large-diameter magnet coils 620 provides a uniform magnetic field which encompasses both ion sources. The embodiment of Fig. 18b enables both n- and p-type dopants to be implanted in a single ion doping tool by dedicating n-type (e.g., phosphorus) materials in source 1, and p-type materials  
10 (e.g., boron) in source 2. Sources 1 and 2 are not typically run at the same time. If desired, both ion sources can be run simultaneously with the same dopant, producing two ribbon beams, doubling the implanted dose rate. Fig. 18b illustrates two ribbon ion beams being generated, beam 630 (e.g., boron-containing), and beam 640 (e.g., phosphorus-containing).

Fig. 18b shows the dual ion source of Fig. 18a doping a rectangular panel 650 with  
15 ribbon beam 660. In this illustrative example, panel 650 is mounted on scan stage 670 and mechanically scanned along direction 680, along the long dimension of the panel 650. Note that in this case, ion beam 660 is indicated as longer than the short dimension of the panel.

Fig. 19 shows a generic ion doping system for the doping of flat panels. Panel 690 is loaded from vacuum cassette 700 into process chamber 710, rotated through 90 degrees, and  
20 scanned vertically in front of ion beam 660'. The dual ion source 600' of Fig. 18a, 18b is shown integrated onto the system in schematic. Magnet coils and details of mechanical feedthroughs are not included, for clarity.

The p-type feed gases of choice in ion doping are diborane ( $B_2H_6$ ) and boron trifluoride ( $BF_3$ ). Since there is no mass analysis between the ion source and the substrate, all ions  
25 produced in the ion source are implanted into the substrate. This makes the use of  $BF_3$  problematic, since fluorine is detrimental to oxides, for example, and has undesirable process effects. Also, there is three times as much fluorine as boron in the source plasma, so much F can be implanted. In the case of  $B_2H_6$ , which most manufacturers prefer to  $BF_3$  since there is not much process effect from H implantation (H implantation causes excess heating of the substrate,  
30 for example), there are two major complaints: 1) extensive cracking pattern (many different ions produced, for example, significant fractions of  $H^+$  and  $BH_x^+$ , as well as  $B_2H_x^+$ . This results in a

broad end-of range implantation due to the variety of effective boron energies implanted into the sample. 2) Insufficient beam current resulting in low throughput, due to the fact that, in a conventional bucket-type source, most of the boron-containing ions produced are deposited on the walls of the ion source chamber.

5           The use of the ion source of Fig. 17 and the substitution of decaborane as a feed gas material solves problems 1) and 2), since high currents of a 70% pure B<sub>10</sub>H<sub>x</sub> beam is produced (as shown in Fig. 19a, a NIST-traceable spectrum of decaborane), the surface area of my ion source is orders of magnitude smaller than in a bucket source, and the ion source of Fig. 17 demonstrates a high ion extraction efficiency. The net result is that the use of the ion source of Fig. 17 running decaborane enables much higher throughput, much lower COO, and much less particulate formation (since less material is accumulated in the ion source) than the prior art.

#### Acceleration/Deceleration Techniques

15           The production of high-brightness ion beams is very important in ion implanters which employ deceleration of the ion beam prior to its impact with the substrate, since both the angular divergence of the decelerated beam and its spatial extent are increased after deceleration. To produce a small angular divergence beam on the target substrate with good spatial uniformity after deceleration, an initially low-emittance beam is required. Since the beam emittance (product of the beam diameters and angular divergences in two orthogonal directions) is  
20           inversely proportional to energy, the emittance of the upstream beam must be smaller than that desired at the substrate by at least an amount equal to the deceleration ratio. While the beam emittance can always be kept below a given value by the addition of a series of apertures, the resulting beam flux is unacceptably low. Therefore, the use of a high-brightness ion source is desirable, where brightness is defined as beam current divided by emittance (i.e., beam current  
25           per unit area per unit solid angle). The brightness is unchanged by such a series of apertures, and hence is a useful figure of merit.

          Certain production implants, such as creation of drain extensions, require both low angular divergence at the substrate and low energy ions, which work against each other unless a high-brightness source is used. The net result is that a much higher implanted dose rate is  
30           achieved with the high brightness beam than with a beam of lesser brightness. This directly leads to higher product throughput, and lower cost devices.



The use of ionized clusters, which contain a single charge but multiple dopant atoms, enables higher brightness beams especially if we replace beam current by dose rate, or "effective" beam current. Since a singly-charged cluster of  $n$  atoms must be accelerated to  $n$  times the energy, the emittance of a cluster beam is  $n$  times smaller than that of a process-equivalent monomer beam. Since the dose rate is also  $n$  times the electrical ion current, the total increase in brightness of a given current of cluster beam is  $n^2$ , when brightness is defined as dose rate divided by emittance. Thus, the use of a high-brightness ion source which can produce cluster ion beams is an enabling technology which allows decelerated beams to perform well-controlled implants with small angular divergence, good spatial uniformity, and high throughput.

In particular, Fig. 20, which is substantially the same as Fig. 1 of above-incorporated PCT Application Serial Number US00/33786 and described more thoroughly therein, shows a general schematic of a decel implanter such as is used with conventional boron implantation. Fig. 20 describes a conventional, non-decel implanter. For example, the ion source 548 produces ions which are extracted from a one-dimensional aperture (i.e., an elongated slot) and accelerated to a transport energy significantly greater than the desired final implantation energy by an electrode 553, and are injected into analyzer magnet 543 which disperses the beam laterally according to the mass-to-charge-ratio of the ions. A mass-resolving aperture (slot) 544 allows only the ion of interest (the ion having a preselected mass-to-charge ratio) to pass downstream to a moveable Faraday for measuring ion beam current, or (when the Faraday is retracted) to the deceleration electrode 557. The deceleration electrode 557 decelerates the ion beam to the desired implantation energy, which then impacts the wafer substrate 555. The schematic of Fig 1 illustrates a batch-style implanter with a mechanically rotating and scanning disk 545, but the general approach of decel can also be adopted in serial implanters.

Since there is a finite probability that some of the ions in the ion beam will undergo charge-exchange interactions with the residual gas molecules in the implanter beam line or with other ions in the beam prior to reaching the decel electrode, most acceleration/deceleration implanters also incorporate a neutral beam filter (not shown in Fig. 20) or other type of energy filter (for example,  $E \times B$  filter, electrostatic deflector, dogleg, etc.) to make sure that only ions of a predetermined energy reach the wafer, as is known in the art.

Typically, a batch style decel implanter will utilize a stationary ion beam, the scanning of the beam across the wafers being accomplished by the rotating and mechanically scanning disk

545; however, other embodiments are possible. For example, the present invention can, with advantage, be incorporated in a serial-style implanter (one wafer at a time) which accomplishes fast scanning (by either electrostatic scanning plates, or by a directional magnetic field) in one direction, while the wafer holder accomplishes a slower mechanical scan in the orthogonal  
5 direction. Alternatively, dual electromagnetic scanning of a stationary wafer is also possible. Serial-style decel implanters have never to my knowledge been commercialized, I realize such a design would have distinct advantages by being able to accommodate single-wafer processing, as well as enabling high tilt angles (up to 60 degrees) of the wafer holder (not currently possible with batch implanters). High tilt implants can be important in many processes, being preferred,  
10 for example, in "quad" implants for the fabrication of well structures, and for profiling of the S/D extensions. In addition, newer wafer fabrication facilities are expected to adopt single-wafer processing in the future to reduce the risks to expensive 300mm process wafers incurred by batch processing.

Serial implantation requires a much higher degree of uniformity of the beam profile than  
15 in batch-style implantation to maintain good uniformity of the implant across the wafer, and this requirement becomes more difficult to achieve for 300mm versus 200mm diameter substrates. A feature of my invention is combining cluster beam implantation with the acceleration/deceleration technique by a serial, high-current beam line implantation system, the improved profile of the beam, as described, meeting the beam profile uniformity demands  
20 needed for the serial implanter to be production worthy.

Fig. 21 shows one preferred embodiment of the ion source used in the present invention, mounted onto the vacuum housing of a conventional ion implanter. This ion source is fully described in the above referenced PCT Application Serial Number US00/33786, in which it is included as Fig. 9B. The ion source operates on a different principal than conventional ion  
25 sources presently in use in commercial ion implantation, in that the ions are produced not by an arc discharge or by a plasma, but by direct electron-impact ionization by a broad directed beam of energetic primary electrons that transit an ionization volume 516'. This ion source is an enabling technology for ionizing molecular compounds, and provides high currents of decaborane ions, as well as of the dimer-containing compounds of Table 1a. The source  
30 incorporates a low-temperature vaporizer 528 for producing vapors from solid materials having a low melting point such as indium hydroxide, trimethyl indium, and decaborane, for example, and

also incorporates a gas feed 526 which allows the ionization of gaseous compounds such as  $\text{PH}_3$ ,  $\text{AsH}_3$ ,  $\text{GeH}_4$ ,  $\text{B}_2\text{H}_6$ , as well as more common implanter gases such as  $\text{BF}_3$ ,  $\text{SbF}_5$ , and  $\text{PF}_3$ . The embodiment of Fig. 21 shows an extended electron gun which incorporates a 90 degree bending stage or mirror 587 to reduce the footprint of the source assembly for retrofit into existing ion  
5 implanters, and to conserve space while enabling a full complement of electron optics to be incorporated into the electron gun to achieve variation of the electron energy to match the ionization needs of the selected molecular species.

Fig. 23 shows another different embodiment of an ion source and its electron gun, which is also fully disclosed in the above-referenced application. The electron gun operates, itself, on  
10 an acceleration/deceleration principle, and does not use a turning stage. Fig. 23 shows the ion source mounted in a volume of the vacuum housing similar to Fig. 21, but with the housing modified to accommodate the straight-through electron gun design. The embodiment of Fig. 23 also has a set of magnet coils to provide confinement for primary electrons within the ionization volume of the ion source. High electron currents at a controllably variable electron energy can be  
15 injected into the ionization chamber by the electron gun; the majority of electrons which transit the ionization volume are intercepted by a beam dump 536' (Fig. 22).

In the embodiment of Fig. 22, the length of the ionization chamber and the corresponding elongation of the ion extraction aperture is greatly extended, such extended length of the ionization chamber having little negative effect and a very positive advantage on the successful  
20 operation of the ion source. This great elongation is in sharp contrast to the conventional Bernas-style arc discharge ion sources commonly used in ion implantation. In these the arc becomes unstable if the chamber length (and hence the separation between the cathode and repeller) is made significantly longer than the common length while the arc current required to operate the Bernas source would increase dramatically (a conventional Bernas source has a  
25 cathode – repeller separation of about 2 inches, and draws up to 5 A of arc current). By greatly extending the length of the ionization volume and the ion extraction slot aperture, according to the present invention, more ion current can be extracted than in the previous embodiment. Special optics are provided, constructed to reduce the length of the beam profile thus produced as the beam progresses away from the aperture. This approach is illustrated by Fig. 24. Elongated  
30 ionization chamber 500 has an elongated ion extraction aperture 510 from which the ion beam is extracted and accelerated by extraction lens 520. I presently contemplate the extraction aperture

510 to be about six inches in length, three times the length of the extraction slit of a conventional arc discharge chamber of a high-current ion implanter. Extraction lens 520 has the special property of being telescopic; it is a two-stage acceleration lens in which the second focal point of the first lens and the first focal point of the second lens roughly coincide, enabling telescopic  
5 focusing. By constructing the lens 520 to achieve a three-to-one demagnification, the height of the ion beam is substantially reduced while preserving a well-collimated beam trajectory 530 for injection into the implanter's analyzer magnet 540. Heretofore such an ion optical approach would be unsuccessful, since if the ion extraction aperture of a high-current implanter were made much longer to increase extracted beam current of a monomer beam, space-charge forces would  
10 not permit lens 520 to function properly, and the beam trajectory 530 would not be well-collimated; that is, the beam would simply blow up. In fact, the net result would be to extract and inject into the analyzer magnet *less* useful beam current than with a conventional, two-inch aperture! The reason is that in a conventional Bernas arc discharge source used in a conventional high-current implanter, beam transport is fully space-charge limited at extraction, since up to  
15 50mA of ion current (in a  $\text{BF}_3$  plasma, about 30% or up to 15mA is boron,  $\text{B}^+$ ) can be readily produced from a two-inch aperture. The ion source of the present invention, in contrast, can produce 1 mA or more of ion current from a two-inch aperture, of which about 70% is decaborane, so that even from a six-inch aperture, between about 3 mA and 5 mA of ion current should be obtainable. Since this low ion current can be extracted at a much higher energy than  
20 possible in a decel implanter using boron (the deceleration ratio is not arbitrary, but is selected to be within desired energy contamination, and transport limitations, and to achieve desired levels of beam current), it follows that the transport depicted in Fig. 24 is not space-charge limited. Hence, by elongating the extraction aperture of the ion source of the present invention as depicted by Fig. 24, it is anticipated to be possible to triple the beam current, and yet maintain  
25 good beam emittance properties.

### Electron Gun

As an introduction, to the electron gun construction now to be described, it is important to observe that using hot cathode based electron guns of the type disclosed is problematic in a  
30 vacuum environment since radiative loads from the hot cathode and also conductive heat transfer between the cathode lead and the surroundings, and in particular electron bombardment of the

individual lens elements, all conspire to make heat dissipation a significant problem in lens designs which isolate the lenses from objects which are at thermal equilibrium with a cold reservoir. Efforts to create electrically isolating and thermally conductive mechanical paths to conduct heat away from the individual lens elements, the most important of which would be the cathode assembly since it dissipates much of the heat which is dissipated throughout the electron gun, are also highly problematic since the mechanical construction of electrically insulating and thermally conductive paths to a cooled heat reservoir are difficult to achieve in practice and are prone to failure. One possible solution to this problem is to allow the lens elements to float to whatever temperature allows them to be in thermal equilibrium with their surroundings, however, this approach, too, is problematic. Even if one were to construct the lens elements out of refractory materials that could easily maintain an operating temperature of 1000° C or more, interactions with process gas make this an unsatisfactory solution. In particular the use of decaborane in such an environment would cause cracking of the decaborane upon contact with lens elements and deposition of boron onto the lens elements creating particulates which are deleterious to the implant process in general, could create electrical shorts by the coating of insulators and can also reduce the cathode and ion source lifetime significantly. According to the invention, an elegant temperature control arrangement is achieved by radiative heat transfer and vacuum to a cool body which subtends nearly  $4\pi$  steradians surrounding the lens elements and more specifically heat transferable holders which also accomplish precise registration of the lens elements with each other and also with the ion source per se.

Referring to Fig. 25, a lens element 300 is held by clamping holder 310. Holder 310 is comprised of an elongated rectangular cross-section aluminum rods having large radiative surface which grasps lens 300 via a clamping arrangement. In the embodiment shown, the lens 300 is inserted into a bore by spreading of the clamp through the insertion of a spreading tool, not shown. Alternatively, clamp 310 and lens 300 may be joined through extreme cooling of lens 300 to shrink it to a smaller size than the bore, for example by immersion in a liquid nitrogen bath, and insertion of the cold, reduced diameter lens 300 into clamp 310, subsequently allowing lens 300 to expand to room temperature, thus cold welding the assembly together. These means of mounting and holding lens elements such as lens element 300 produces effective heat transfer across the mated, contacting surfaces and enables radiative heat dissipation from the large surface area of clamp holder 310. To improve the emittance properties of the aluminum

holder 310, the services can be anodized or coated with a colloidal suspension of carbon such as Aquadag®. An additional benefit of the assembly of lens holder 310 and lens element 300 is that the holder and the lens element may be of different material. For example, lens 300 may be constructed of stainless steel which is chemically inert or molybdenum which has very good structural characteristics at high temperature.

Referring to Figs. 26 and 27, the electron gun consists of four discrete and separated lens elements: the cathode assembly 320 followed, in sequence, by first anode 330, focus electrode 340, and exit lens 350, each lens in array to be at different potential held by a respective holder of the general construction just described for holder 310. A gap is provided between lens element 350 and the base of a housing 360 which completely surrounds the assembly of four spaced-apart lens holders. The housing 360 of aluminum maintained at much colder temperature than lens elements 320-350 and allows radiative coupling between the several lens holders 370. This is accomplished by close coupling the base 360a of housing 360 in good thermal contact with a water cooled or temperature controlled source block which has been previously described.

Because of the large contact surface area and the good thermal coupling, which is accomplished by thermally conductive elastomeric seals between base 360a and source block which is temperature controlled, the housing 360 can be maintained at a temperature not too different from the temperature of the source block. Thus, a temperature difference is maintained between the several lens holders 370 and the housing 360, enabling good radiative transfer from the broad radiative surface of the lens holder. Furthermore, the use of radiative cooling enables a stable operating temperature for the electron gun, that is somewhat independent of power dissipated in the gun elements. This stability is due to the nonlinear effect of radiative cooling which is much less efficient at low temperatures than at the very efficient high temperatures. Thus the assembly is, to a degree, self regulating and allows for consistent operating temperature of the electron gun elements.

The several lens holders 370 are constructed in a mostly rectangular profile so that significant surface area is exposed both to neighboring surfaces of the other lens element holders as well as to the surface of the housing 360. This arrangement accomplishes two functions. The first function is that the regions where the highest power dissipation is expected (namely the uppermost lens element comprising the cathode assembly 320 and the bottommost lens, exit lens 350) are directly cooled by close proximity to the heat reservoir represented by housing 360,

whereas some of the power dissipated in the lens element 330 and 340 shown in Fig. 26 is distributed among the lens elements, enabling a more uniform operating temperature to occur. Nevertheless, there is significant radiative loss area exposed to the cooled housing 360 for all the lens elements since four sides of the holders are radiatively exposed to opposing surfaces of the housing. If two or fewer sides of a holder are exposed to neighboring elements and two or greater sides are exposed to the cooled housing 360.

Referring now to Fig. 25, typical dimensions of holder 310 are a length  $l$  of 170 millimeters, width  $w$  of 26 millimeters, and height  $h$  of 12 millimeters. Lens element 300 typically has an inside diameter of 12.5 millimeters and an outside diameter of 16 millimeters.

Turning now to Fig. 26, the overall dimensions of the gun assembly are shown with length  $L$  of 6 inches, height  $H$  of 3 inches, and width  $W$  of 1.5 inches. Feed through 380 contacts the individual lens elements through metal springs indicated by 390 which are electrically isolated from each other by a holder plate 395 of ceramic, which allows mechanical stability of the clips such that when the clips are engaged to the several lens holders 370 they accomplish both electrical contact to the individual elements and also provide indexing and registration to maintain alignment of the lens elements. The lens elements are further constrained and insured to be coaxial by an alumina rod 400 which passes through several alumina spacers 410 that are individually counterbored into each of the lens holders 370. This accomplishes both electrical isolation and also controls the spacing between the lens elements and insures alignment in three dimensions.

The lens elements 320, 330, 340, 350 and any subsequent lens must be maintained in a coaxial relationship to a high degree of tolerance to ensure proper focusing of the electron beam and to limit aberrations. The fields that are set up between the lens elements are very sensitive to this alignment, especially in the polar angular coordinates defined by the cylindrical symmetry of the lens system (the  $z$ -axis being along the mechanical axis, i.e., the direction being the direction of propagation of the electron beam), and also the two dimensional spatial coordinates that are transverse to this axis. However, it must be said that the degree of alignment required for the correct direction and focusing of the electron beam is within the normal limits of machining practices and most importantly, of the alignment techniques accomplished by alumina rod 400, individual spacers 410, precision machining of both lens elements 320 through 350 and the several holders 370. The construction of the lens elements in correct alignment ensures that the

beam will propagate in the correct direction through the desired volume in the ionization chamber and also that the beam will be well defined, propagating parallel to the long dimension of the ion extraction aperture. Thus, a small volume ionization region is precisely located adjacent to the ion extraction aperture to achieve high brightness and low emittance, as described above. In addition, proper temperature control of the lens elements is important for the operation of the ion source as a whole to prevent either condensation or decomposition of process gas or process vapor which normally occupies the ionization chamber and therefore penetrates into the electron gun region. Should excessive decomposition or condensation occur in the lens elements it will degrade the overall life time of the ion source and have a negative impact on preventive maintenance intervals. In order to ensure proper ion beam characteristics of the ion extracted from the ion extraction aperture it is important that the ionization region be uniformly located with respect to the ion extraction aperture. Misalignment or defocusing of the electron beam will cause variation in proximity and size of the electron beam and hence the ionization region along the long axis of the ion extraction aperture which is undesirable. However, proper alignment of the electron beam and proper focusing of the electron beam, as achieved by the alignment and coupling features, and temperature stability which have been described for the holders, ensure that ion beam created in the ionization chamber is bright, the transverse energy of the ions is limited, and the ions are created mostly located in front of the aperture, and in a uniform density across the long axis of the aperture. The brightness of the ion beam that is extracted from the ion source which is proportional to the total current and inversely proportional to the emittance of the ions as they exit the ion extraction aperture, becomes higher as the ionization volume is decreased as long as the total current remains constant. Thus with the design described, by achieving a dense electron beam which is well controlled within a small ionization volume, a much brighter source of ions is obtained than would be obtained with a diffuse ionization region created by a defocused or misaligned electron beam.

The brightness properties enabled by this lens and lens holder design, where the brightness of the ion source is maximized is very important when used in an accel-decel (acceleration-deceleration) type ion implanter where the performance of the implant on wafer is directly proportional to the brightness of the ion beam. That is, the characteristics of devices formed by the implanter and also the productivity of the implanter, are directly related to the level of brightness of the ion beam. Therefore this design enables high brightness beams for



accel-decel type implanters to be achieved and thus improves the performance of accel-decel designs.

In the case of using decaborane or similar clusters to further enhance the brightness of beams delivered in any kind of implanter and in particular with respect to accel-decel implant  
5 ions, excellent temperature control of all parts of the ion source including the electron gun elements which are in contact with the decaborane vapor, as achieved here, is critical to the success of the ion source. In particular, it will enable high ion currents to be produced. It will also enable much longer life time and much higher production worthiness in the final ion source and in the implants. Decaborane in particular will dissociate to boron components when it meets  
10 a wall temperature in excess of 350C. Decomposed boron particles can deposit on cathodes and lens elements. If significant boron becomes deposited on the cathode it can degrade the performance of the cathode and significantly reduce ion production, thus limiting lifetime of the cathode. Also boron components can cause lens elements to charge and become less effective at controlling the electron beam and hence reduce the brightness of the ion beam generated by the  
15 ion source. Therefore, good temperature control as achieved by the design just described is critical to successful implementation of decaborane, particularly for accel-decel applications.

## WHAT IS CLAIMED IS:

- 1           1. A method of ion implantation by producing a high brightness ion beam that  
2 extends along an axis by ionizing molecules of a gas or vapor, the molecules containing an  
3 implantable species, the method comprising:  
4           providing an ionization chamber having a restricted outlet aperture,  
5           providing in said ionization chamber said gas or vapor at a pressure substantially  
6 higher than the pressure within an extraction region into which the ions are to be extracted  
7 external to the ionization chamber,  
8           by direct electron impact ionization by primary electrons, ionizing the gas or vapor in  
9 a region adjacent the outlet aperture of the ionization chamber in a manner to produce ions  
10 from the molecules of the gas or vapor to a density of at least about  $10^{10} \text{ cm}^{-3}$  at the aperture  
11 while maintaining conditions that limit the transverse kinetic energy of the ions to less than  
12 about 0.7 eV,  
13           the width of the ionization volume adjacent the aperture, in which said density of ions  
14 is formed, being limited to a width less than about three times the corresponding width of the  
15 outlet aperture; and conditions within the ionization chamber being maintained to prevent  
16 formation of an arc discharge,  
17           by an extraction system, extracting ions formed within the ionization chamber via the  
18 outlet aperture into the extraction region downstream of the aperture,  
19           thereafter, with ion beam optics, transporting the beam to a target surface, and  
20           implanting the ions of the transported ion beam into the target.  
21  
22           2. The method of claim 1 in which conditions are maintained within the ionization  
23 chamber to prevent formation of a plasma.  
24  
25           3. The method of any of the foregoing claims in which the brightness of the ion beam  
26 upon extraction is more than about  $1 \text{ mA-cm}^{-2}\text{-deg}^{-2} \times (E_0/E)$ , where E is the beam energy,  
27 and  $E_0=10\text{keV}$ .  
28

29           4. The method of any of the foregoing claims in which the x-emittance of the beam  
30 upon extraction is less than about  $70 \text{ mm-mrad} \times (E_0/E)^{1/2}$  (where E is the beam energy and  
31  $E_0=10\text{keV}$ ), for an ion current density of at least  $1 \text{ mA/cm}^2$ , even for an ion mass of 120 amu.  
32

33           5. The method of any of the foregoing claims in which the beam noise of the stream  
34 of ions extracted through the outlet aperture is maintained below 1%.  
35

36           6. The method of any of the foregoing claims in which the field strength of any  
37 magnetic  
38 field present in the ionization chamber is less than 70 gauss.  
39

40           7. The method of claim 6 in which the field strength of any magnetic field present in  
41 the ionization chamber is less than 20 gauss.  
42

43           8. The method of claim 7 in which there is substantially no magnetic field present in  
44 the ionization chamber.  
45

46           9. The method of any of the foregoing claims in which any magnetic field present in  
47 the extraction region has a field strength of less than about 20 gauss.  
48

49           10. The method of any of the foregoing claims in which the consumption  
50 of said gas or vapor is maintained less than 10 sccm.  
51

52           11. The method of any of the foregoing claims in which said primary electrons are  
53 introduced into the ionization chamber by electron optics in a directed beam generated  
54 external to said ionization chamber.  
55

56           12. The method of any of the foregoing claims in which each of the molecules to be  
57 ionized respectively comprises or consists of at least two atoms of the implantable species.  
58

59           13. A method of ion implantation comprising

60 producing a high brightness ion beam that extends along an axis by  
61 providing an ionization chamber having an outlet aperture,  
62 providing in the ion chamber molecules of a gas or vapor, in which each  
63 molecule to be ionized comprises or consists of at least two atoms of an implantable species,  
64 ionizing said molecules and extracting ions formed from said molecules under  
65 conditions to produce a beam having, upon extraction, a brightness of upon extraction is  
66 more than about  $1 \text{ mA-cm}^{-2}\text{-deg}^{-2} \times (E_0/E)$ , where E is the beam energy, and  $E_0=10\text{keV}$  and  
67 an x-emittance of less than about  $70 \text{ mm-mrad} \times (E_0/E)^{1/4}$  (where E is the beam energy and  
68  $E_0=10\text{keV}$ ), for an ion current density of at least  $1 \text{ mA/cm}^2$ , even for an ion mass of 120 amu,  
69 thereafter, with ion beam optics,  
70 transporting the beam to a target surface, and  
71 implanting the ions of the transported ion beam into the target.

72  
73 14. The method of claim 12 or 13 in which the molecules are dimers.

74  
75 15. The method of claim 12 or 13 in which the molecules comprise decaborane.

76  
77 16. The method of any of the foregoing claims conducted in a manner to cause the  
78 high brightness ion beam to have a low angular divergence at contact with the target of less  
79 than about one degree relative to said axis.

80  
81 17. The method of claim 16, wherein the step of implanting the ions of the  
82 transported ion beam into the target is employed to cause the high brightness, low divergence  
83 beam to form a drain extension region of a transistor structure on the target, in which the  
84 transistor structure comprises a source, a gate and a drain.

85  
86 18. The method of claim 17 in which the target further comprises a well dopant and  
87 the gate of the transistor structure has a gatelength of 0.20  $\mu\text{m}$  or less, the drain extension  
88 intersecting the gate at a lateral junction edge, the drain extension having a lateral abruptness  
89 of 3 nm/decade or less, wherein lateral abruptness is defined as the lateral extent required to  
90 accomplish a one decade change in the volume concentration of the implanted species at the

lateral junction edge, the junction edge being defined as the region where the volume concentrations of the implanted ions and the well dopant are equal.

19. The method of claim 18 wherein the drain extension has a lateral abruptness of 2 nm/decade or less.

20. The method of any one of claims 17 through 19 in which ions of the high brightness, low angular divergence beam are implanted at opposite ends of the gate, sharply defining a channel beneath the gate.

21. The method of claim 20, wherein sharply defining the channel beneath the gate includes sharply defining the length of the channel.

22. An ion implantation system for implanting at a desired low implant energy into a target substrate comprising an ion source for producing molecular ions (based on a molecule having a cluster of atoms of the desired species to be implanted), an acceleration stage enabling the ions to be accelerated to a transport energy substantially greater than the desired implant energy, and prior to the target substrate, a deceleration stage for lowering the energy of the ions to the desired implant energy.

23. The ion implantation system of claim 22 in which the ion source comprises an electron gun for producing a beam of electrons at controlled energy adapted to ionize the molecules by direct electron impact ionization.

24. The ion implantation system of claim 23 in which the energy of the electrons is between about 20eV and 500eV.

25. The ion implantation system of claims 22, 23 or 24 in which the gun is arranged relative to an ion chamber to cause the beam of electrons to transit the chamber to a beam dump.

122           26. The ion implantation system of any of claims 22-25 in which a lengthy elongated  
123 ionization chamber has a correspondingly elongated slot-form extraction aperture, and  
124 electron optics following the aperture are constructed to reduce the length of the profile of  
125 the resultant beam, relative to the corresponding length of the extraction aperture, prior to the  
126 beam entering the analyzer.

127  
128           27. The ion implantation system of claim 26 in which the electron optics comprise a  
129 telescope.

130  
131           28. The ion implantation system of claim 26 or 27 in which the extraction aperture of  
132 the ionization chamber is of the order of about 6 inches in length.

133  
134           29. The ion implantation system of any of claims 22-28 constructed for batch  
135 operation, a set of wafers being mounted on a carrier that moves relative to the beam to effect  
136 scanning.

137  
138           30. The ion implantation system of any of the preceding claims 22-28 constructed as  
139 a serial ion implanter.

140  
141           31. The ion implantation system of any of claims 22-30 in which the ion source has a  
142 vaporizer mounted integrally with an ionization chamber of the ion source, and temperature  
143 control system for the temperature of the vaporizer.

144  
145           32. The ion implantation system of claim 31 in which the ionization chamber  
146 electron gun and a beam dump to which the beam of electrons is directed are each thermally  
147 isolated from the ionization chamber.

148  
149           33. The ion implantation system of any of claims 22-32 in which the ion source is a  
150 decaborane source and the electron given is constructed to produce a beam of electron energy  
151 between about 50 and 1000 eV.

152

153           34. The ion implantation system of any of the foregoing claims 22-33 in which the  
154 ion source is a source of  $\text{As}_2^+$  ions.

155

156           35. The ion implantation system of any of the foregoing claims 22-33 in which the  
157 ion source is a source of  $\text{P}_2^+$  ions.

158

159           36. The ion implantation system of any of the foregoing claims 22-33 in which the  
160 ion source is a source of  $\text{B}_2^+$  ions.

161

162           37. The ion implantation system of any of the foregoing claims 22-33 in which the  
163 ion source is a source of  $\text{In}_2^+$  ions.

164

165           38. The ion implantation system of any of the foregoing claims 22-33 in which the  
166 ion source is a source of  $\text{Sb}_2^+$  ions.

167

168           39. A method of conducting ion implantation by use of the ion implantation system  
169 of any of the foregoing claims.

170

171           40. The method of ion implantation of ions at a desired implant energy on a target  
172 substrate comprising forming molecular ions (based on a molecule having a cluster of atoms  
173 of the desired species to be implanted, accelerating the ions to and transporting the ions at an  
174 energy substantially above the implant energy, and prior to implant upon the substrate,  
175 decelerating the ions to the implant energy.

176

177           41. The method of claim 40 in which the ions are decaborane.

178

179           42. The method of claim 40 in which the ions are  $\text{P}_2^+$  ions.

180

181           43. The method of claim 40 in which the ions are  $\text{B}_2^+$  ions.

182

183           44. The method of claim 40 in which the ions are  $\text{In}_2^+$  ions.

184

185 45. The method of claim 40 in which the ions are  $\text{Sb}_2^+$ .

186

187 46. An ion implantation system comprising:

188 an ion implanter having an ion extraction system;

189 an ion source capable of providing ions in commercial ion current levels to the ion  
190 extraction system, the ion source including an ionization chamber defined by walls enclosing  
191 an ionization volume, one of said walls defining an extraction aperture of a length and width  
192 sized and arranged to enable the ion current to be extracted from said ionization volume by  
193 said extraction system;

194 an electron gun constructed, sized and arranged with respect to the ionization  
195 chamber to project a directional beam of primary electrons along an axis through the  
196 ionization chamber;

197 a beam dump aligned with the electron gun to receive the directional beam, the beam  
198 dump being maintained at a substantial positive voltage relative to the emitter voltage of the  
199 electron beam gun, the axis of the beam path of said primary electrons extending in a  
200 direction generally adjacent to the aperture, the electron beam having a dimension in the  
201 direction corresponding to the direction of the width of the extraction aperture that is about  
202 the same as or larger than the width of the aperture.

203

204 47. The ion implantation system of claim 46 further comprising a vaporizer arranged  
205 to introduce vapor to the ionization volume, a gas passage for introducing gas from a gas  
206 source to the ionization volume and a control system enabling control of an energy associated  
207 with the primary electrons to ionize individual vapor or gas molecules principally by  
208 collisions with primary electrons from the electron gun.

209

210 48. The ion implantation system of claim 47 wherein the vapor comprises  
211 decaborane.

212

213 49. The ion implantation system of claim of claim 46 in which the directional beam  
214 is a ribbon ion beam.



215

216           50. The ion implantation system of claim 49 in which the ribbon beam is of shorter  
217 extent than the length of the ion extraction aperture.

218

219           51. The ion implantation system of claim 49 in which the ribbon beam is longer than  
220 the ion extraction aperture.

221

222           52. The ion implantation system of claim 49 in which the ribbon beam is about the  
223 same length as the length of the ion extraction aperture.

224

225           53. The ion implantation system of claim 51 in which the length of said aperture is at  
226 least as long as the length or width of a target substrate.

227

228           54. A method of irradiating an extended panel of predetermined dimensions, the  
229 method comprising generating a ribbon ion beam with the ion implantation system of any of  
230 claims 46-53, and directing the ribbon ion beam onto a surface of the extended panel.

231

232           55. The method of claim 54 in which the extended panel is a flat panel, the method  
233 including irradiating the flat panel across substantially an entire panel surface.

234

235           56. The method of claim 55 wherein the ribbon ion beam produced is stationary, the  
236 flat panel being mechanically scanned across the beam to accomplish ion doping of the  
237 panel.

238

239           57. The method of claim 51 in which the length of the ribbon beam is longer than the  
240 flat panel substrate dimension orthogonal to the scan direction.

241

1/31

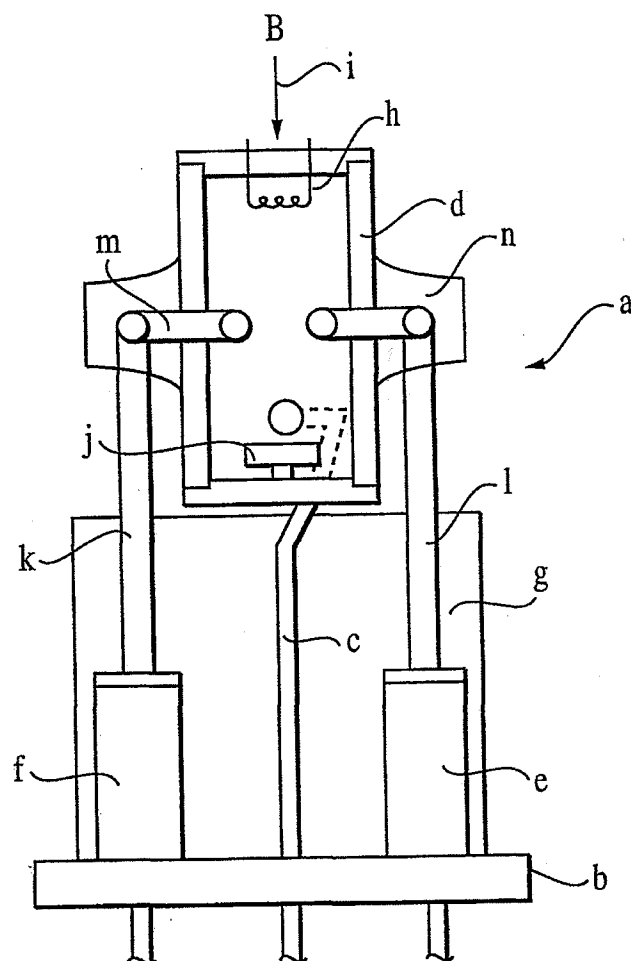


FIG. 1  
PRIOR ART

2/31

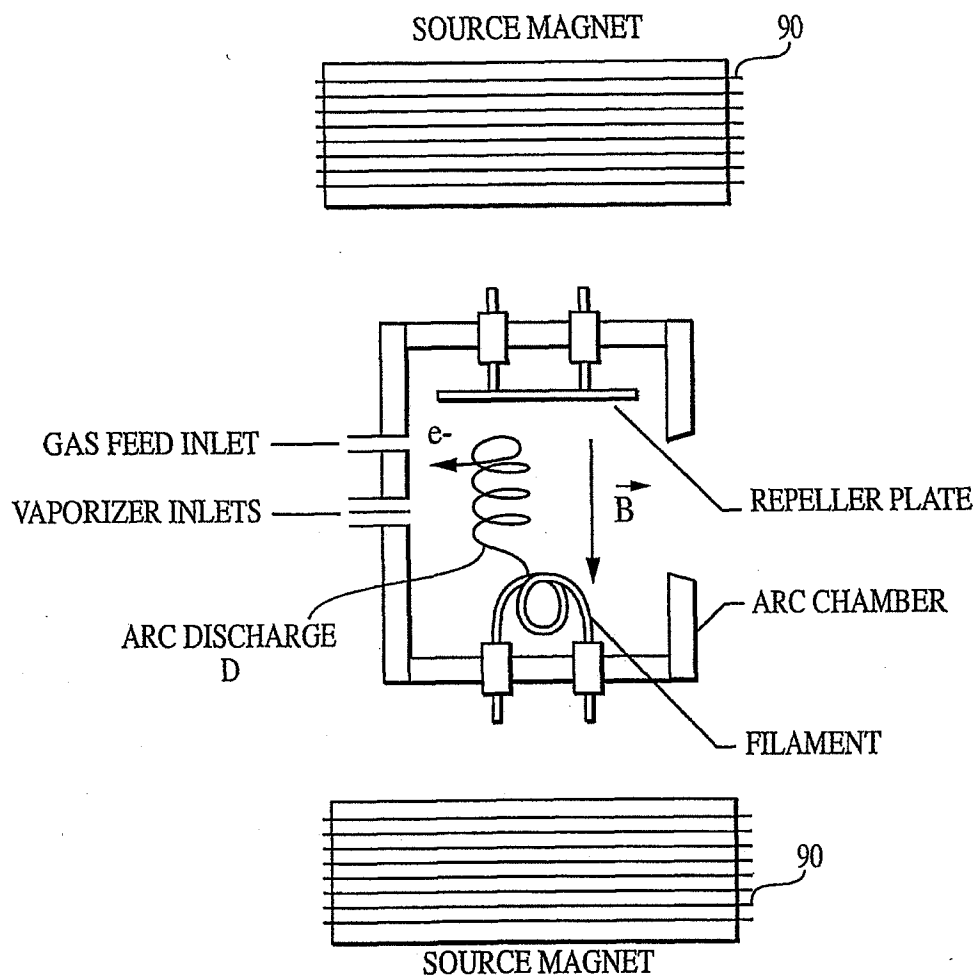


FIG. 2  
PRIOR ART

3/31

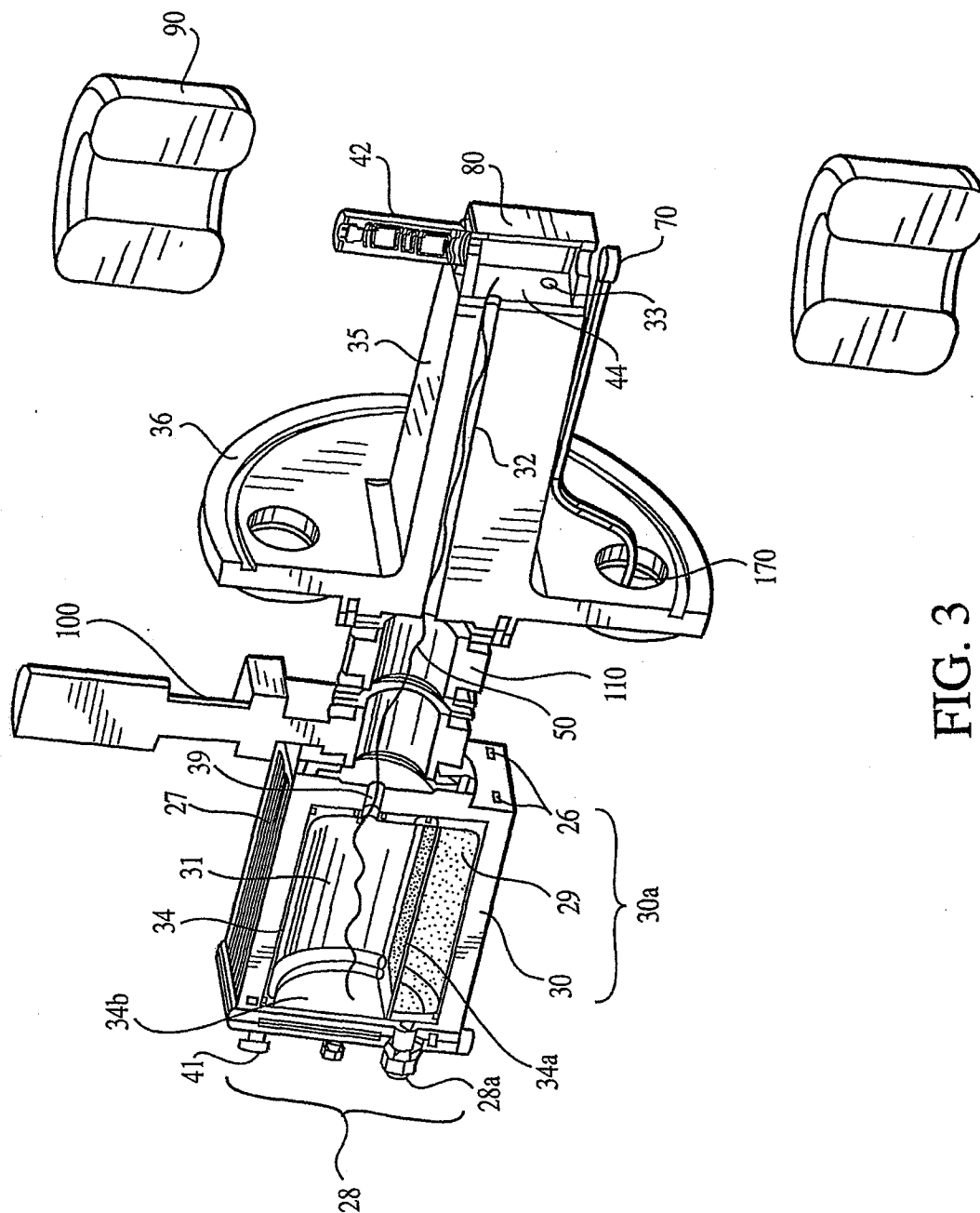


FIG. 3

4/31

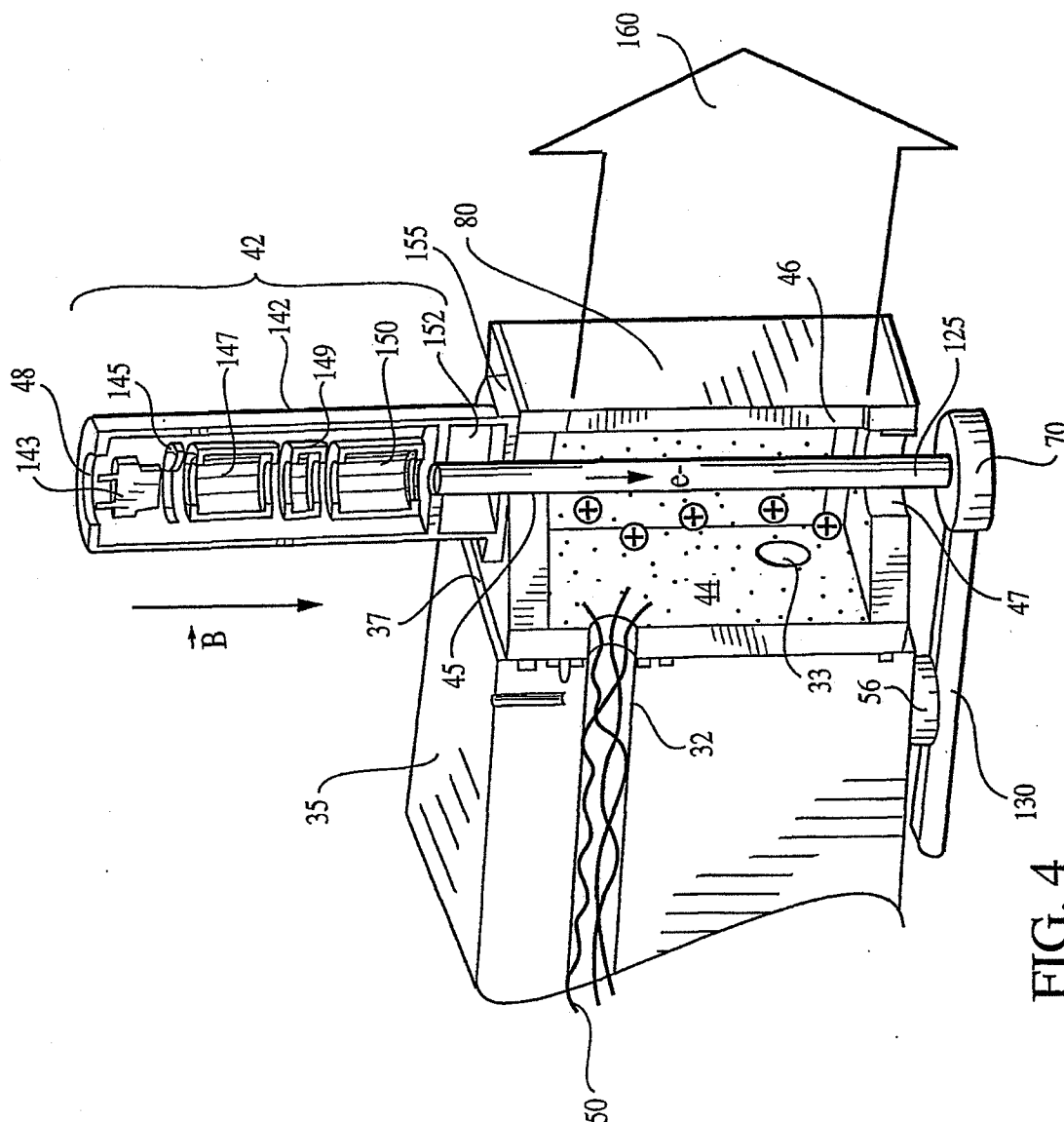


FIG. 4

5/31

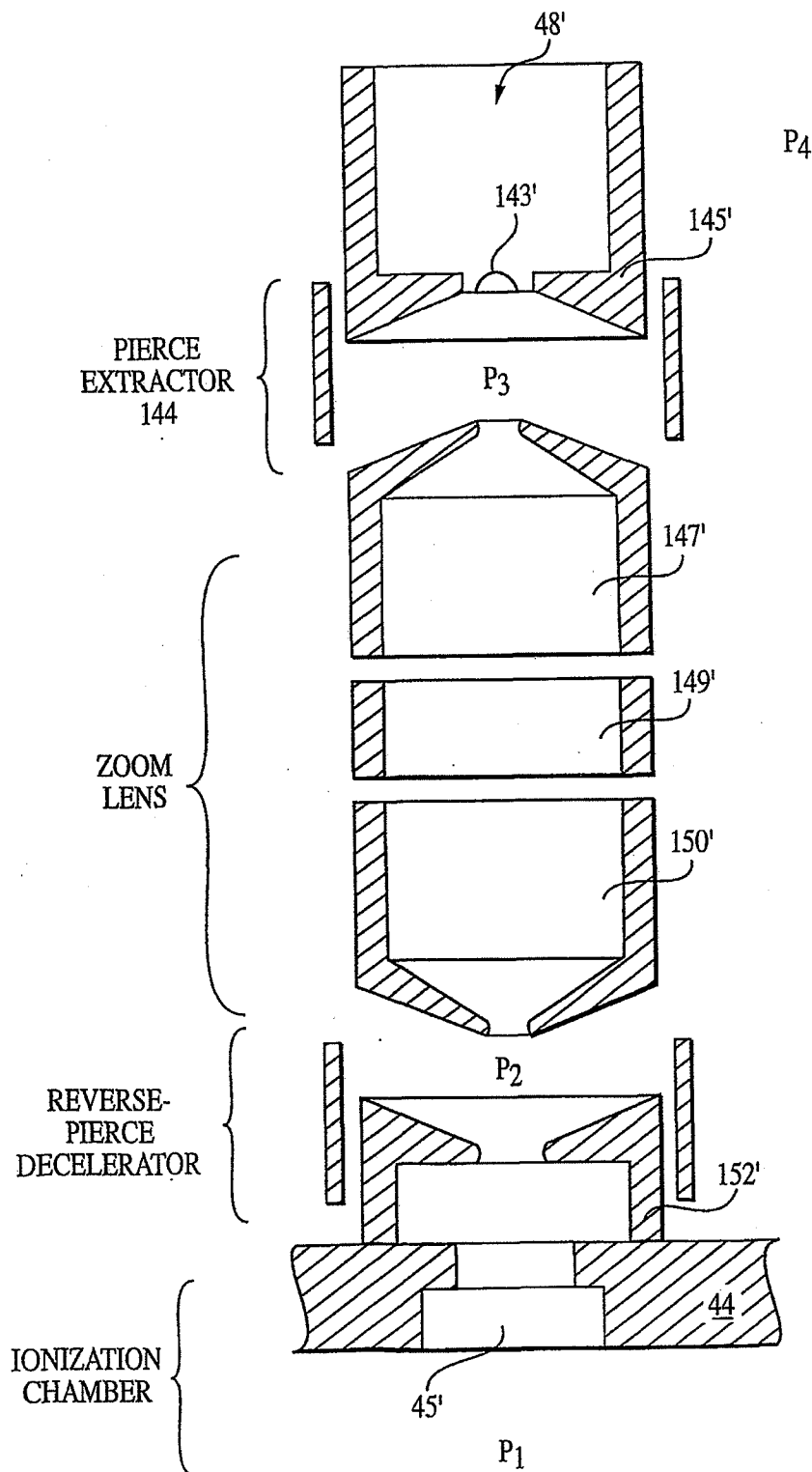


FIG. 4a

SUBSTITUTE SHEET (RULE 26)

6/31

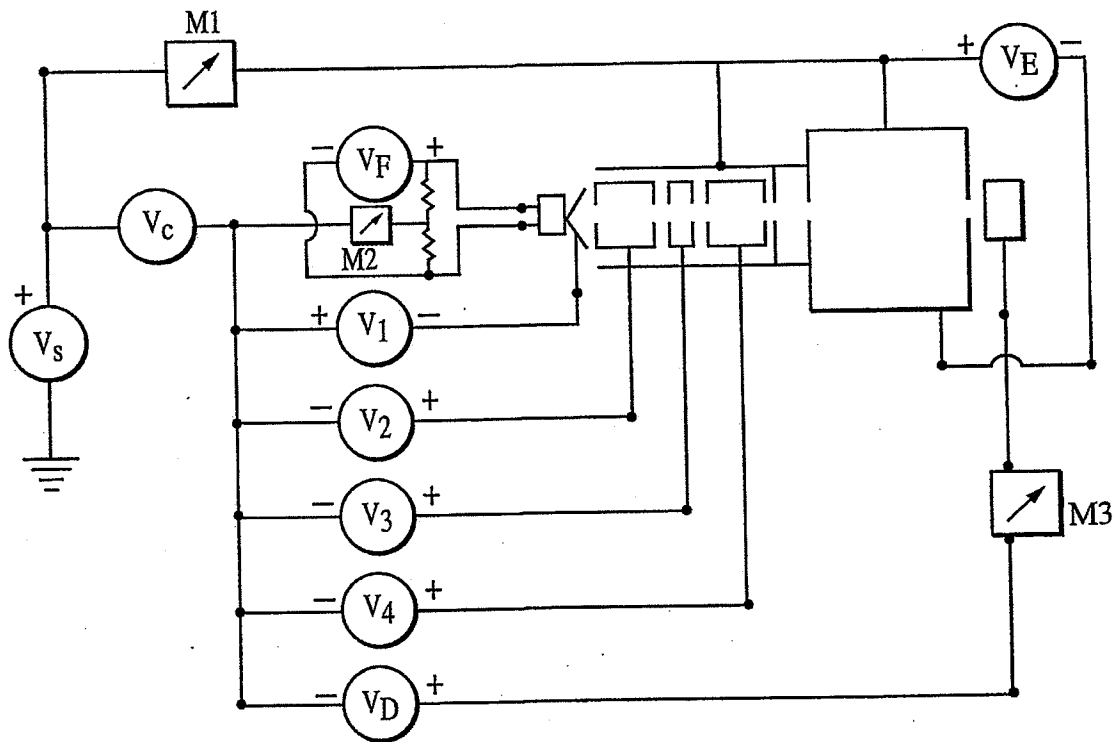
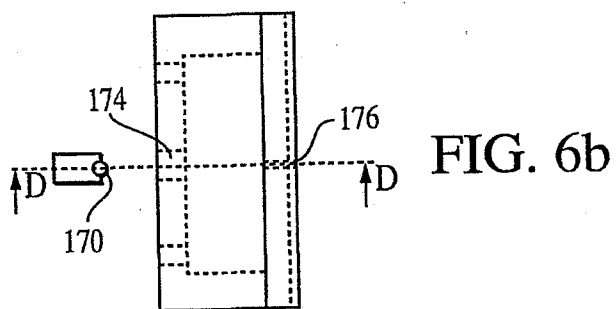
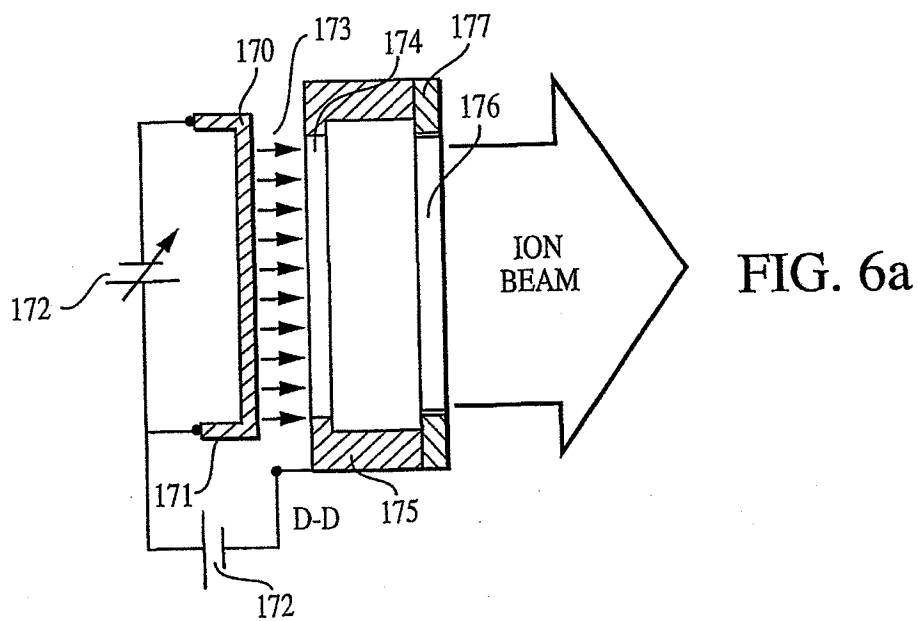


FIG. 5

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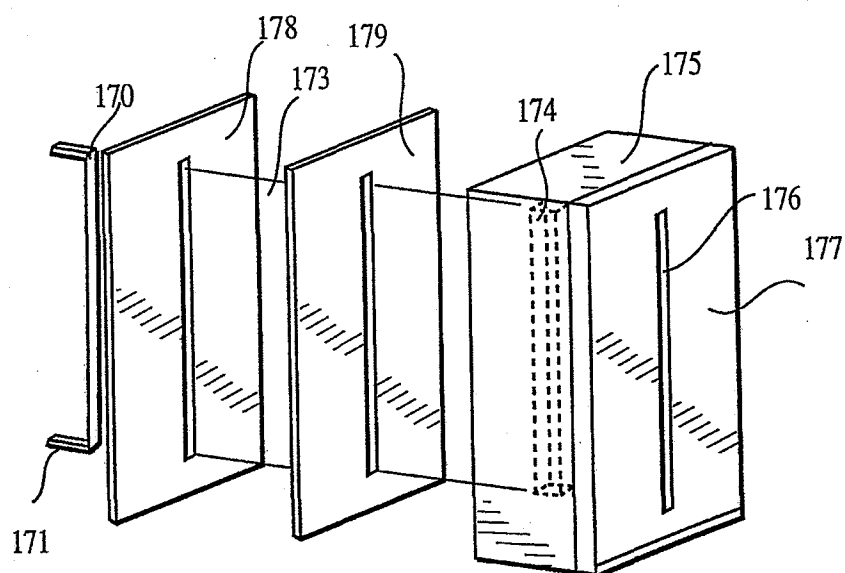


FIG. 7a

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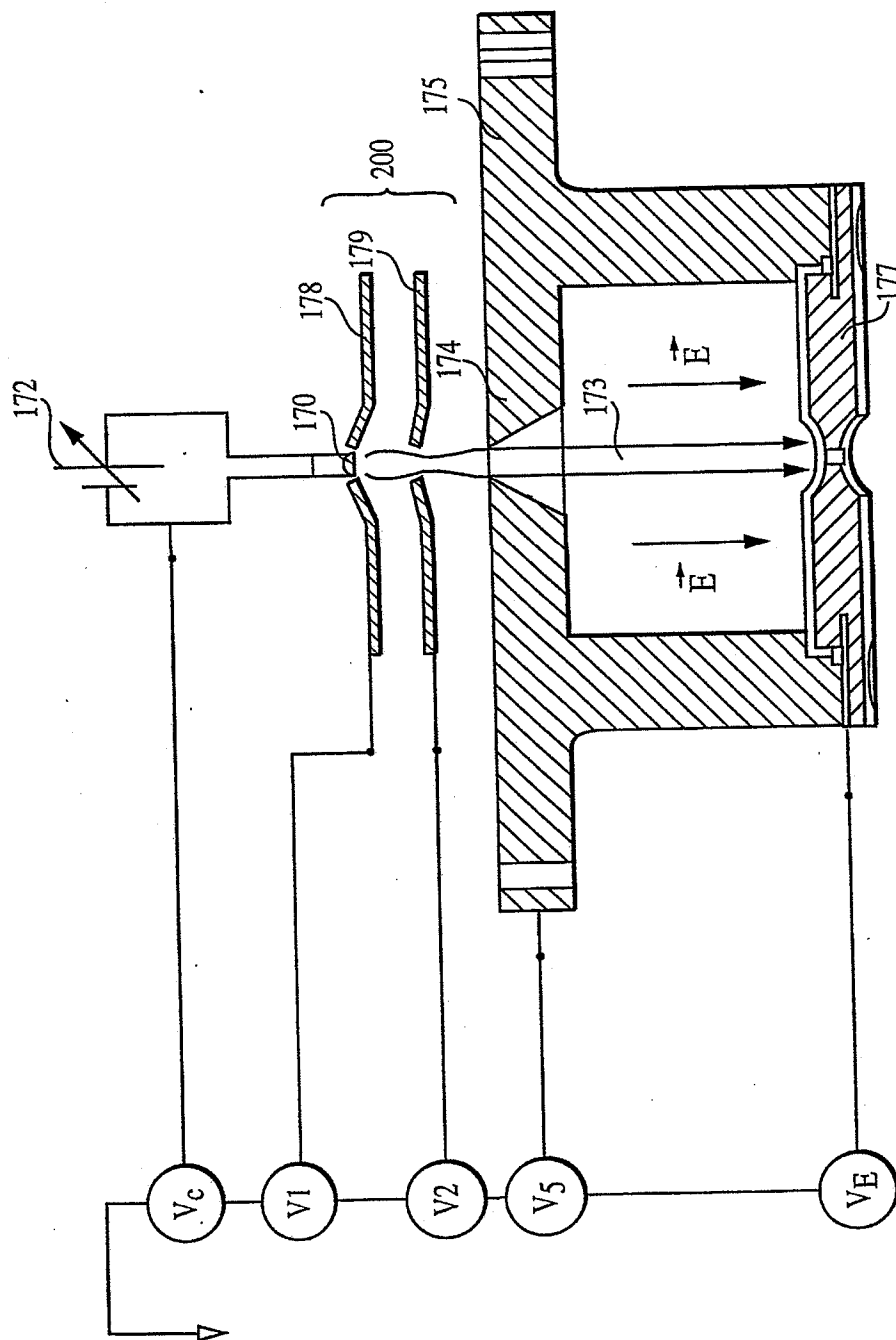
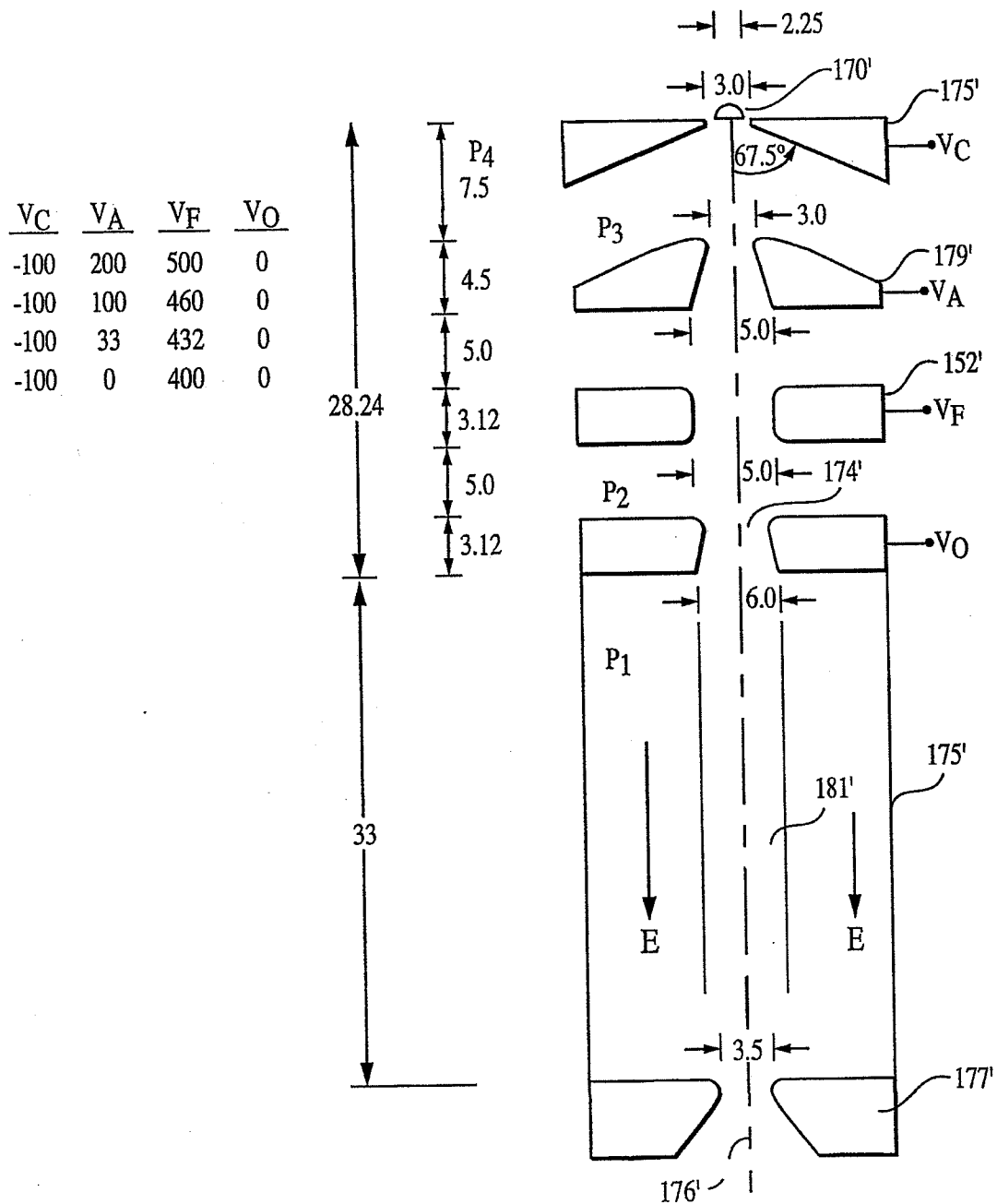


FIG. 7b

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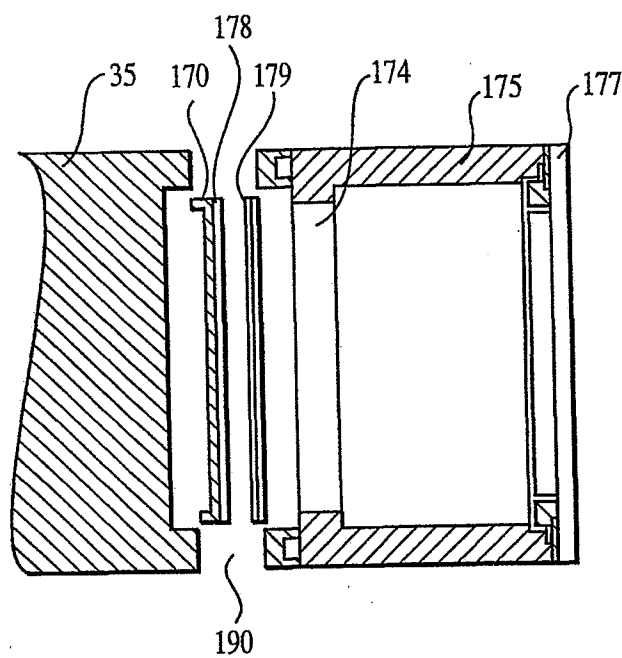


FIG. 8

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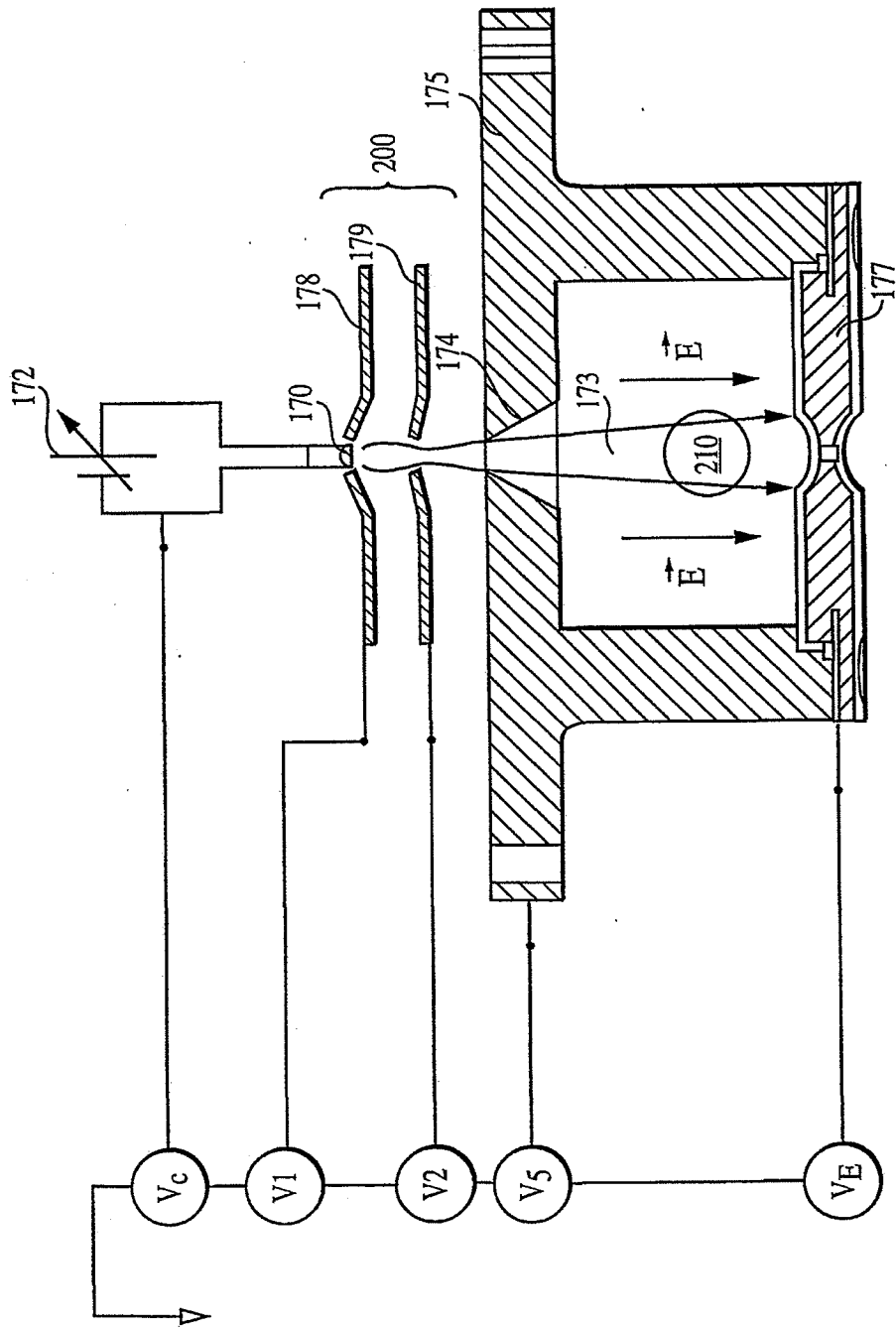


FIG. 9a

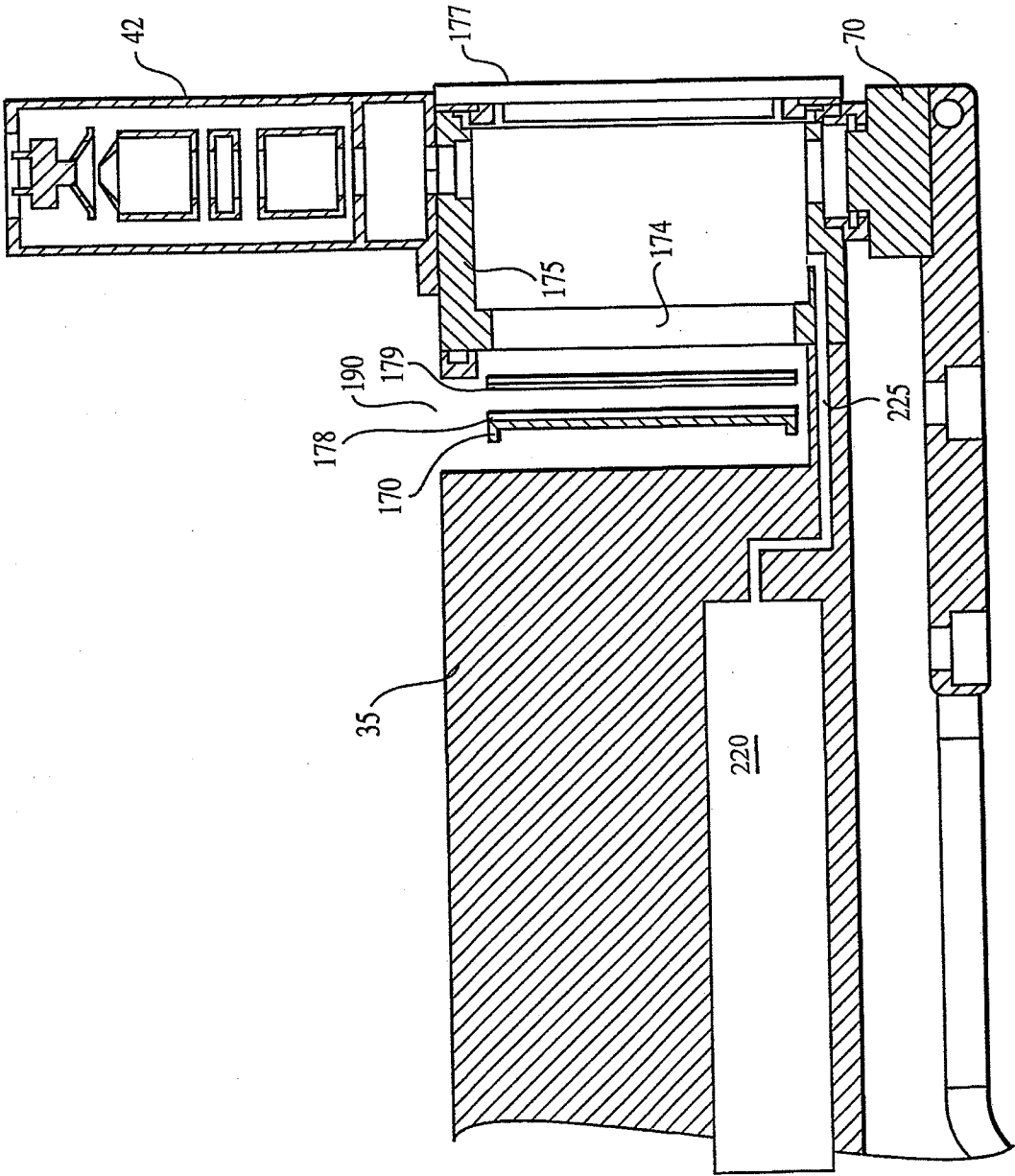


FIG. 10

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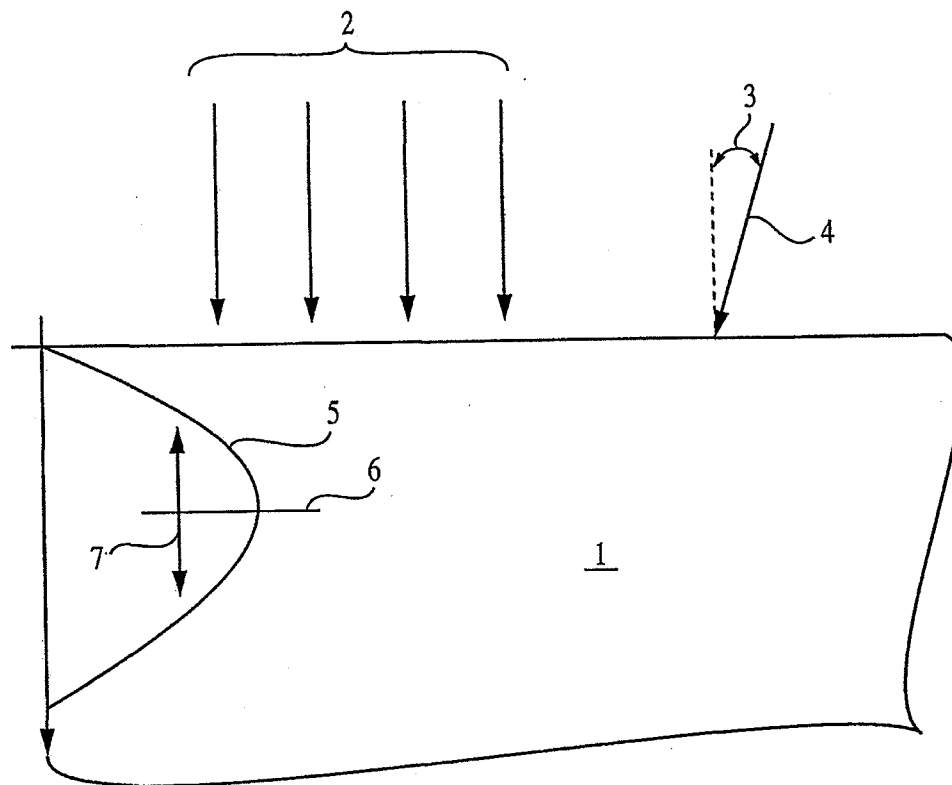


FIG. 11

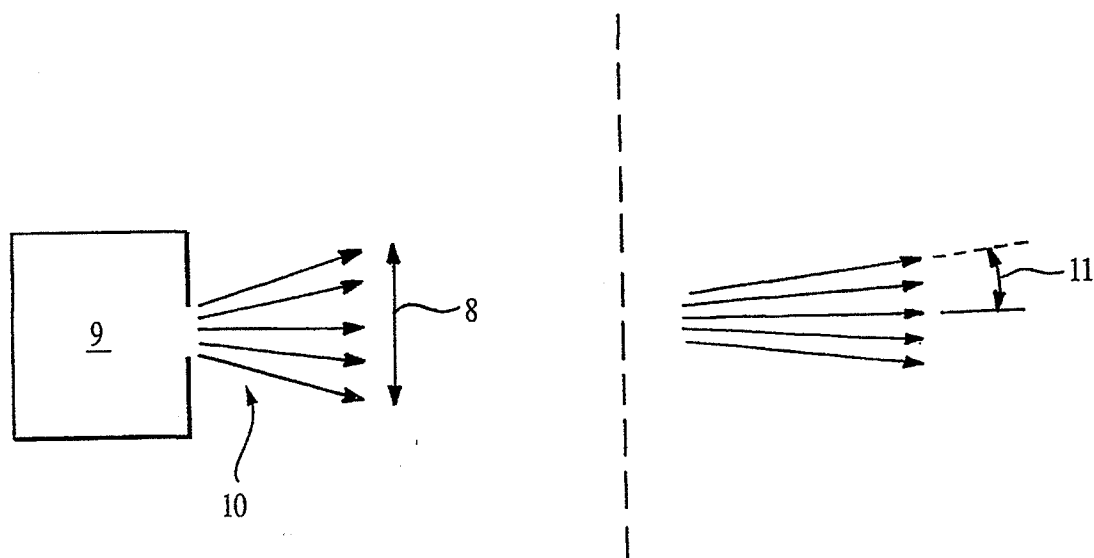


FIG. 12

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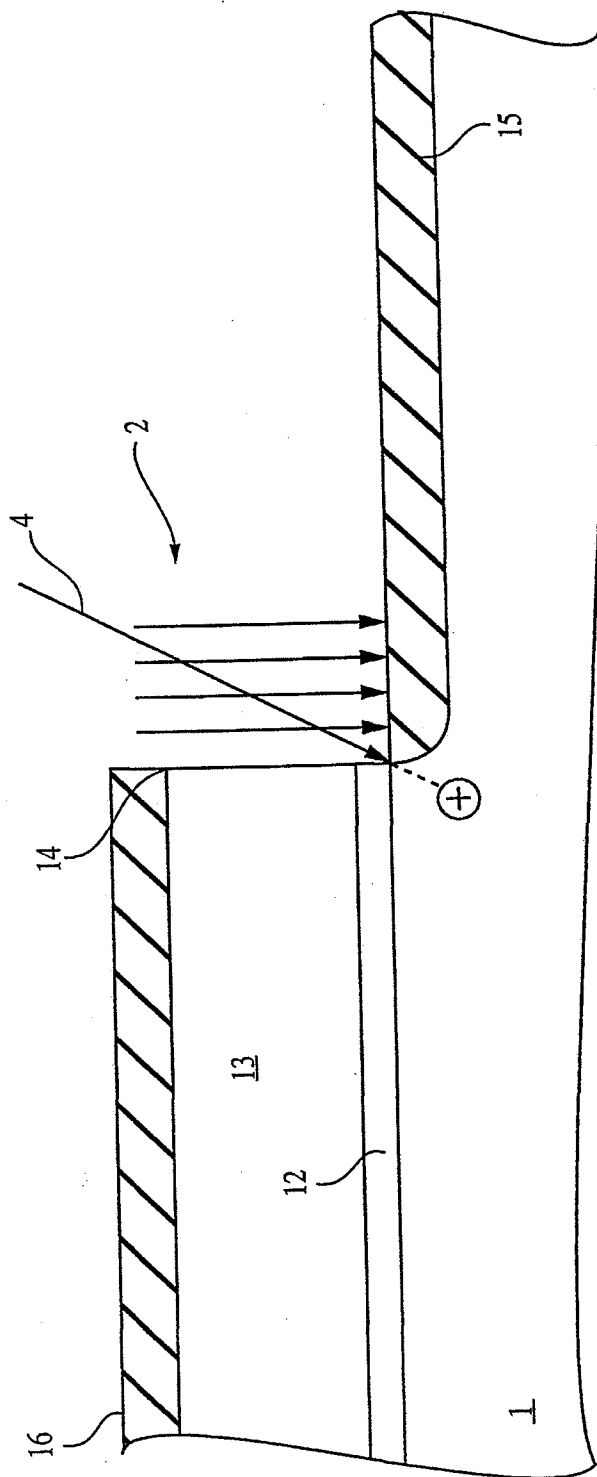


FIG. 13



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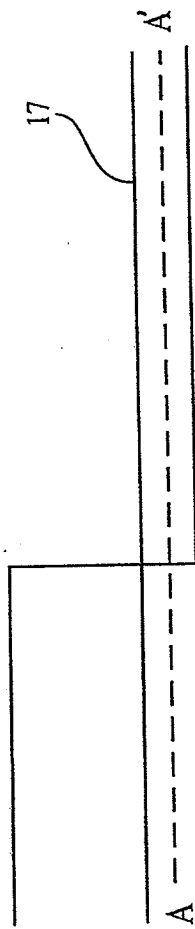


FIG. 14a

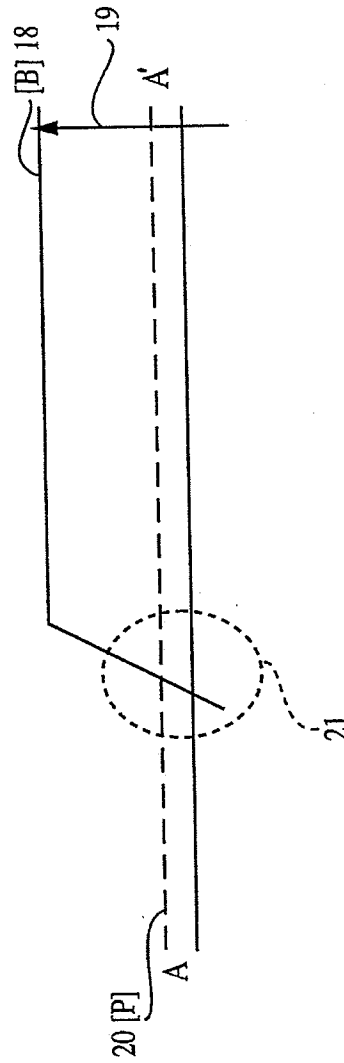


FIG. 14b

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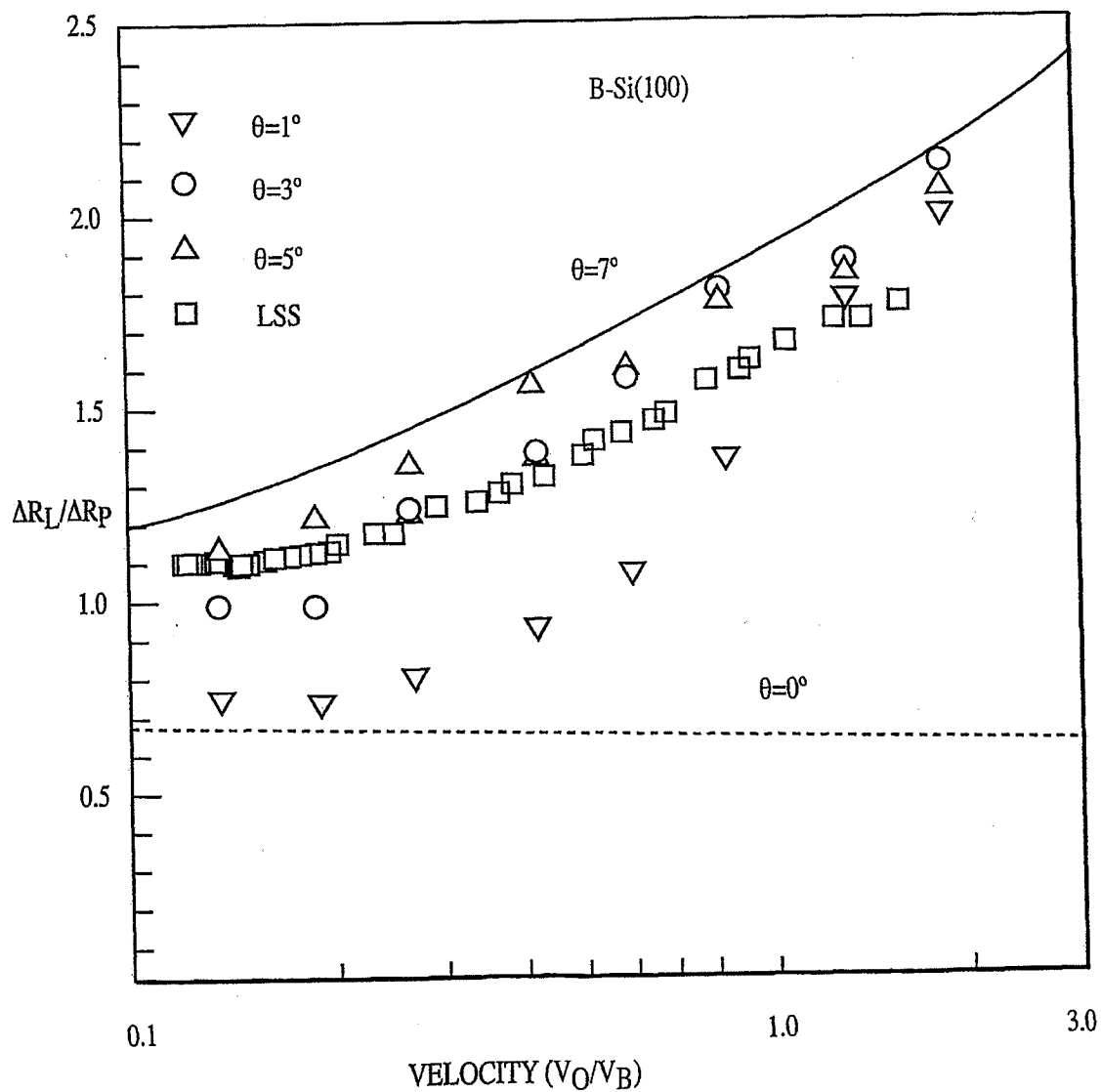


FIG. 15

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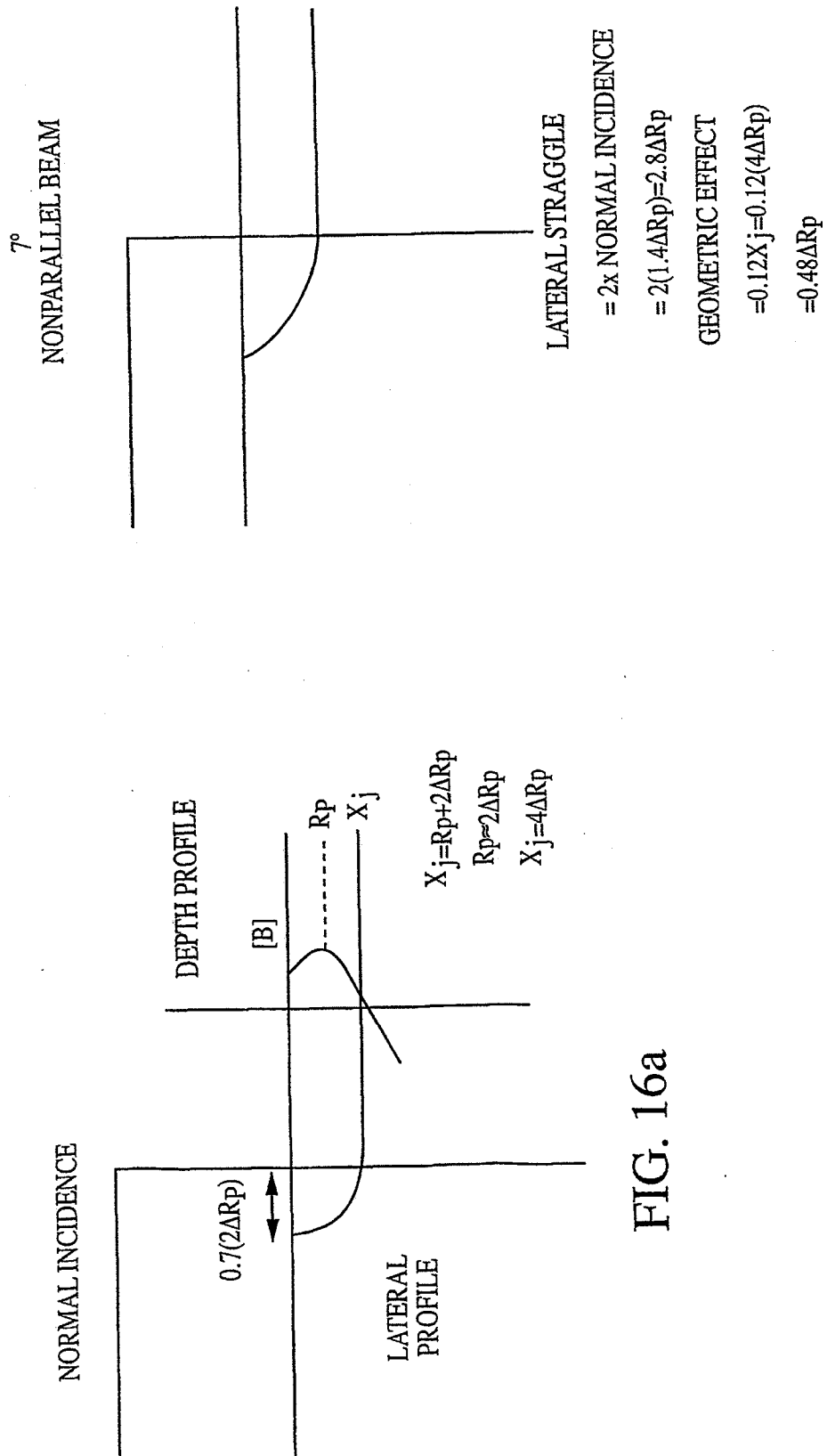


FIG. 16a

FIG. 16b

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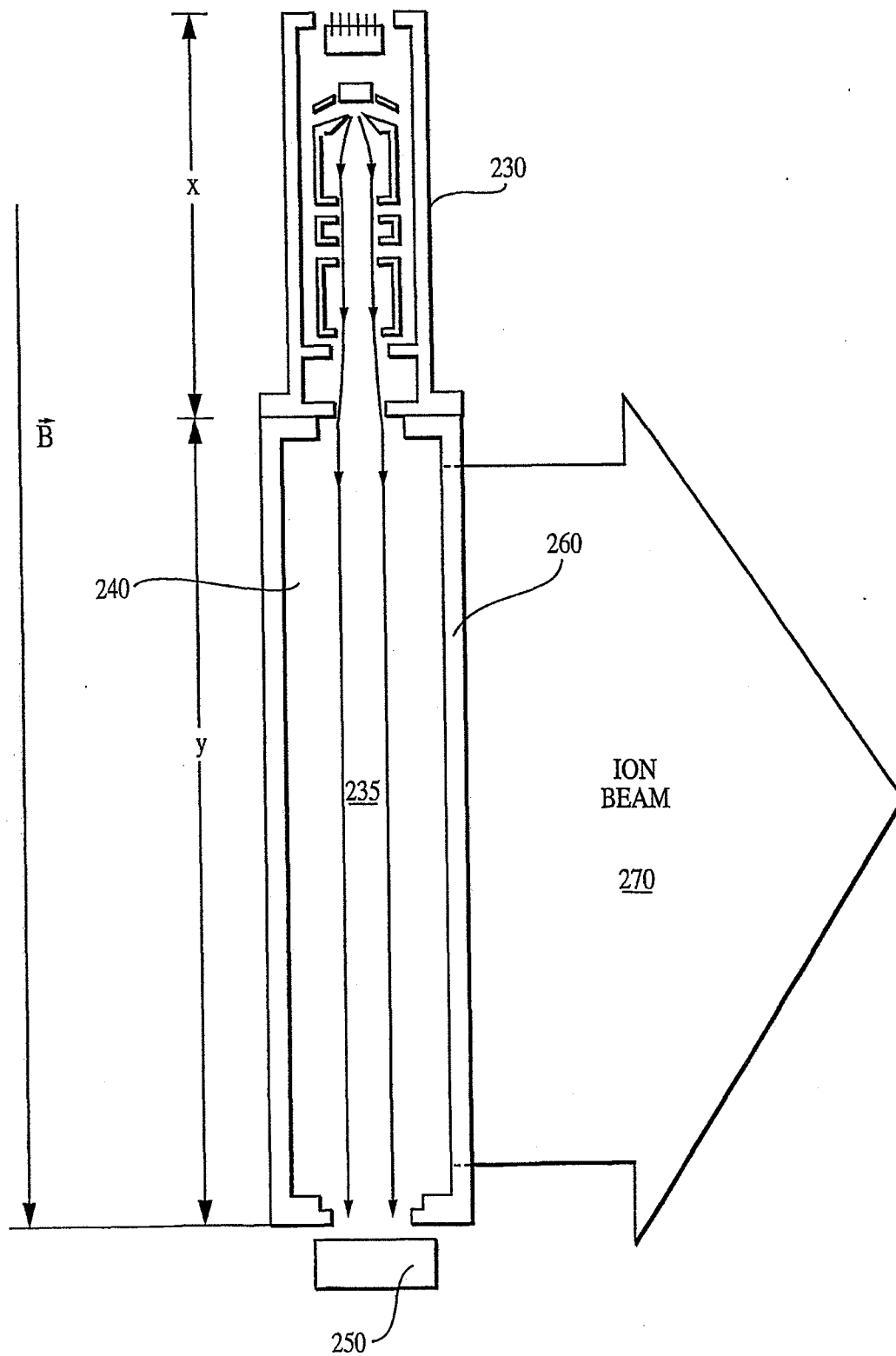


FIG. 17

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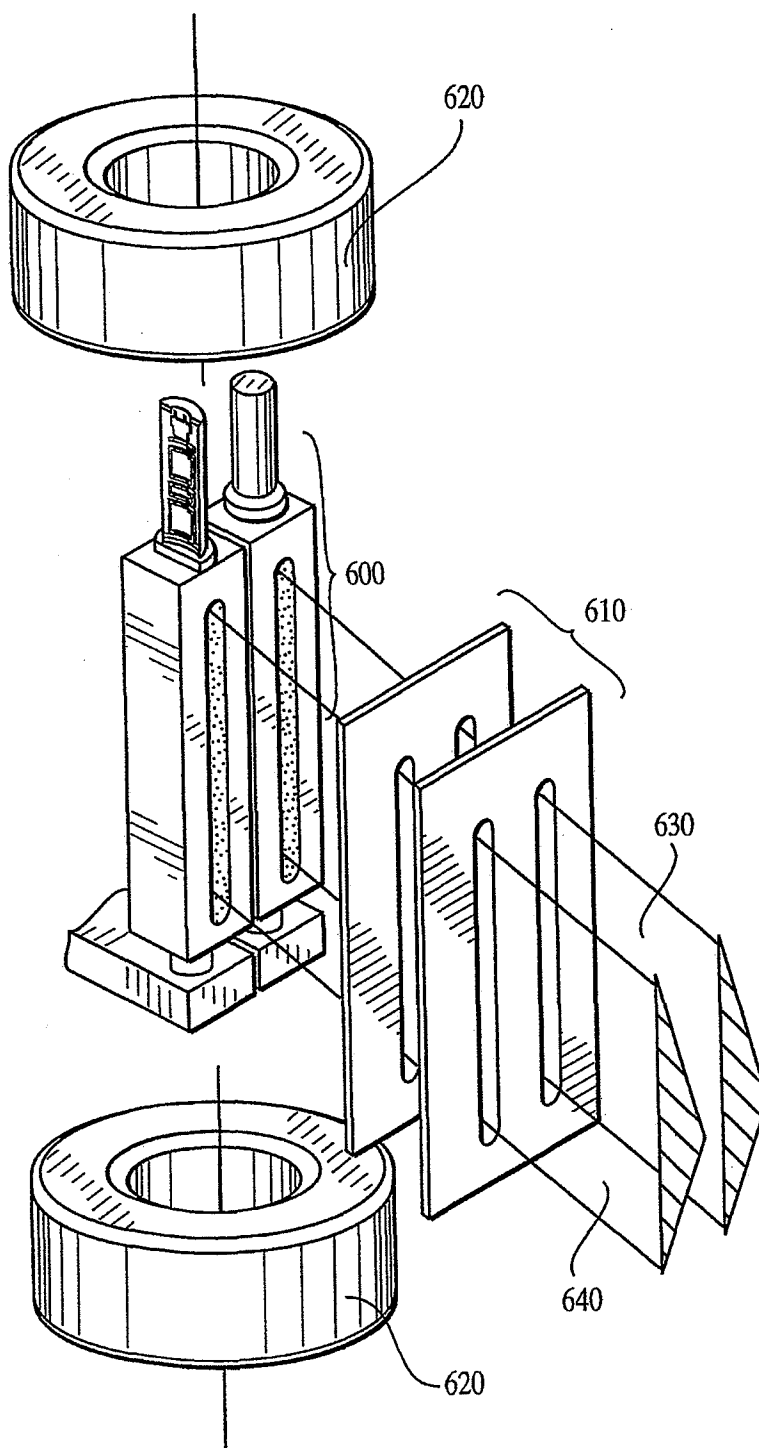


FIG. 18a

21/31

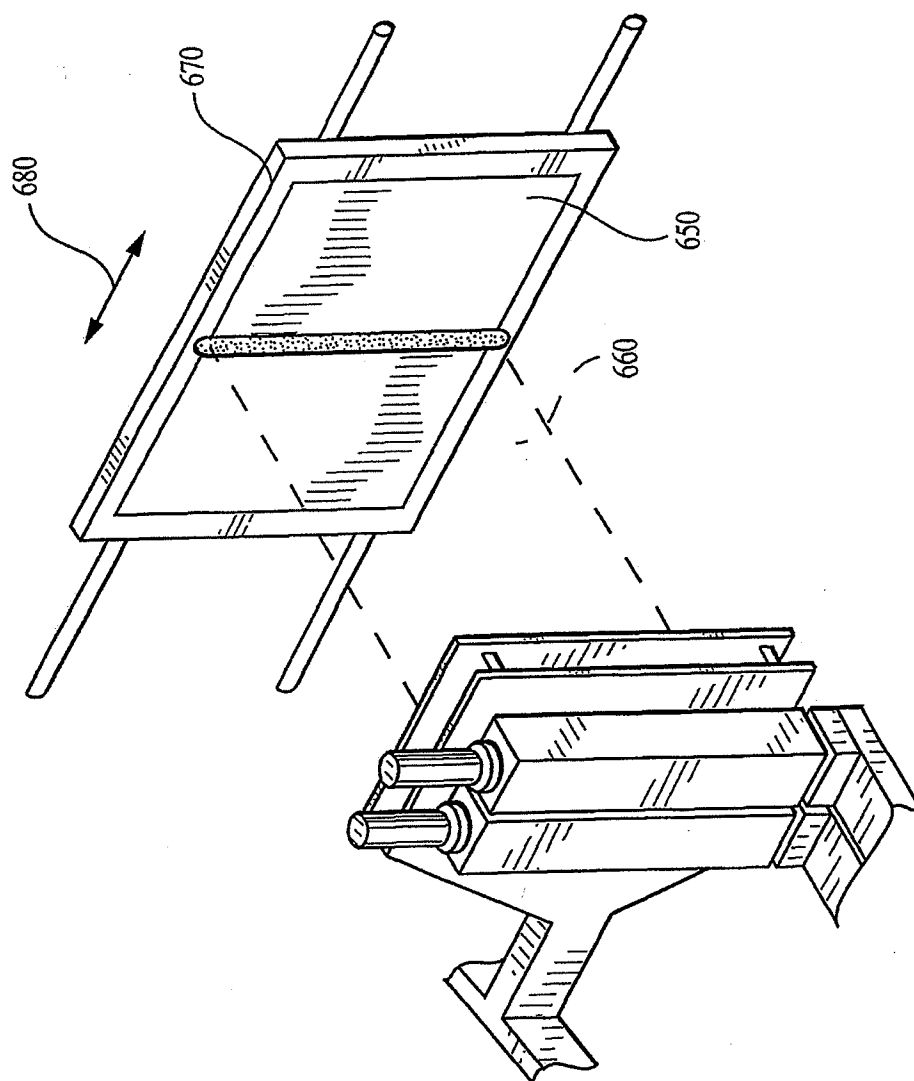


FIG. 18b

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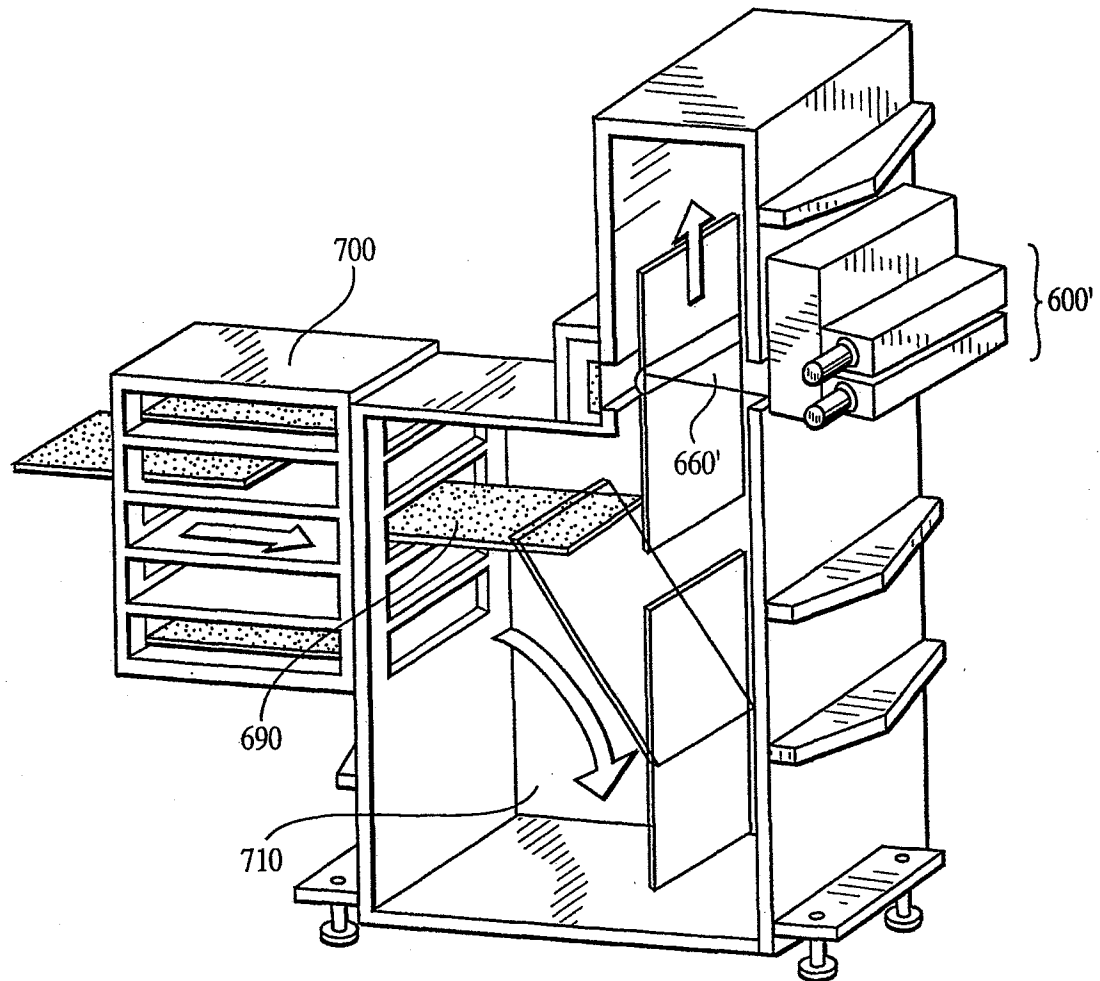


FIG. 19

23/31

B 10094

B10H14

B 1130

B 1131

B 1420

B-1,776

B1, BENZODIAZEPINE

B 208

B 208-TROPON

DECABORANE(14)

FORMULA: B<sub>10</sub>H<sub>14</sub>

MW: 124 CAS#: 17702-41-9 NIST#: 2415 ID#: 29981

DB: MAIN LIB

OTHER DBs: FINE, TSCA, EPA, HODOC, NIH, EINECS

CONTRIBUTOR: CCC 0024

109 MASSES AND ABUNDANCES

2	185	37	15	60	5	82	9	104	125
10	20	38	11	61	1	83	5	105	83
11	70	39	8	62	1	84	10	106	75
12	61	41	1	63	2	85	31	107	109
13	197	42	1	64	6	86	70	108	181
14	1	43	4	65	16	87	112	109	241
15	1	44	9	66	30	88	131	110	251
16	1	45	16	67	37	89	135	111	267
22	1	46	23	68	35	90	131	112	336

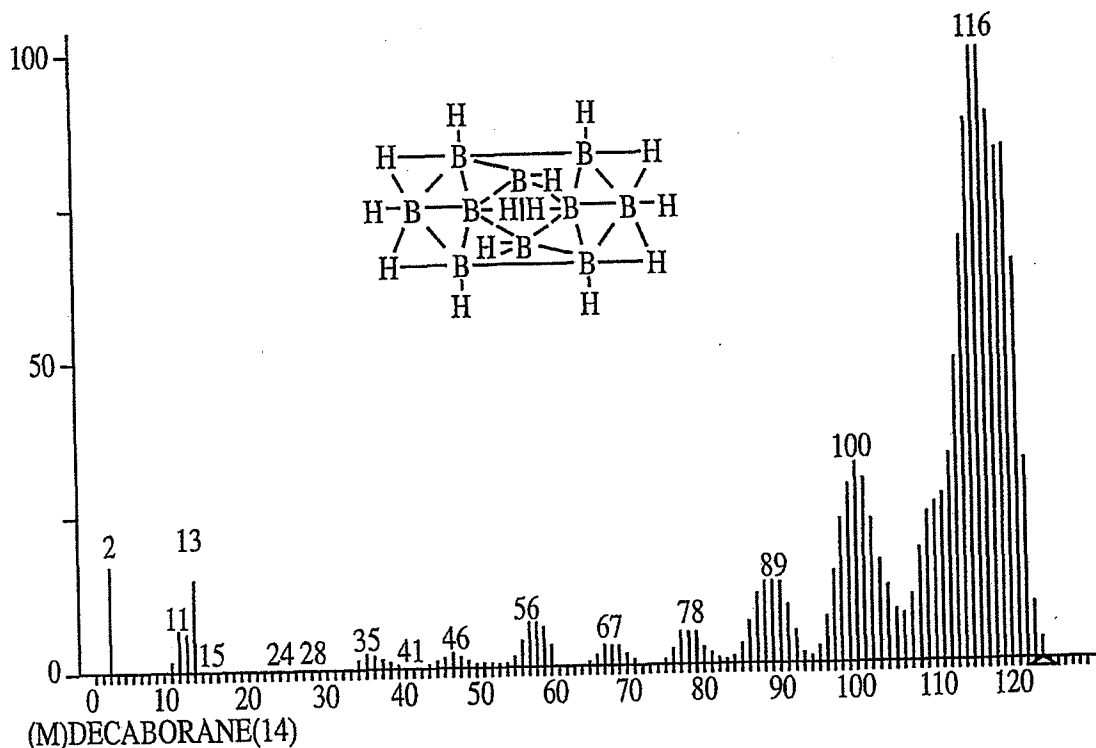
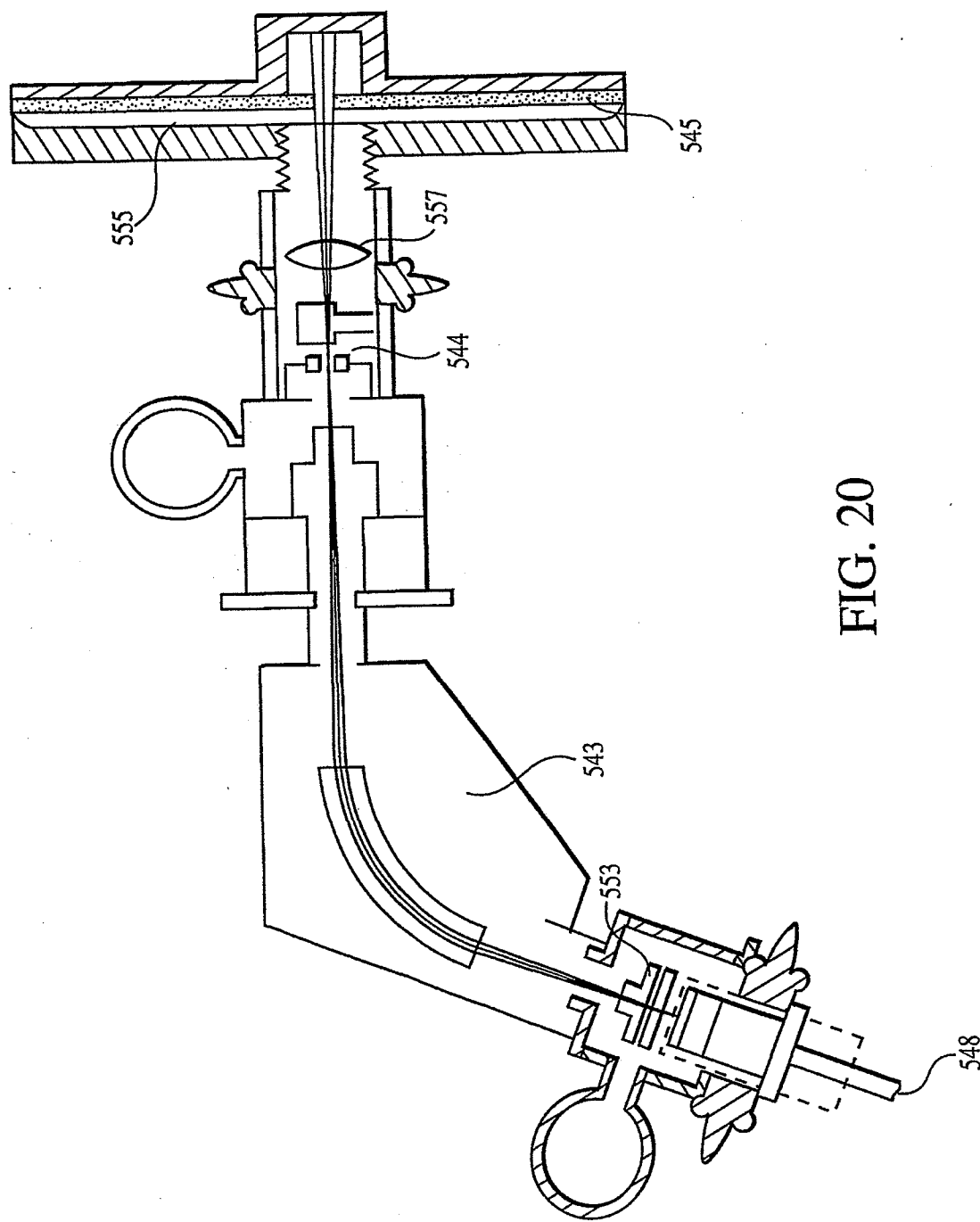


FIG. 19a



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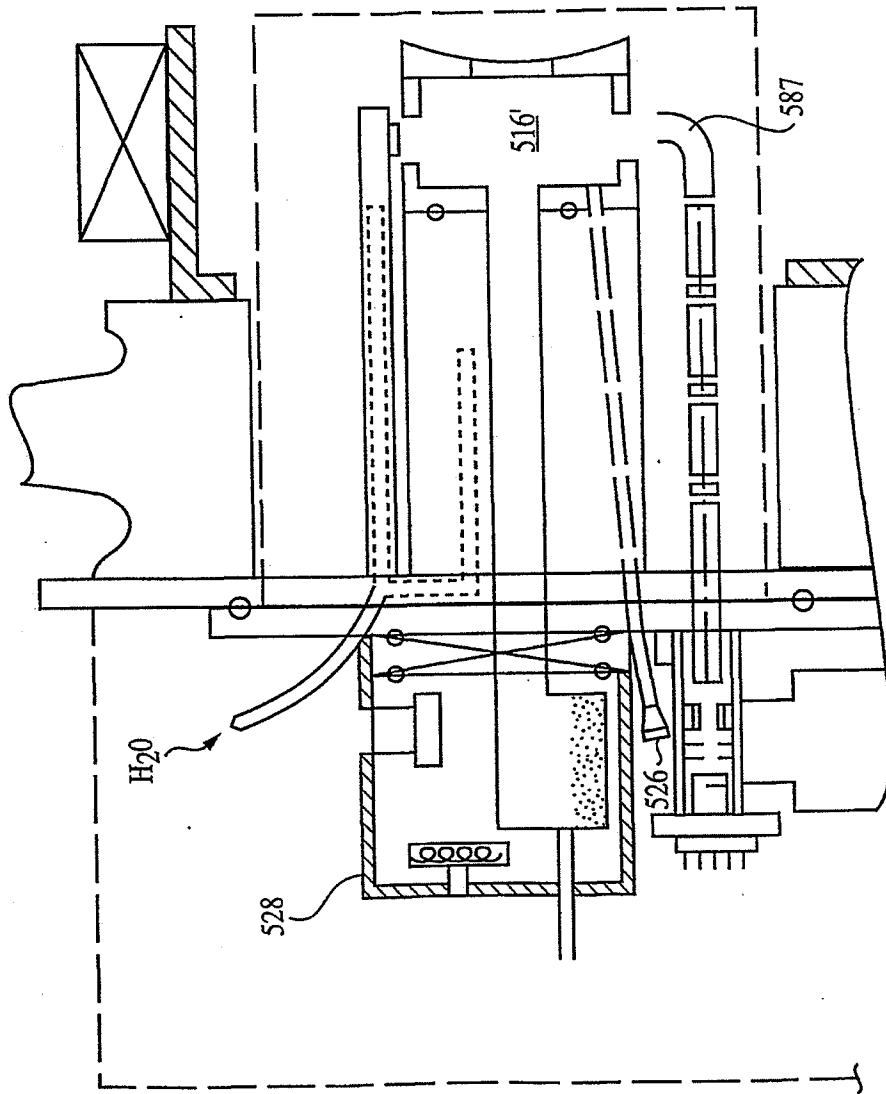


FIG. 21

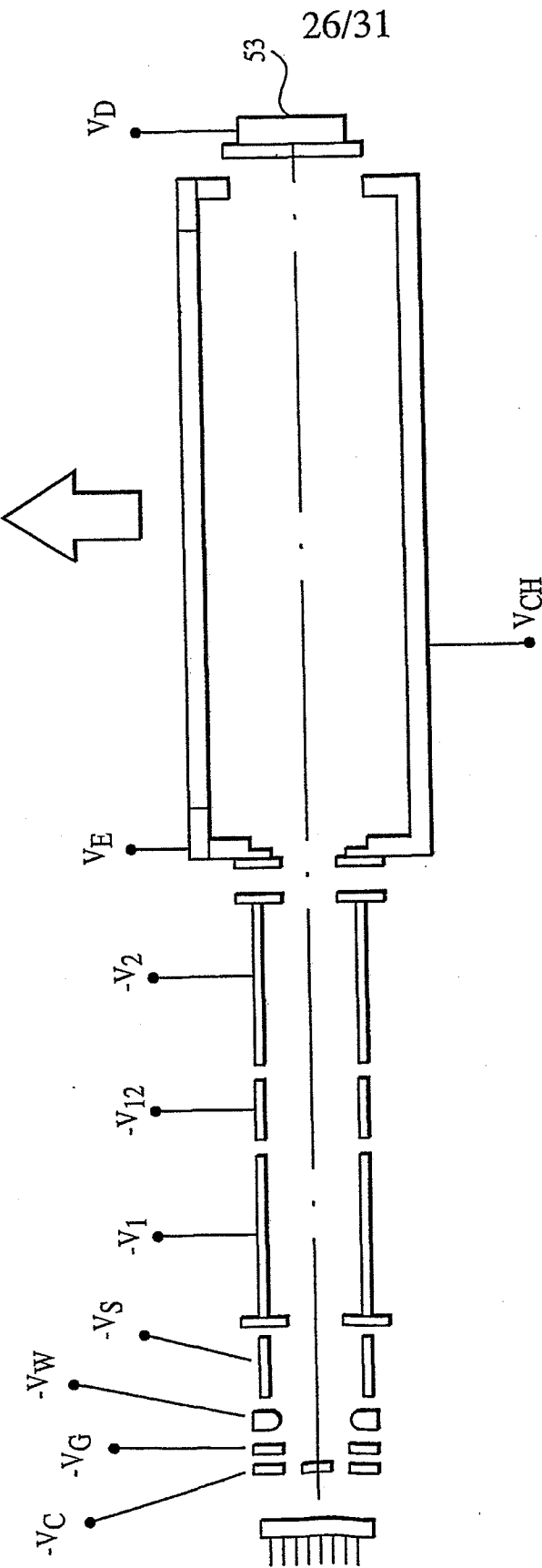


FIG. 22

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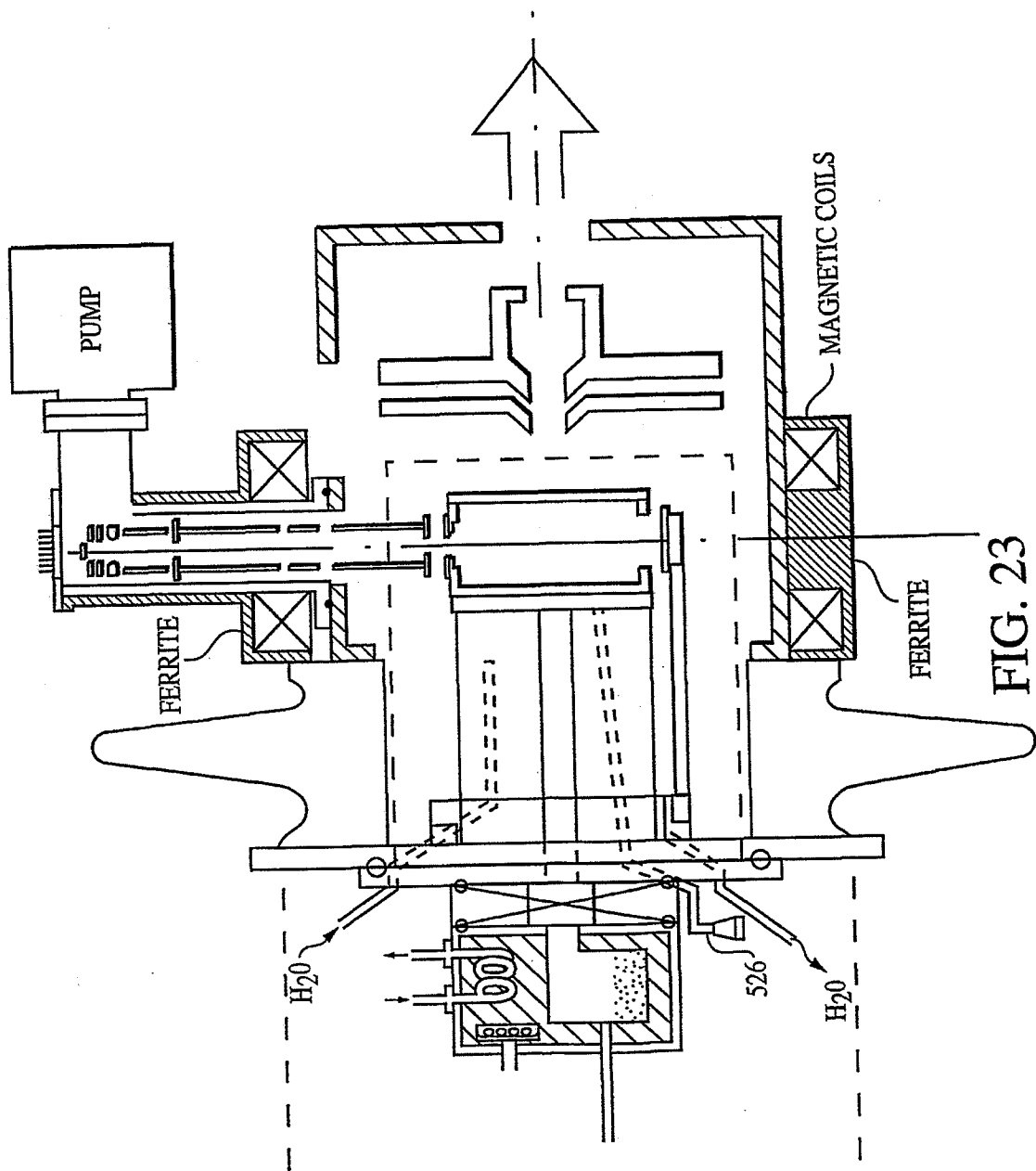


FIG. 23

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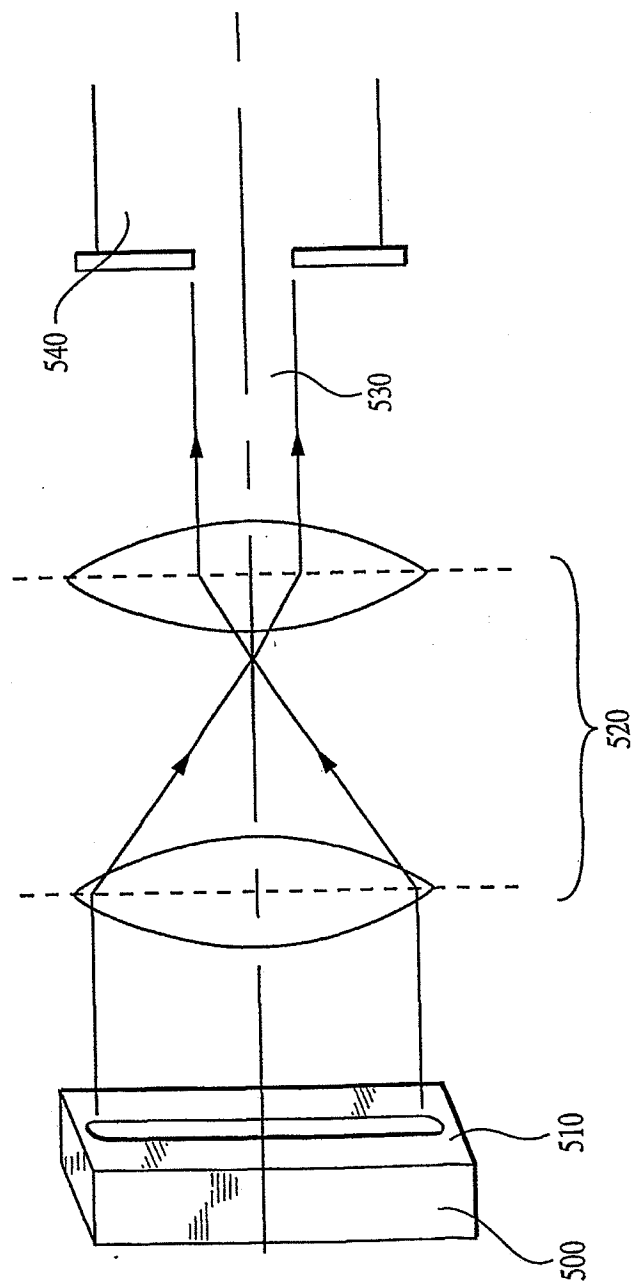


FIG. 24

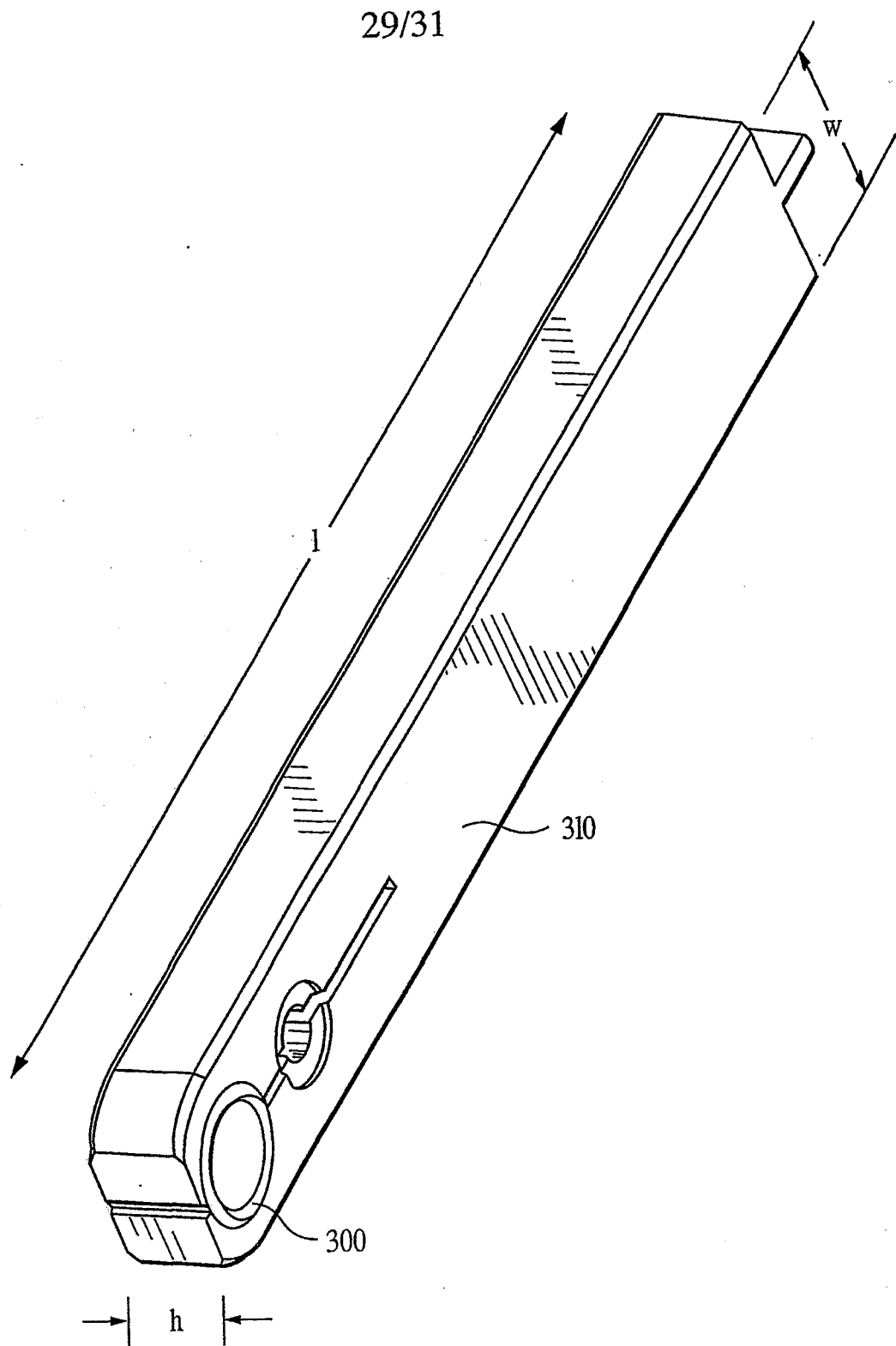


FIG. 25

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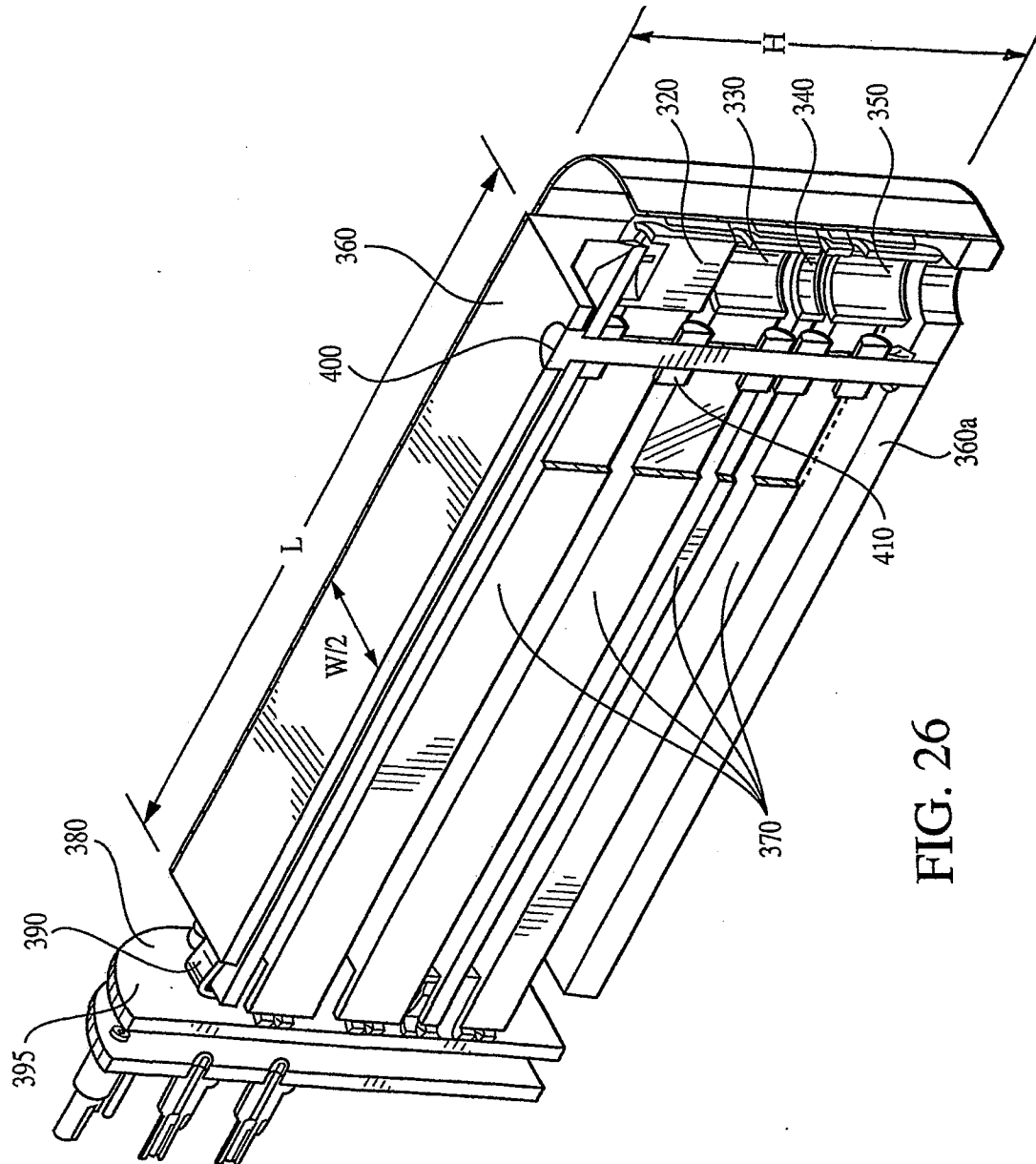
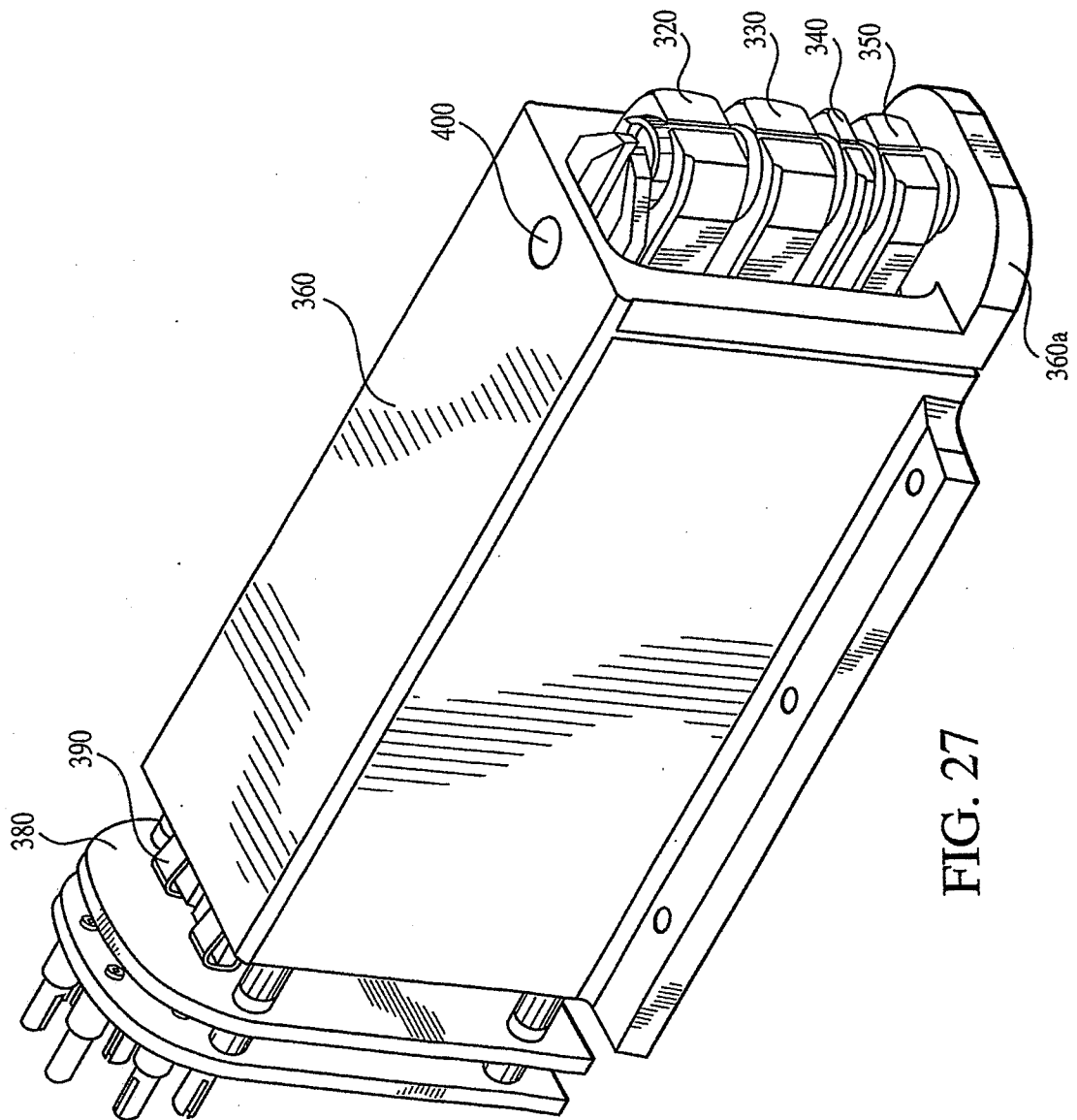


FIG. 26

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## INTERNATIONAL SEARCH REPORT

International application No.  
PCT/US01/18822

<b>A. CLASSIFICATION OF SUBJECT MATTER</b> IPC(7) : A61N 5/00; H01J 7/24 ✓ US CL : Please See Extra Sheet. According to International Patent Classification (IPC) or to both national classification and IPC														
<b>B. FIELDS SEARCHED</b> Minimum documentation searched (classification system followed by classification symbols) U.S. : 250/389, 424, 425, 492.1, 492.2, 492.3; 427/523; 315/111.81, 111.91, 111.21 Documentation searched other than minimum documentation to the extent that such documents are included in the fields searched none Electronic data base consulted during the international search (name of data base and, where practicable, search terms used) EAST text search; terms: ion implantation, electron optics, vaporizer, chamber, electron gun, acceleration, deceleration.														
<b>C. DOCUMENTS CONSIDERED TO BE RELEVANT</b>														
Category*	Citation of document, with indication, where appropriate, of the relevant passages	Relevant to claim No.												
X	US 5,293,508 A (SHIRATAKE ET AL.) 08 MARCH 1994, (08/03/94) figs 1-3; col. 1, lines 20-42; col. 2, lines 3-19.	22-30, 35-39, 40-45												
A	US 4,904,902 A (TAMAI ET AL.) 27 FEBRUARY 1990, (27/02/90) see entire document.	1-57												
A	US 3, 915, 757 A (ENGEL) 28 OCTOBER 1975, (28/10/75) see entire document.	1-57												
A	US 3,908,183 A (ENNIS, JR.) 23 SEPTEMBER 1975, (23/09/75) see entire document.	1-57												
<input type="checkbox"/> Further documents are listed in the continuation of Box C. <input type="checkbox"/> See patent family annex.														
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Date of the actual completion of the international search 19 JULY 2001		Date of mailing of the international search report 14 AUG 2001												
Name and mailing address of the ISA/US Commissioner of Patents and Trademarks Box PCT Washington, D.C. 20231 Facsimile No. (703) 305-3230		Authorized officer THUY VINH TRAN <i>[Signature]</i> Telephone No. (703) 305-0012												

# INTERNATIONAL SEARCH REPORT

International application No.

PCT/US01/18822

## A. CLASSIFICATION OF SUBJECT MATTER:

US CL :

250/389, 424, 425, 492.1, 492.2, 492.3; 427/523; 315/111.81, 111 91, 111.21